# BTS710404ESPXUMA1 Datasheet

| | |
|---|---|
| DiGi Electronics Part Number | BTS710404ESPXUMA1-DG |
| Manufacturer | Infineon Technologies |
| Manufacturer Product Number | BTS710404ESPXUMA1 |
| Description | SPOC PG-TSDSO-24 |
| Detailed Description | Power Switch/Driver 1:4 N-Channel 3A PG-TSDSO-24-42 |

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

## Purchase and inquiry

| Manufacturer Product Number: | Manufacturer: |
| --- | --- |
| BTS710404ESPXUMA1 | Infineon Technologies |
| Series: | Product Status: |
| SPOC™ | Active |
| Switch Type: | Number of Outputs: |
| Relay, Solenoid Driver | 4 |
| Ratio - Input:Output: | Output Configuration: |
| 1:4 | High Side |
| Output Type: | Interface: |
| N-Channel | PWM, SPI |
| Voltage - Load: | Voltage - Supply (Vcc/Vdd): |
| 6V ~ 28V | 3V ~ 5.5V |
| Current - Output (Max): | Rds On (Typ): |
| 3A | 22.5mOhm |
| Input Type: | Features: |
| Non-Inverting | Load Discharge, PWM Input, Slew Rate Controlled, Status Flag |
| Operating Temperature: | Grade: |
| -40°C ~ 150°C (TJ) | Automotive |
| Qualification: | Mounting Type: |
| AEC-Q100 | Surface Mount |
| Supplier Device Package: | Package / Case: |
| PG-TSDSO-24-42 | 24-TSSOP (0.154", 3.90mm Width) Exposed Pad |
| Base Product Number: | |
| BTS71040 | |

## Environmental & Export classification

| RoHS Status: | Moisture Sensitivity Level (MSL): |
| --- | --- |
| ROHS3 Compliant | 2A (4 Weeks) |
| REACH Status: | ECCN: |
| REACH Unaffected | EAR99 |
| HTSUS: | |
| 8542.39.0001 | |

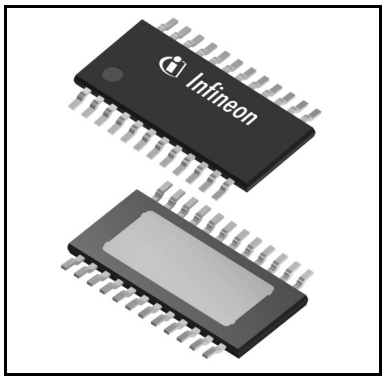
# BTS71040-4ESP

**SPOC™ +2** **4x 22.5 mΩ**

**Serial Interface Power Controller**

AEC Qualified RoHS PRO SIL ISO 26262 ready

| | |
|---|---|
| **Package** | PG-TSDSO-24 |
| **Marking** | 71040-4ESP |




## 1 Overview

### Potential Applications

- Suitable for resistive, inductive and capacitive loads
- Replaces electromechanical relays, fuses and discrete circuits
- Driving capability suitable for 3 A loads and high inrush current loads such as 27W bulb or equivalent electronic loads (e.g. LED modules)

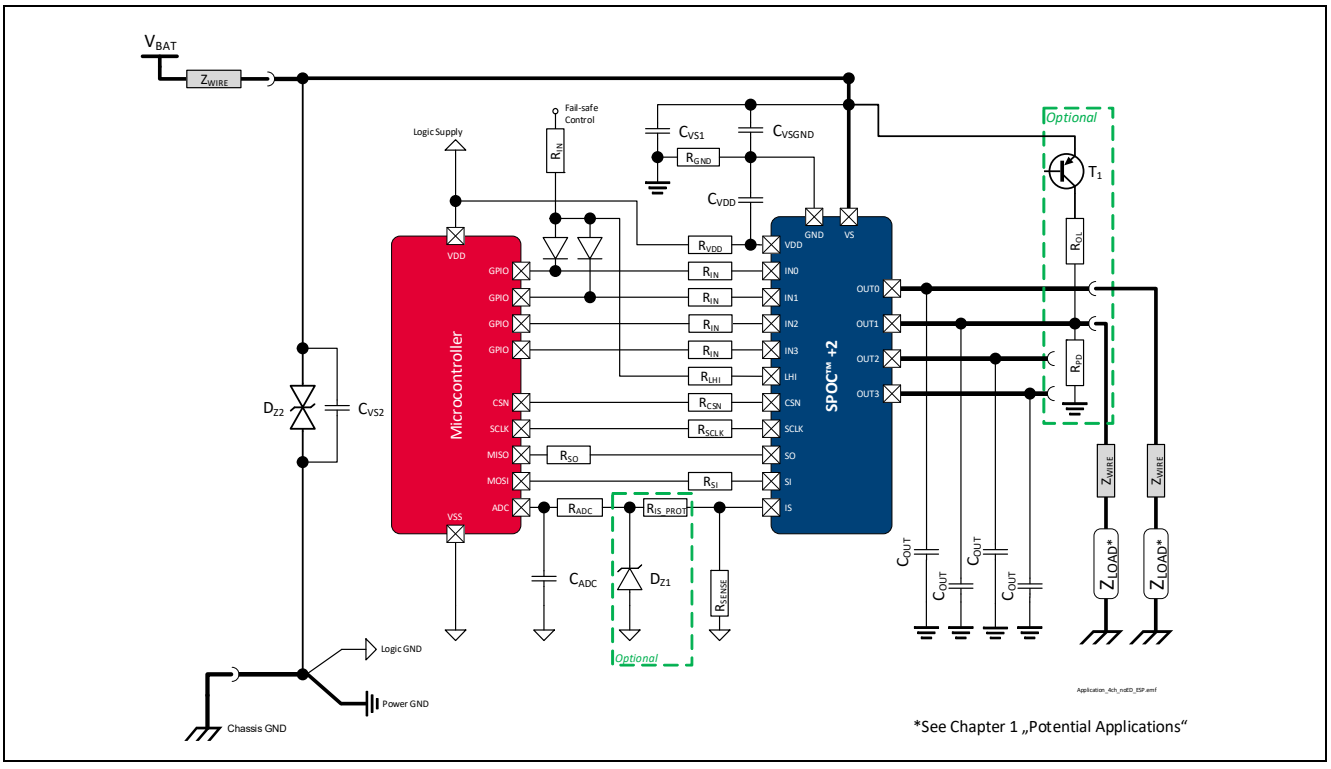



**Figure 1 Application Diagram. Further information in Chapter 11**

# BTS71040-4ESP
## SPOC™ +2

## Overview

### Basic Features

- High-Side Switch with Diagnosis and Embedded Protection
- Part of SPOC™ +2 Family
- Daisy Chain capable SPI interface
- 3.3 V and 5 V compatible logic pins
- Slew rate control for all Channels
- ReverseON for low power dissipation in Reverse Polarity
- Switch ON capability while Inverse Current condition (InverseON)
- Green Product (RoHS compliant)

### Protection Features

- Absolute and dynamic temperature limitation with controlled restart
- Overcurrent protection (tripping) with Programmable Restart Control and Current Threshold
- Undervoltage shutdown
- Overvoltage protection with external components

### Diagnostic Features

- Proportional load current sense multiplexed
- Open Load in ON and OFF state
- Short circuit to ground and battery
- Diagnosis feedback via SPI

### Functional Safety Features

- Limp Home mode
- Monitoring of Input pin status (IN and LHI)
- Checksum verification of Configuration Registers
- Current Sense verification mode

### Product Validation

Qualified for automotive applications. Product validation according to AEC-Q100 Grade 1.

### Description

The BTS71040-4ESP is a Serial Interface Power Controller, providing protection functions and diagnosis. The device is integrated in SMART7 technology.

# BTS71040-4ESP
## SPOC™ +2

## Overview

**Table 1 Product Summary**

| Parameter | Symbol | Values |
|---|---|---|
| Minimum Operating voltage (at switch ON) | $V_{S(OP)}$ | 4.1 V |
| Minimum Operating voltage (cranking) | $V_{S(UV)}$ | 3.1 V |
| Maximum Operating voltage | $V_S$ | 28 V |
| Digital Supply voltage | $V_{DD}$ | 3.3 V or 5 V |
| Minimum Overvoltage protection ($T_J \geq 25$ °C) | $V_{DS(CLAMP)\_25}$ | 35 V |
| Maximum current in Sleep mode ($T_J \leq 85$ °C) | $I_{VS(SLEEP)\_85}$ | 0.4 µA |
| Maximum operative current | $I_{GND(ACTIVE)}$ | 7 mA |
| Maximum ON-state resistance ($T_J = 150$ °C) | $R_{DS(ON)\_150}$ | 38 mΩ |
| Nominal load current ($T_A = 85$ °C) | $I_{L(NOM)}$ | 3 A |
| Typical current sense ratio at $I_L = I_{L(NOM)}$ | $k_{ILIS}$ | 2000 |
| Serial Clock Frequency | $f_{SCLK(max)}$ | 5 MHz |

# 2 Block Diagram and Terms

## 2.1 Block Diagram

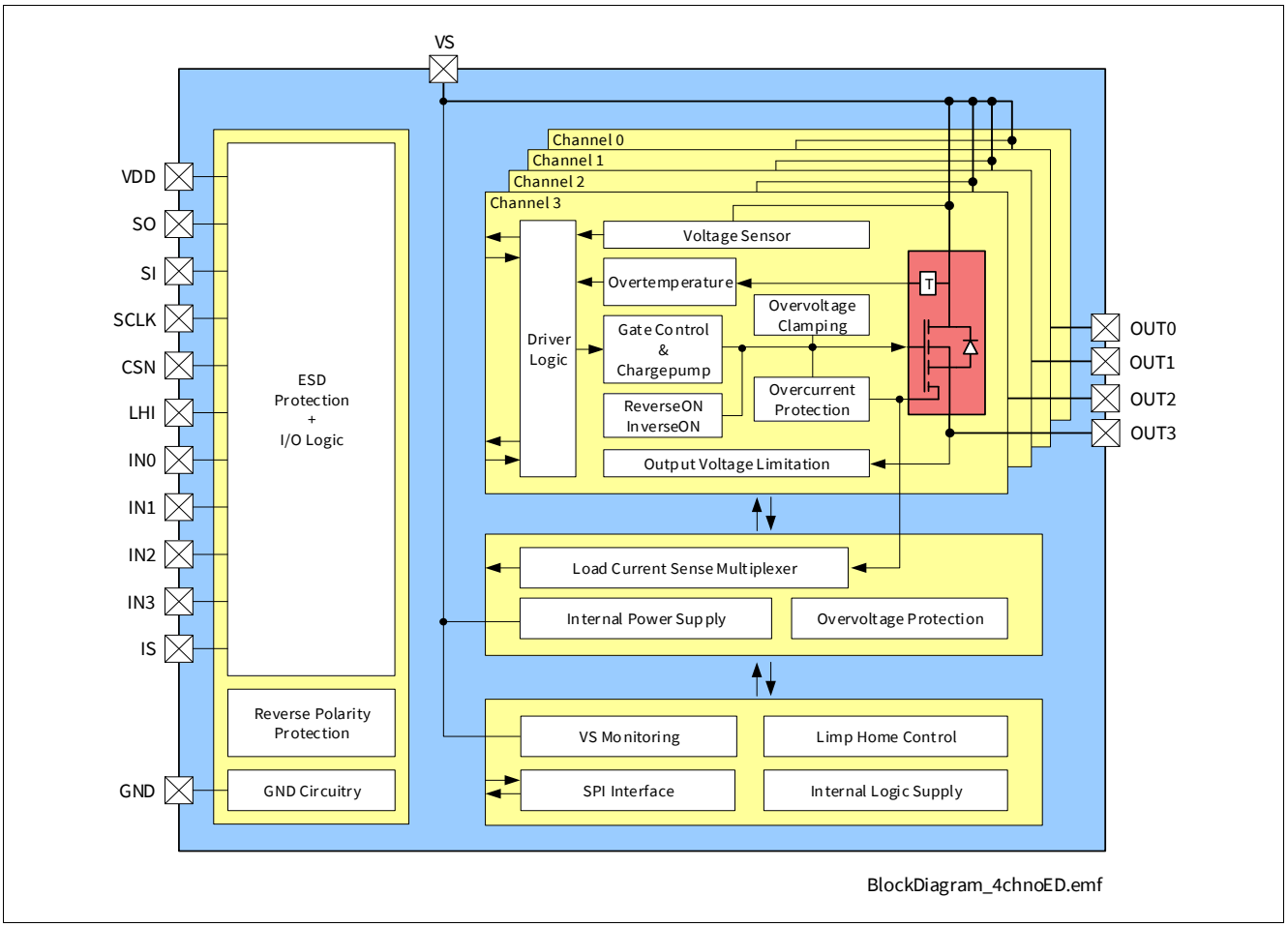



**Figure 2 Block Diagram of BTS71040-4ESP**

## 2.2 Terms

**Figure 3** shows all terms used in this data sheet, with associated convention for positive values.

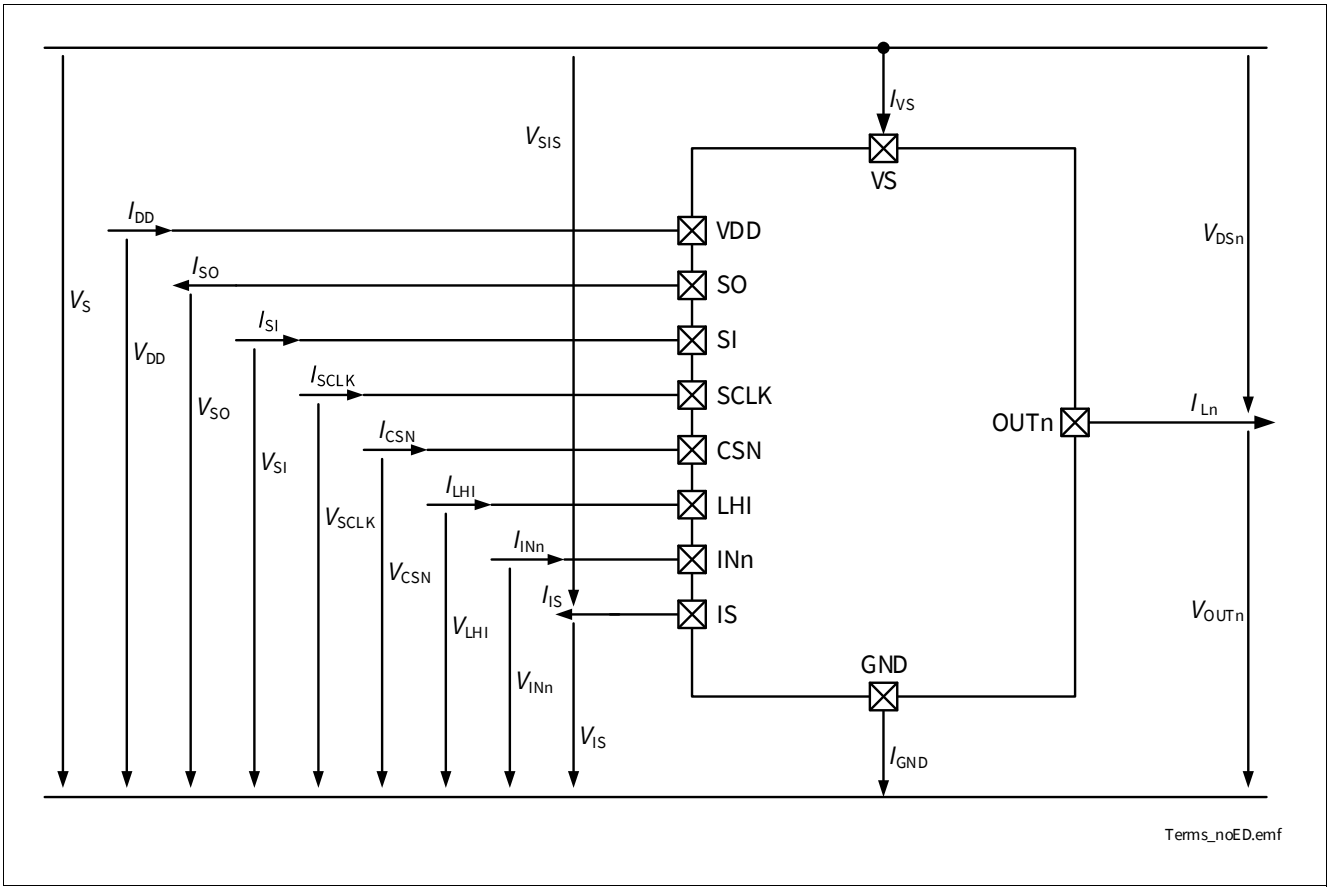



**Figure 3 Voltage and Current Convention**

# 3 Pin Configuration

## 3.1 Pin Assignment

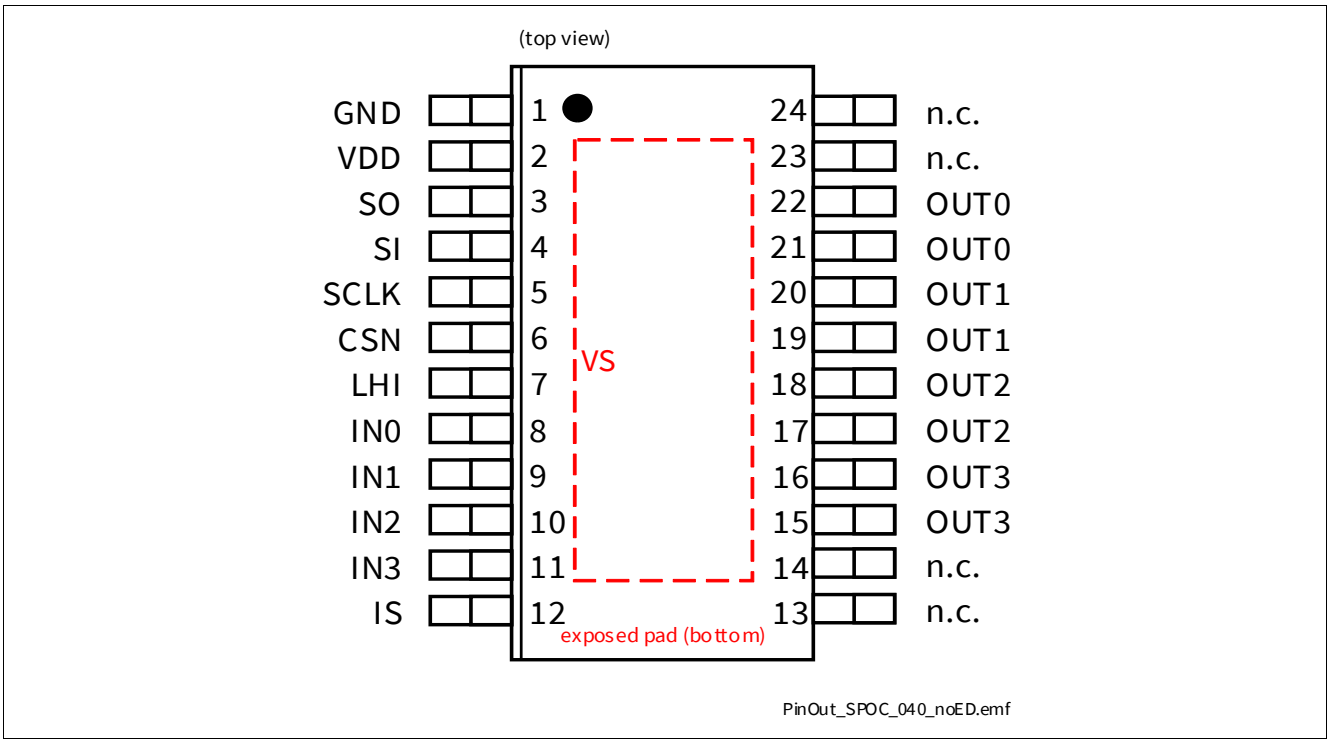



**Figure 4 Pin Configuration**

## 3.2 Pin Definitions and Functions

**Table 2 Pin Definition**

| Pin | Symbol | I/O | Function |
|---|---|---|---|
| EP | VS<br>(exposed pad) | - | **Power Supply Voltage**<br>Battery voltage |
| 1 | GND | - | **Ground** |
| 2 | VDD | - | **Digital Supply Voltage** |
| 3 | SO | O | **Serial output of SPI interface** |
| 4 | SI | I | **Serial input of SPI interface (“high” active)** |
| 5 | SCLK | I | **Serial clock of SPI interface (“high” active)** |
| 6 | CSN | I | **Chip select of SPI interface (“low” active); integrated pull up to VDD** |
| 7 | LHI | I | **Limp Home activation signal (“high” active)** |
| 8, 9<br>10, 11 | INn | I | **Input Channel n**<br>Digital signal to switch ON the channel n (“high” active)<br>If not used: connect with a 10 kΩ resistor either to GND pin or to module ground |
| 12 | IS | O | **Current sense output signal** |
| 23-24 | n.c. | - | **Not connected, internally not bonded, shorted together** |
| 21-22<br>19-20<br>17-18<br>15-16 | OUTn | O | **Output n**<br>Protected high-side power output of channel n[1)] |
| 13-14 | n.c. | - | **Not connected, internally not bonded, shorted together** |

1) All output pins of the channel must be connected together on the PCB. All pins of the output are internally connected together. PCB traces have to be designed to withstand the maximum current which can flow.

# 4 General Product Characteristics

## 4.1 Absolute Maximum Ratings - General

**Table 3 Absolute Maximum Ratings[1)]**

$T_J$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Supply pins** | | | | | | | |
| Power Supply Voltage | $V_S$ | -0.3 | – | 28 | V | – | P_4.1.0.1 |
| Digital Supply Voltage | $V_{DD}$ | -0.3 | – | 5.5 | V | – | P_4.1.0.29 |
| Load Dump Voltage | $V_{BAT(LD)}$ | – | – | 35 | V | suppressed Load Dump acc. to ISO16750-2 (2010). $R_i$ = 2 Ω | P_4.1.0.3 |
| Supply Voltage for Short Circuit Protection | $V_{BAT(SC)}$ | 0 | – | 24 | V | Setup acc. to AEC-Q100-012 | P_4.1.0.25 |
| Reverse Polarity Voltage | $-V_{BAT(REV)}$ | – | – | 16 | V | $t \le 2$ min $T_A$ = +25 °C Setup as described in **Chapter 11** | P_4.1.0.5 |
| Current through GND Pin | $I_{GND}$ | -50 | – | 50 | mA | $R_{GND}$ according to **Chapter 11** | P_4.1.0.9 |
| Current through VDD Pin | $I_{VDD(REV)}$ | -10 | – | 30 | mA | $t \le 2$ min | P_4.1.0.10 |
| Counter Reset Delay Time after Fault Condition | $t_{RETRY}$ | 50 | – | – | ms | – | P_4.1.0.35 |
| **Logic & control pins (Digital Input = DI) DI = INn, CS, SCLK, SI, LHI** | | | | | | | |
| Current through DI Pin | $I_{DI}$ | -1 | – | 2 | mA | 2) | P_4.1.0.14 |
| Current through DI Pin Reverse Battery Condition | $I_{DI(REV)}$ | -1 | – | 10 | mA | 2) $t \le 2$ min | P_4.1.0.36 |
| **Logic & control pins (Digital Output = DO) DO = SO** | | | | | | | |
| Current through DO Pin | $I_{DO}$ | -2 | – | 1 | mA | 2) | P_4.1.0.33 |
| Current through DO Pin Reverse Battery Condition | $I_{DO(REV)}$ | -10 | – | 1 | mA | 2) $t \le 2$ min | P_4.1.0.37 |

**Table 3 Absolute Maximum Ratings[1)]** (continued)

$T_J$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **IS pin** | | | | | | | |
| Voltage at IS Pin | $V_{IS}$ | -1.5 | – | $V_S$ | V | $I_{IS}$ = 10 µA | P_4.1.0.16 |
| Current through IS Pin | $I_{IS}$ | -25 | – | $I_{IS(SAT),MAX}$ | mA | – | P_4.1.0.18 |
| **Temperatures** | | | | | | | |
| Junction Temperature | $T_J$ | -40 | – | 150 | °C | – | P_4.1.0.19 |
| Storage Temperature | $T_{STG}$ | -55 | – | 150 | °C | – | P_4.1.0.20 |
| **ESD Susceptibility** | | | | | | | |
| ESD Susceptibility all Pins (HBM) | $V_{ESD(HBM)}$ | -2 | – | 2 | kV | HBM[3)] | P_4.1.0.21 |
| ESD Susceptibility OUTn vs GND and VS connected (HBM) | $V_{ESD(HBM)\_OUT}$ | -4 | – | 4 | kV | HBM[3)] | P_4.1.0.22 |
| ESD Susceptibility all Pins (CDM) | $V_{ESD(CDM)}$ | -500 | – | 500 | V | CDM[4)] | P_4.1.0.23 |
| ESD Susceptibility Corner Pins (pins 1, 12, 13, 24) | $V_{ESD(CDM)\_CRN}$ | -750 | – | 750 | V | CDM[4)] | P_4.1.0.24 |

1) Not subject to production test - specified by design.
2) Maximum $V_{DI}$ to be considered for Latch-Up tests: 5.5 V.
3) ESD susceptibility, Human Body Model "HBM", according to AEC Q100-002.
4) ESD susceptibility, Charged Device Model "CDM", according to AEC Q100-011.

**Notes**

1. *Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*
2. *Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as “outside” normal operating range. Protection functions are not designed for continuous repetitive operation.*

## 4.2 Absolute Maximum Ratings - Power Stages

### 4.2.1 Power Stages - 22.5 mΩ channels

**Table 4 Absolute Maximum Ratings - 22.5 mΩ channels[1)]**

$T_J$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Maximum Energy Dissipation Single Pulse | $E_{AS}$ | – | – | 28 | mJ | $I_L = 2^* I_{L(NOM)}$<br>$T_{J(0)}$ = 150 °C<br>$V_S$ = 28 V | P_4.2.16.1 |
| Maximum Energy Dissipation Repetitive Pulse | $E_{AR}$ | – | – | 8.5 | mJ | $I_L = I_{L(NOM)}$<br>$T_{J(0)}$ = 85 °C<br>$V_S$ = 13.5 V<br>1M cycles | P_4.2.16.2 |
| Load Current | $\|I_L\|$ | – | – | $I_{L(OVL),MAX}$ | A | – | P_4.2.16.3 |

1) Not subject to production test - specified by design.

## 4.3 Functional Range

**Table 5 Functional Range - Supply Voltages and Temperature[1)]**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Power Supply Voltage Range for Normal Operation | $V_{S(NOR)}$ | 6 | 13.5 | 18 | V | – | P_4.3.0.1 |
| Lower Extended Power Supply Voltage Range for Operation | $V_{S(EXT,LOW)}$ | 3.1 | – | 6 | V | 2)3) (parameter deviations possible) | P_4.3.0.2 |
| Upper Extended Power Supply Voltage Range for Operation | $V_{S(EXT,UP)}$ | 18 | – | 28 | V | 3) (parameter deviations possible) | P_4.3.0.3 |
| Digital Supply Voltage Range | $V_{DD(NOR)}$ | 3.0 | – | 5.5 | V | – | P_4.3.0.4 |
| Junction Temperature | $T_J$ | -40 | – | 150 | °C | – | P_4.3.0.5 |

1) Not subject to production test - specified by design.
2) In case of $V_S$ voltage decreasing: $V_{S(EXT,LOW),MIN}$ = 3.1 V. In case of $V_S$ voltage increasing: $V_{S(EXT,LOW),MIN}$ = 4.1 V.
3) Protection functions still operative.

*Note: Within the functional or operating range, the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the Electrical Characteristics tables.*

## 4.4 Thermal Resistance

*Note: This thermal data was generated in accordance with JEDEC JESD51 standards. For more information, go to **www.jedec.org**.*

**Table 6 Thermal Resistance[1)]**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Thermal Characterization Parameter Junction-Top | $\Psi_{JTOP}$ | – | 0.9 | 1.5 | K/W | 2) | P_4.4.0.17 |
| Thermal Resistance Junction-to-Case | $R_{thJC}$ | – | 0.5 | 0.9 | K/W | 2) simulated at exposed pad | P_4.4.0.18 |
| Thermal Resistance Junction to Ambient | $R_{thJA}$ | – | 26.5 | – | K/W | 2) | P_4.4.0.10 |

1) Not subject to production test - specified by design.
2) According to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board; the Product (Chip + Package) was simulated on a 76.2 × 114.3 × 1.5 mm board with 2 inner copper layers (2 × 70 µm Cu, 2 × 35 µm Cu). Where applicable a thermal via array under the exposed pad contacted the first inner copper layer. Simulation done at $T_A$ = 105°C, $P_{DISSIPATION}$ = 1 W.

### 4.4.1 PCB Setup

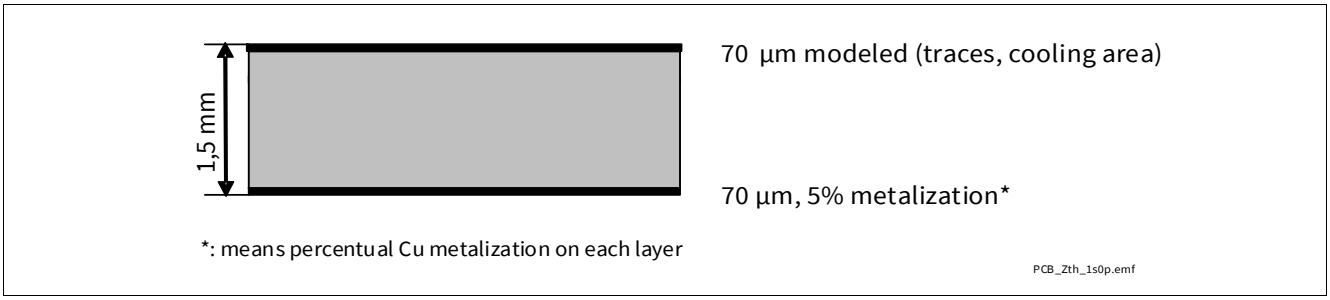



**Figure 5 1s0p PCB Cross Section**

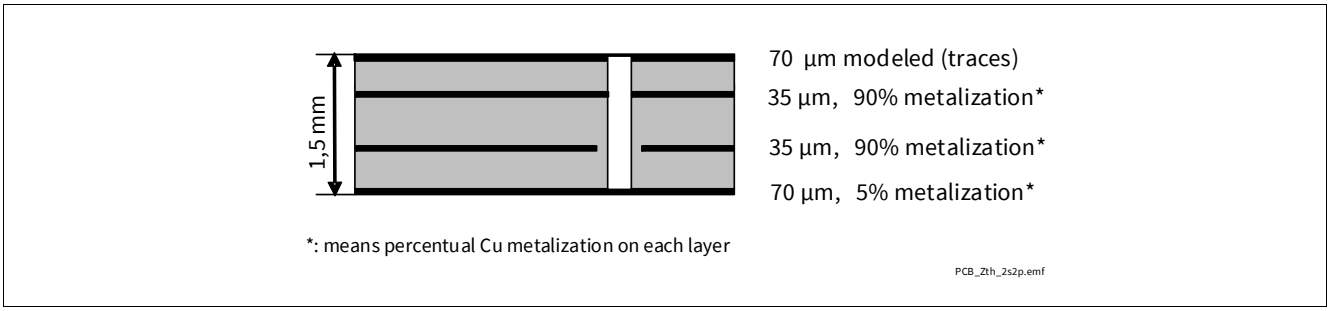



**Figure 6 2s2p PCB Cross Section**

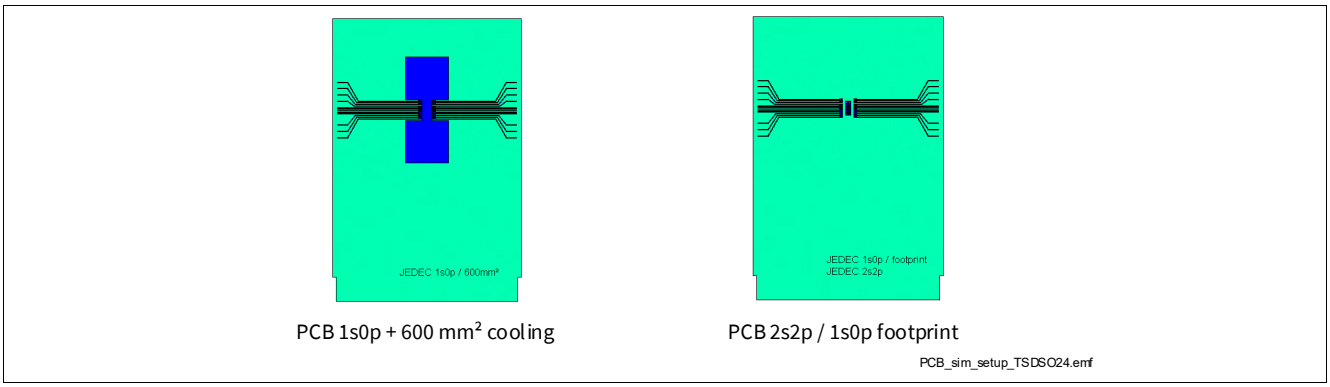



**Figure 7 PCB setup for thermal simulations**

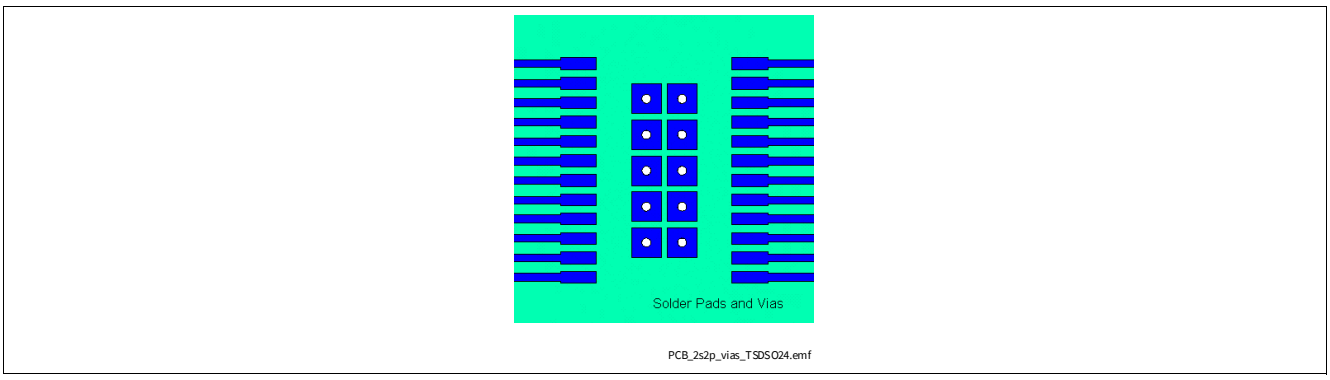



**Figure 8 Thermal vias on PCB for 2s2p PCB setup**

## 4.4.2 Thermal Impedance

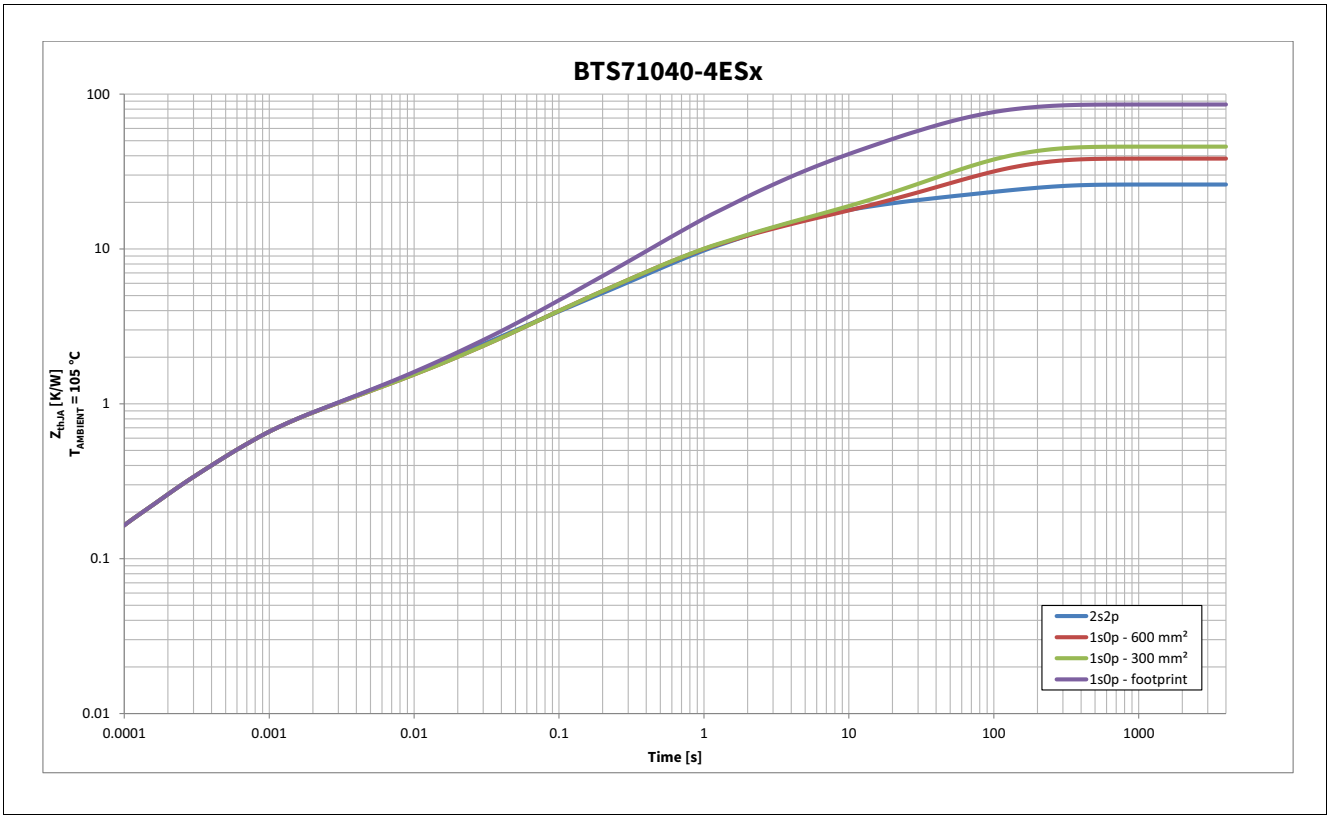



**Figure 9 Typical Thermal Impedance. PCB setup according Chapter 4.4.1**

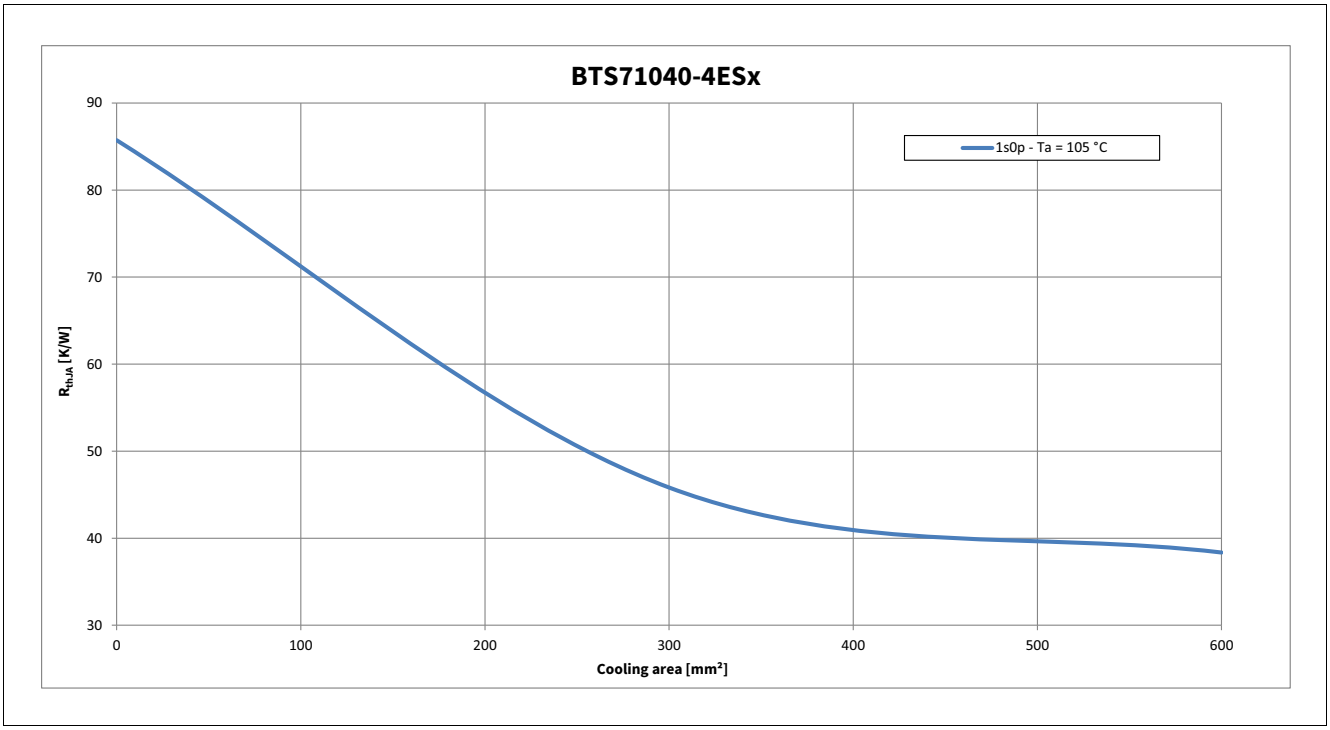



**Figure 10 Thermal Resistance on 1s0p PCB with various cooling surfaces**

# 5 Logic Pins

The device has 9 digital pins to configure and control the device. They can be grouped based on their function into input pins, SPI pins and Limp Home pin.

## 5.1 Input Pins (INn)

The input pins IN0 to IN3 activate the corresponding output channel, if the device is either in Sleep, Stand-by, Ready or in Limp Home mode. The input circuitry is compatible with 3.3V and 5V microcontroller. The electrical equivalent of the input circuitry is shown in **Figure 11**. In case the pin is not used, it must be connected with a 10 kΩ resistor either to GND pin or to module ground.

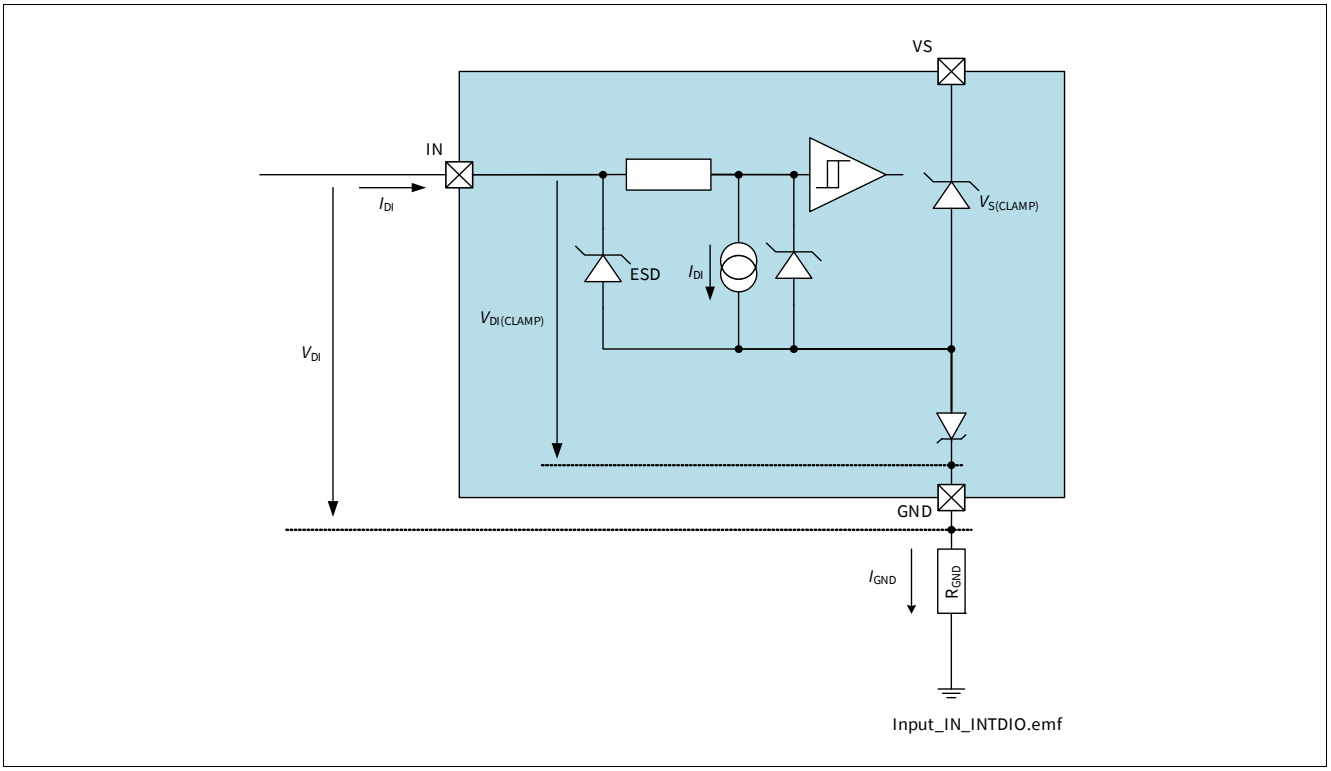



**Figure 11 Input circuitry**

The logic thresholds for “low” and “high” states are defined by parameters $V_{DI(TH)}$ and $V_{DI(HYS)}$. The relationship between these two values is shown in **Figure 12**. The voltage $V_{IN}$ needed to ensure a “high” state is always higher than the voltage needed to ensure a “low” state.

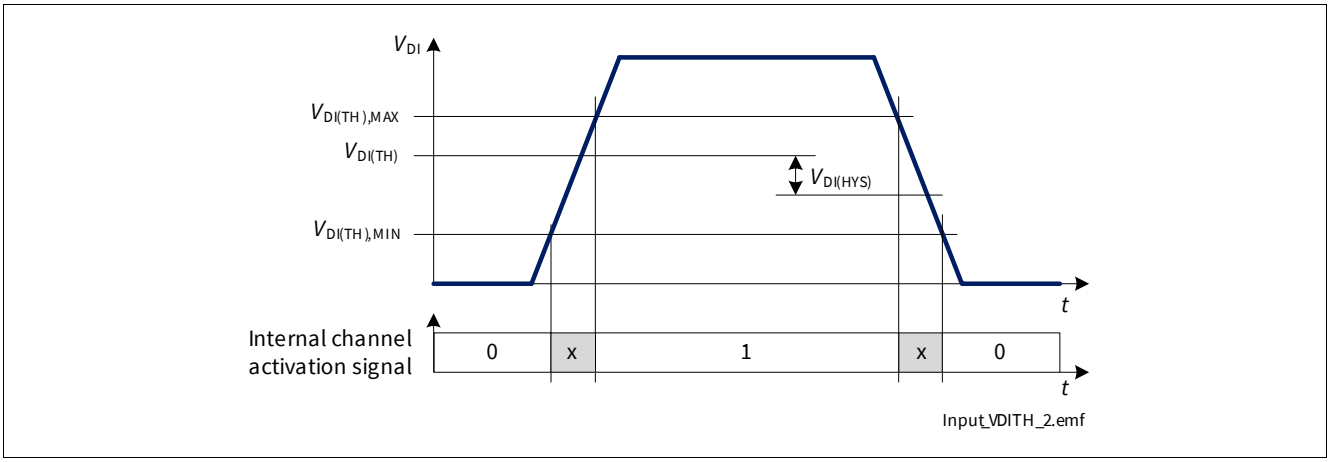



**Figure 12 Input Threshold voltages and hysteresis**

There are two ways of using the input pins in combination with the register **OUT** by programming bit **HWCR.COL** in register **HWCR** (see **Table 30**).

- **HWCR.COL** = $0_B$: A channel is switched ON either by the according **OUT.OUTn** bit or by the input pin.
- **HWCR.COL** = $1_B$: A channel is switched ON by the according **OUT.OUTn** bit only, when the input pin is “high”. In this configuration, a PWM signal can be applied to the input pin and the channel is activated by the SPI register **OUT** (see **Table 30**).

The default state (**HWCR.COL** = $0_B$) is the OR-combination of the input signal and the SPI-bit. In Limp Home mode (LHI pin set to “high”) the combinatorial logic is in default state to enable a channel activation via the input pins only. **Figure 13** shows the complete input switch matrix.

The logic level of the input pins can be monitored via the input status monitor. In case of a “high” level on an input pin, the corresponding **ICS.INSTn** bit is set and cleared on read.

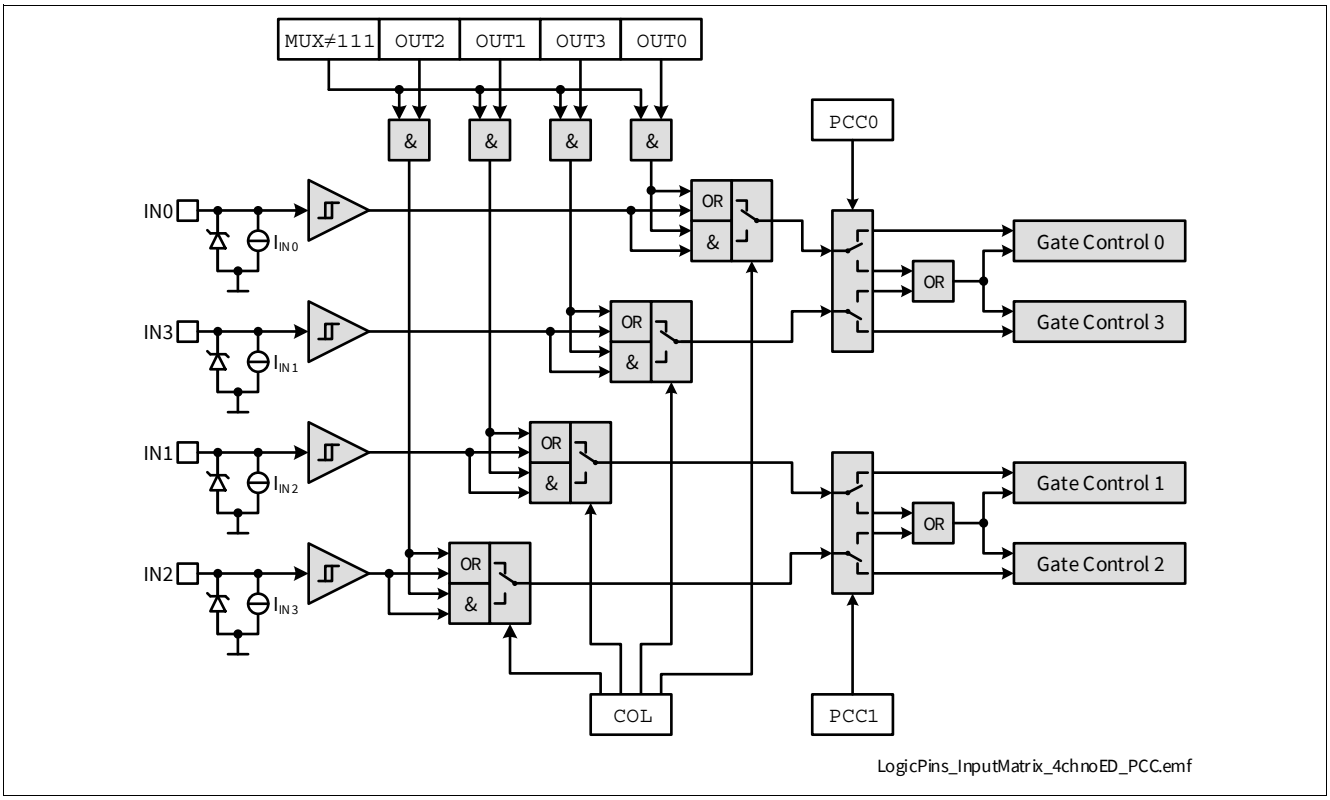



**Figure 13 Input Switch Matrix**

## 5.2 Advanced Features Pins

### 5.2.1 SPI Pins

The serial peripheral interface (SPI) is a full duplex synchronous serial slave interface, which uses four lines: SO, SI, SCLK and CSN. See **Chapter 10** for further information.

### 5.2.2 Limp Home Input (LHI) Pin

For activating the fail-safe state, the device features a Limp Home Input pin. When the pin is set to “high” for a time longer than $t_{LHI(AC)}$, the Limp Home mode will be activated. See **Chapter 6.1.7** and **Chapter 6.1.8** for further information.

## 5.3 Electrical Characteristics Logic Pins

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C
Digital Input (DI) pins = IN

**Table 7 Electrical Characteristics: Logic Pins - General**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Digital Input Voltage Threshold | $V_{DI(TH)}$ | 0.8 | 1.3 | 2 | V | See **Figure 11** and **Figure 12** | P_5.4.0.1 |
| Digital Input Clamping Voltage | $V_{DI(CLAMP1)}$ | – | 7 | – | V | 1) $I_{DI}$ = 1 mA See **Figure 11** and **Figure 12** | P_5.4.0.2 |
| Digital Input Clamping Voltage | $V_{DI(CLAMP2)}$ | 6.5 | 7.5 | 8.5 | V | $I_{DI}$ = 2 mA See **Figure 11** and **Figure 12** | P_5.4.0.3 |
| Digital Input Hysteresis | $V_{DI(HYS)}$ | – | 0.25 | – | V | 1) See **Figure 11** and **Figure 12** | P_5.4.0.4 |
| Digital Input Current (“high”) | $I_{DI(H)}$ | 2 | 10 | 25 | µA | $V_{DI}$ = 2 V See **Figure 11** and **Figure 12** | P_5.4.0.5 |
| Digital Input Current (“low”) | $I_{DI(L)}$ | 2 | 10 | 25 | µA | $V_{DI}$ = 0.8 V See **Figure 11** and **Figure 12** | P_5.4.0.6 |

1) Not subject to production test - specified by design.

## 5.4 Electrical Characteristics Logic Pins - Advanced Features

**Table 8 Electrical Characteristics: Logic Pins - Advanced**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **SPI pins** | | | | | | | |
| Digital Input Voltage Threshold of Pin CSN | $V_{CSN(TH)}$ | 0.8 | 1.3 | 2 | V | – | P_5.5.0.1 |
| Digital Input Voltage Threshold of Pin SCLK | $V_{SCLK(TH)}$ | 0.8 | 1.3 | 2 | V | 1) | P_5.5.0.2 |
| Digital Input Voltage Threshold of Pin SI | $V_{SI(TH)}$ | 0.8 | 1.3 | 2 | V | – | P_5.5.0.3 |
| Digital Input Clamping Voltage of Pin CSN | $V_{CSN(CLAMP1)}$ | – | 7 | – | V | 2) $I_{CSN}$ = 1 mA | P_5.5.0.4 |
| Digital Input Clamping Voltage of Pin CSN | $V_{CSN(CLAMP2)}$ | 6.5 | 7.5 | 8.5 | V | $I_{CSN}$ = 2 mA | P_5.5.0.5 |

## Logic Pins

**Table 8 Electrical Characteristics: Logic Pins - Advanced** (continued)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Digital Input Clamping Voltage of Pin SCLK | $V_{SCLK(CLAMP1)}$ | – | 7 | – | V | [2] $I_{SCLK}$ = 1 mA | P_5.5.0.6 |
| Digital Input Clamping Voltage of Pin SCLK | $V_{SCLK(CLAMP2)}$ | 6.5 | 7.5 | 8.5 | V | $I_{SCLK}$ = 2 mA | P_5.5.0.7 |
| Digital Input Clamping Voltage of Pin SI | $V_{SI(CLAMP1)}$ | – | 7 | – | V | [2] $I_{SI}$ = 1 mA | P_5.5.0.8 |
| Digital Input Clamping Voltage of Pin SI | $V_{SI(CLAMP2)}$ | 6.5 | 7.5 | 8.5 | V | $I_{SI}$ = 2 mA | P_5.5.0.9 |
| Digital Input Hysteresis of Pin CSN | $V_{CSN(HYS)}$ | – | 0.25 | – | V | [2] See **Figure 12** | P_5.5.0.11 |
| Digital Input Hysteresis of Pin SCLK | $V_{SCLK(HYS)}$ | – | 0.25 | – | V | [2] See **Figure 12** | P_5.5.0.13 |
| Digital Input Hysteresis of Pin SI | $V_{SI(HYS)}$ | – | 0.25 | – | V | [2] See **Figure 12** | P_5.5.0.15 |
| Digital Input Current (“low”) of Pin CSN | $-I_{CSN(L)}$ | 2 | 10 | 25 | µA | $V_{CSN}$ = 0.5 V | P_5.5.0.10 |
| Digital Input Current (“high”) of Pin CSN | $-I_{CSN(H)}$ | 2 | 10 | 25 | µA | $V_{CSN}$ = 2.6 V | P_5.5.0.12 |
| Digital Input Current (“low”) of Pin SCLK | $I_{SCLK(L)}$ | 2 | 10 | 25 | µA | $V_{SCLK}$ = 0.5 V | P_5.5.0.14 |
| Digital Input Current (“high”) of Pin SCLK | $I_{SCLK(H)}$ | 2 | 10 | 25 | µA | $V_{SCLK}$ = 2.6 V | P_5.5.0.16 |
| Digital Input Current (“low”) of Pin SI | $I_{SI(L)}$ | 2 | 10 | 25 | µA | $V_{SI}$ = 0.5 V | P_5.5.0.18 |
| Digital Input Current (“high”) of Pin SI | $I_{SI(H)}$ | 2 | 10 | 25 | µA | $V_{SI}$ = 2.6 V | P_5.5.0.20 |
| Digital Output Voltage (“low”) of Pin SO | $V_{SO(L)}$ | 0 | – | 0.5 | V | $I_{SO}$ = -0.5 mA | P_5.5.0.22 |
| Digital Output Voltage (“high”) of Pin SO | $V_{SO(H)}$ | $V_{DD}$ - 0.5 V | – | $V_{DD}$ | V | $I_{SO}$ = 0.5 mA | P_5.5.0.23 |
| Output Tristate Leakage Current of Pin SO | $I_{SO(OFF)}$ | -1 | – | 1 | µA | $V_{CSN}$ = $V_{DD}$ $V_{SO}$ = 0 V or $V_{CSN}$ = $V_{DD}$ $V_{SO}$ = $V_{DD}$ | P_5.5.0.24 |
| **LHI pin** | | | | | | | |
| Digital Input Voltage Threshold of Pin LHI | $V_{LHI(TH)}$ | 1.4 | 1.9 | 2.6 | V | – | P_5.5.0.25 |
| Digital Input Clamping Voltage of Pin LHI | $V_{LHI(CLAMP1)}$ | – | 7 | – | V | [2] $I_{LHI}$ = 1 mA | P_5.5.0.27 |
| Digital Input Clamping Voltage of Pin LHI | $V_{LHI(CLAMP2)}$ | 6.5 | 7.5 | 8.5 | V | $I_{LHI}$ = 2 mA | P_5.5.0.28 |

## Logic Pins

**Table 8 Electrical Characteristics: Logic Pins - Advanced** (continued)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Digital Input Hysteresis of Pin LHI | $V_{LHI(HYS)}$ | – | 0.25 | – | V | 2) | P_5.5.0.29 |
| Digital Input Current (“high”) of Pin LHI | $I_{LHI(H)}$ | 10 | 32 | 65 | µA | $V_{LHI}$ = 5 V<br>$V_{DD}$ = 0 V | P_5.5.0.30 |
| Digital Input Current (“low”) of Pin LHI | $I_{LHI(L)}$ | 10 | 24 | 45 | µA | $V_{LHI}$ = 0.8 V<br>$V_{DD}$ = 0 V | P_5.5.0.32 |

1) Functional test only.
2) Not subject to production test - specified by design.

# 6 Power Supply

The BTS71040-4ESP is supplied by two supply voltages:

- Power Supply Voltage ($V_S$)
- Digital Supply Voltage ($V_{DD}$)

The $V_S$ supply line is connected to a battery feed and used for the driving circuitry of the power stages, while $V_{DD}$ is used for the SPI logic and for driving SO pin. $V_S$ and $V_{DD}$ supply voltages have an undervoltage detection circuit, which prevents the activation of the associated function in case the measured voltage is below the undervoltage threshold. More in detail:

- An undervoltage on $V_{DD}$ supply prevents SPI communication. SPI registers are reset to their default values
- An undervoltage on $V_S$ supply switches OFF all channels, even in Limp Home mode. The channels are enabled again as soon as $V_S \geq V_{S(OP)}$

The voltage at pin $V_S$ is also monitored. In case of a negative voltage transient on $V_S$ resulting in $V_S < V_{S(TP)}$ when the device is out of Sleep mode, any SPI command sent by the microcontroller is not accepted (see **Chapter 6.2** and **Chapter 10.5** for further information). An overview of channel behavior according to different $V_S$ and $V_{DD}$ supply voltages is shown in **Table 9**.

**Table 9 Device capability as function of $V_S$ and $V_{DD}$[1)]**

| | $V_{DD} \leq V_{DD(PO)}$ ($V_{DD(PO)}$ see P_6.4.1.1) | $V_{DD} > V_{DD(PO)}$ |
|---|---|---|
| $V_S \leq V_{S(TP)}$ ($V_{S(TP)}$ see P_6.4.0.5) | Channels are OFF | Channels are OFF |
| | SPI registers reset | SPI registers protected |
| | SPI communication not available ($f_{SCLK}$ = 0 MHz) | SPI communication available[2)] ($f_{SCLK}$ = 5 MHz) |
| | Limp Home mode not available | Limp Home mode not available |
| $V_{S(TP)} < V_S \leq V_{S(UV)}$ ($V_{S(UV)}$ see P_6.4.0.1) | Channels are OFF | Channels are OFF |
| | SPI registers reset | SPI registers available |
| | SPI communication not available ($f_{SCLK}$ = 0 MHz) | SPI communication available ($f_{SCLK}$ = 5 MHz) |
| | Limp Home mode available (channels are OFF) | Limp Home mode available (channels are OFF) |
| $V_S > V_{S(UV)}$[3)] | Channels cannot be controlled by SPI | Channels can be controlled by SPI |
| | SPI registers reset | SPI registers available |
| | SPI communication not available ($f_{SCLK}$ = 0 MHz) | SPI communication available ($f_{SCLK}$ = 5 MHz) |
| | Limp Home mode available | Limp Home mode available |

1) Valid after a successful supply voltage ramp-up.
2) Write commands are ignored. Furthermore the device responds with `STDDIAG` only.
3) The undervoltage condition on VS supply must be considered. See **Chapter 6.2**.

## 6.1 Operation Modes

BTS71040-4ESP has the following operation modes:

- Sleep mode
- Active mode
- Stand-by mode
- Ready mode
- Limp Home mode
- Limp Home Active mode

The transition between operation modes is determined according to these variables:

- Digital supply level ($V_{DD}$)
- Logic level at INn pins
- Logic level at LHI pin
- Current sense multiplexer state (**DCR.MUX**)
- Output register state (**OUT.OUTn**)
- Configuration registers state

The state diagram including the possible transitions is shown in **Figure 14**. The behavior of BTS71040-4ESP as well as some parameters may change in dependence from the operation mode of the device. Furthermore, due to the undervoltage detection circuitry which monitors $V_S$ supply voltage, some changes within the same operation mode can be seen accordingly.

There are five parameters describing each operation mode of BTS71040-4ESP:

- Status of the output channels
- Status of SPI registers
- Status of SPI communication
- Current consumption at VS pin (measured by $I_{VS}$ in Sleep mode, $I_{GND}$ in all other operative modes)
- Current consumption at VDD pin ($I_{VDD}$)

**Table 10** shows the correlation between operation modes, $V_S$ and $V_{DD}$ supply voltages, and the state of the most important functions (channel status, SPI communication and SPI registers).

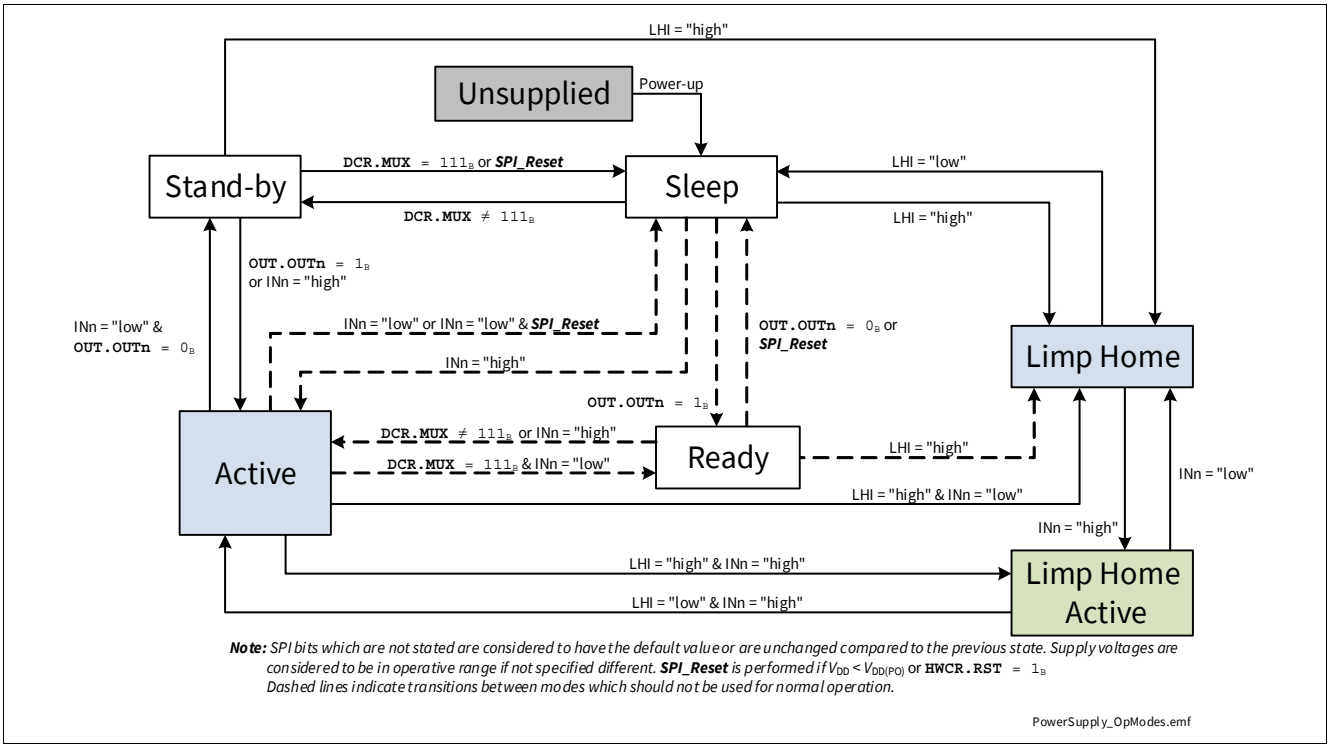



**Figure 14 Operation Mode state diagram**

**Table 10 Device function in relation to operation modes, $V_{DD}$ and $V_S$ voltages**

| Operative Mode | Function | $V_S \le V_{S(TP)}$ | $V_{S(TP)} \le V_S \le V_{S(UV)}$ | $V_S > V_{S(UV)}$ |
|---|---|---|---|---|
| Sleep | Channels | OFF | OFF | OFF |
| | SPI registers | available[1)] | available[1)] | available[1)] |
| | SPI comm. | available[1)] | available[1)] | available[1)] |
| Stand-by | Channels | OFF | OFF | OFF |
| | SPI registers | protected[1)] | available[1)] | available[1)] |
| | SPI comm. | all commands rejected[1)] | available[1)] | available[1)] |
| Ready | Channels | OFF | OFF | OFF |
| | SPI registers | protected[1)] | available[1)] | available[1)] |
| | SPI comm. | all commands rejected[1)] | available[1)] | available[1)] |
| Active | Channels | OFF | OFF | follow SPI and/or Input pins |
| | SPI registers | protected[1)] | available[1)] | available[1)] |
| | SPI comm. | all commands rejected[1)] | available[1)] | available[1)] |
| Limp Home / Limp Home Active | Channels | OFF | OFF | follow Input pins |
| | SPI registers | protected[1)] | reset (Diagnosis available)[1)] | reset (Diagnosis available)[1)] |
| | SPI comm. | all commands rejected[1)2)] | read-only[1)] | read-only[1)] |

1) In case $V_{DD} > V_{DD(PO)}$ otherwise not available or in reset.
2) In case all input pins are set to “low”, SPI communication is in read-only mode.

### 6.1.1 Unsupplied

In this state, the device is either unsupplied (no voltage applied to VS pin and VDD pin) or the supply voltages are both below the corresponding undervoltage threshold.

### 6.1.2 Power-up

The Power-up condition is entered when one of the supply voltages ($V_S$ or $V_{DD}$) is applied to the device. Both supplies are rising until they are above the undervoltage thresholds $V_{S(OP)}$ and $V_{DD(PO)}$ therefore the internal Power-On signals are set. The SPI interface can be accessed after wake up time $t_{WU(PO)}$.

### 6.1.3 Sleep mode

The device is in Sleep mode when all Digital Input pins (INn, LHI) are set to “low” and **DCR.MUX** is still set to $111_B$. When BTS71040-4ESP is in Sleep mode, all outputs are OFF. The SPI registers can be programmed if $V_{DD} > V_{DD(PO)}$. The current consumption is minimum (see parameter $I_{VS(SLEEP)}$). No Overtemperature or Overload protection mechanism is active when the device is in Sleep mode. The circuitry that monitors $V_S$ versus $V_{S(UV)}$ and $V_S$ versus $V_{S(TP)}$ is disabled. This allows the programming of the registers even if $V_S < V_{S(TP)}$.

### 6.1.4 Stand-by mode

The device is in Stand-by mode when **DCR.MUX** $\neq 111_B$ and no command to switch ON a channel was received (either via SPI or via Input pins). All channels are OFF but the internal supply circuitry is working and therefore the device current consumption is increased. A command to switch ON one or more outputs is accepted and executed, bringing the device into Active mode. SPI communication is possible.

### 6.1.5 Ready mode

In Ready mode, one or more outputs received a command to switch ON (either via SPI or via Input pins if **HWCR.COL** = $1_B$). Nevertheless, all outputs are OFF because of **DCR.MUX** bits still set to $111_B$. It is necessary to change the value of those bits to bring the device into Active mode and switch ON the channels.

*Note: Since **OUT** register is blanked with **DCR.MUX** = $111_B$ it is not possible to enter Active mode when **HWCR.COL** bit is set to $1_B$.*

### 6.1.6 Active mode

Active mode is the normal operation mode of BTS71040-4ESP when no Limp Home condition is set and one or more outputs are switched ON. Device current consumption is specified by parameter $I_{GND(ACTIVE)}$. An undervoltage condition on $V_{DD}$ supply voltage brings the device into Sleep mode in case all Input pins are set to “low”.

### 6.1.7 Limp Home mode

The device enters Limp Home mode when LHI pin is set to “high” for $t > t_{LHI(AC)}$. SPI registers are reset to the default values when Limp Home mode is entered. The corresponding bit in the standard diagnosis (**STDDIAG.LHI**) will be set to $1_B$ once the LHI pin is set to “high” and latched until next **STDDIAG** transmission. See **Figure 15** for further information. SPI registers are available for read access. ERRDIAG, STDDIAG, WRNDIAG and ICS can be used for diagnosis in Limp Home.

When the device is in transient protection ($V_S \leq V_{S(TP)}$) and the LHI pin is set to "high", the **STDDIAG.LHI** bit will be set but the device will not change its state to Limp Home mode. Furthermore **STDDIAG.VSMON** and **STDDIAG.TER** bits will be set to report the battery transient protection.

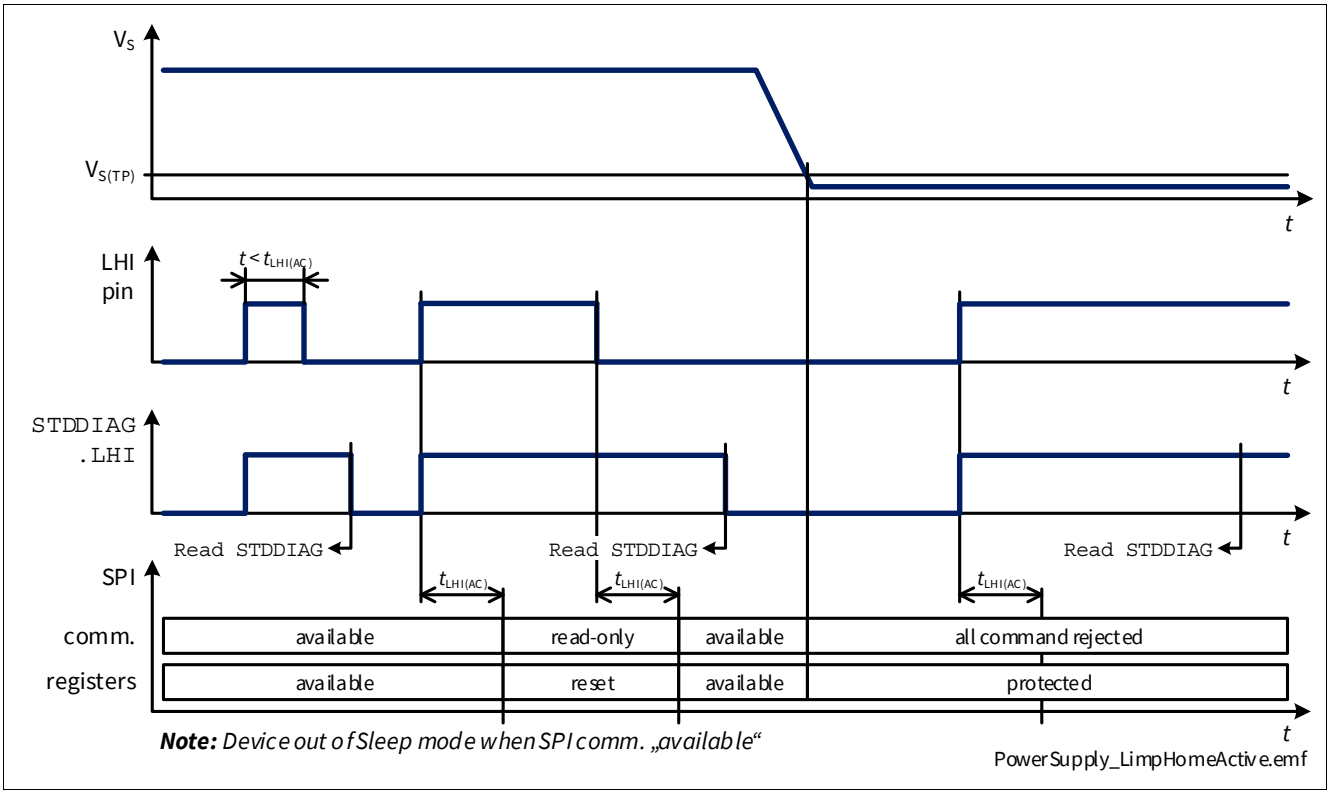



**Figure 15 Limp Home Activation as function of $V_S$**

### 6.1.8 Limp Home Active mode

Limp Home Active mode is entered when the device is in Limp Home mode and one of the IN pins is set to “high”. Overload, Overtemperature and Overvoltage protections are active. Since SPI registers cannot be written current sensing is not available.

### 6.1.9 Definition of Operation modes transition times

The channel turn-ON time is as defined by parameter $t_{ON}$ when BTS71040-4ESP is in Active mode or in Limp Home mode. In all other cases, it is necessary to add the transition time required to reach one of the two aforementioned operation modes (as shown in **Figure 16**).

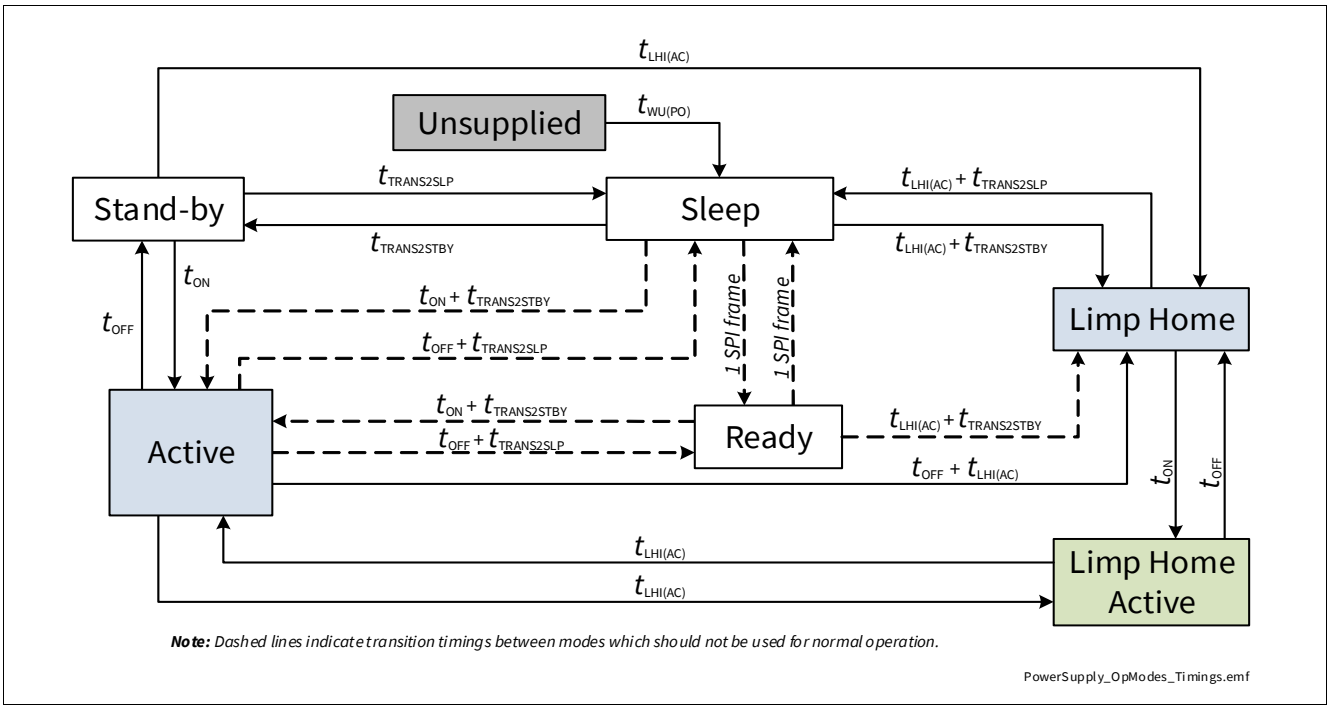



**Figure 16 Transition Time diagram**

## 6.2 Undervoltage on $V_S$

Between $V_{S(OP)}$ and $V_{S(UV)}$ the undervoltage mechanism is triggered. If the device is operative (in Active or Limp Home Active mode) and the supply voltage drops below the undervoltage threshold $V_{S(UV)}$, the internal logic switches OFF the output channels. When the device is either in Stand-by, Active or Limp Home mode the bit **STDDIAG.VSMON** is set and latched until readout. When the state is changed from Sleep to any other state, a delay of t ≥ $t_{TRANS2STBY}$ has to be considered until **STDDIAG.VSMON** is valid.

As soon as the supply voltage $V_S$ is above the operative threshold $V_{S(OP)}$, the channels having the corresponding input pin set to “high” or the bit in the **OUT** register set to $1_B$ are switched ON again.

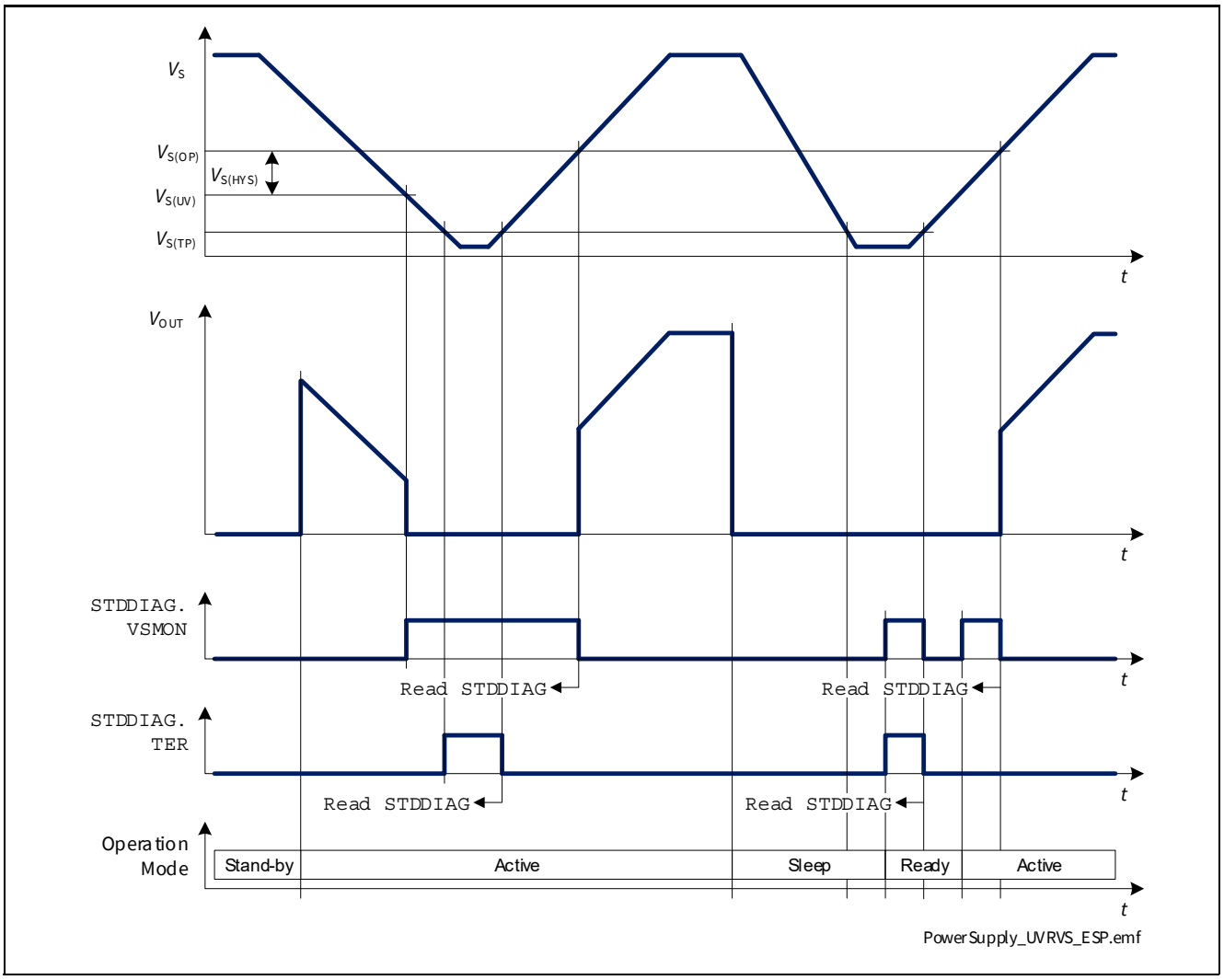



**Figure 17 $V_S$ undervoltage behavior**

## 6.3 Reset Condition

One of the following conditions reset the SPI registers to their default value:

- $V_{DD}$ is not present or below the undervoltage threshold $V_{DD(PO)}$
  - SPI registers will be reset to their default values (in the first communication after reset the **STDDIAG.TER** will be set to $1_B$).
  - Restart counters will not be reset if $V_S$ is available or LHI is "high".
- LHI pin is set to “high” for $t > t_{LHI(AC)}$ and $V_S > V_{S(TP)}$
  - Configuration registers will be reset to their default values. **ERRDIAG** and **WRNDIAG** will be reset.
  - Restart counters will be reset.
- Reset command (**HWCR.RST** = $1_B$) is executed and $V_S > V_{S(TP)}$
  - Configuration registers will be reset to their default values. **ERRDIAG**, **WRNDIAG** and **STDDIAG** will not be reset.
  - Restart counters will not be reset.

In case all Input pins are set to “low” after any reset condition, all channels are switched OFF.

## 6.4 Electrical Characteristics Power Supply

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

22.5 mΩ: $R_L$ = 4.8 Ω

**Table 11 Electrical Characteristics: Power Supply - General**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **VS pin** | | | | | | | |
| Power Supply Undervoltage Shutdown | $V_{S(UV)}$ | 1.8 | 2.3 | 3.1 | V | $V_S$ decreasing<br>IN = “high” or<br>`OUT.OUTn` = $1_B$<br>From $V_{DS} \le 0.5$ V to $V_{DS} = V_S$<br>See **Figure 17** | P_6.4.0.1 |
| Power Supply Minimum Operating Voltage | $V_{S(OP)}$ | 2.0 | 3.0 | 4.1 | V | $V_S$ increasing<br>IN = “high”or<br>`OUT.OUTn` = $1_B$<br>From $V_{DS} = V_S$ to $V_{DS} \le 0.5$ V<br>See **Figure 17** | P_6.4.0.3 |
| Power Supply Voltage Threshold for Battery Transients Protection | $V_{S(TP)}$ | 0.6 | 1.0 | 1.8 | V | $V_S$ decreasing<br>`STDDIAG.VSMON` = $1_B$<br>`STDDIAG.TER` = $1_B$<br>`DCR.MUX` ≠ $111_B$<br>See **Figure 17** | P_6.4.0.5 |
| Power Supply Undervoltage Shutdown Hysteresis | $V_{S(HYS)}$ | – | 0.7 | – | V | 1)<br>$V_{S(OP)} - V_{S(UV)}$<br>See **Figure 17** | P_6.4.0.6 |
| Breakdown Voltage between GND and VS Pins in Reverse Battery | $-V_{S(REV)}$ | 16 | – | 30 | V | 1)<br>$I_{GND(REV)}$ = 14 mA<br>$T_J$ = 150 °C | P_6.4.0.9 |

1) Not subject to production test - specified by design.

### 6.4.1 Electrical Characteristics Power Supply

**Table 12 Electrical Characteristics: Power Supply**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **VDD pin** | | | | | | | |
| Digital Supply Operating Voltage | $V_{DD(OP)}$ | 2.45 | 4.3 | 5.5 | V | 1) $f_{SCLK}$ = 5 MHz | P_6.4.1.1 |
| Digital Supply Power-On Reset Threshold Voltage | $V_{DD(PO)}$ | 1.4 | 1.9 | 2.3 | V | 1) $V_{DD}$ increasing | P_6.4.1.9 |
| Digital Supply Undervoltage Shutdown | $V_{DD(UV)}$ | 1.3 | 1.8 | 2.2 | V | $V_{DD}$ decreasing `OUT.OUTn` = $1_B$ From $V_{DS} \leq 0.5$ V to $V_{DS} = V_S$ | P_6.4.1.2 |
| Digital Supply Undervoltage Shutdown Hysteresis | $V_{DD(HYS)}$ | – | 0.1 | – | V | 1) | P_6.4.1.3 |
| Digital Supply Clamping Voltage | $V_{DD(CLAMP1)}$ | – | 6.5 | – | V | 1) $I_{DD}$ = 1 mA | P_6.4.1.11 |
| Digital Supply Clamping Voltage | $V_{DD(CLAMP2)}$ | 6 | 7 | 8 | V | $I_{DD}$ = 20 mA | P_6.4.1.12 |
| Power-On Wake Up Time | $t_{WU(PO)}$ | – | 10 | 30 | µs | 1) | P_6.4.1.13 |
| Transition Time to Stand-by Mode | $t_{TRANS2STBY}$ | 5 | 10 | 30 | µs | 1) | P_6.4.1.4 |
| Transition Time to Sleep Mode | $t_{TRANS2SLP}$ | 1 | 5 | 60 | µs | 1)2) | P_6.4.1.5 |
| Limp Home Acknowledgement Time | $t_{LHI(AC)}$ | 10 | 20 | 40 | µs | 1) | P_6.4.1.6 |

1) Not subject to production test - specified by design.
2) If output channel enters inductive clamping, clamping time has to be added.

## 6.5 Electrical Characteristics Power Supply - Product Specific

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

22.5 mΩ: $R_L$ = 4.8 Ω

### 6.5.1 BTS71040-4ESP

**Table 13 Electrical Characteristics: Power Supply BTS71040-4ESP**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Digital Supply Current Consumption in Normal Operation | $I_{DD}$ | – | 80 | 200 | µA | $f_{SCLK}$ = 0 MHz<br>$V_S > V_{S(UV)}$<br>$V_{CSN} = V_{DD}$ = 5 V<br>**DCR.MUX** ≠ $111_B$ | P_6.5.32.1 |
| Digital Supply Current Consumption in Normal Operation during SPI Traffic (Average) | $I_{DD(ACTIVE)}$ | – | 2.5 | – | mA | 1)2)<br>$f_{SCLK}$ = 5 MHz<br>$V_S > V_{S(UV)}$<br>$V_{DD}$ = 5 V<br>$V_{CSN}$ = 0 V<br>$C_{L(SO)}$ = 50 pF<br>**DCR.MUX** ≠ $111_B$ | P_6.5.32.2 |
| Digital Supply Current Consumption in Sleep Mode | $I_{DD(SLEEP)}$ | – | 17 | 50 | µA | $f_{SCLK}$ = 0 MHz<br>$V_S > V_{S(UV)}$<br>$V_{CSN} = V_{DD}$ = 5 V<br>**DCR.MUX** = $111_B$ | P_6.5.32.3 |
| Digital Supply Current Consumption in Sleep Mode | $I_{DD(SLEEP)}$ | – | 17 | 35 | µA | $f_{SCLK}$ = 0 MHz<br>$V_S > V_{S(UV)}$<br>$V_{CSN} = V_{DD}$ = 5 V<br>**DCR.MUX** = $111_B$<br>$T_J \le 85$ °C | P_6.5.32.12 |
| Power Supply Current Consumption in Sleep Mode with Loads at $T_J \le 85$ °C | $I_{VS(SLEEP)\_85}$ | – | 0.05 | 0.4 | µA | 2)3)<br>$V_S$ = 18 V<br>$V_{OUT}$ = 0 V<br>INx = “low”<br>$T_J \le 85$ °C | P_6.5.32.4 |
| Power Supply Current Consumption in Sleep Mode with Loads at $T_J$ = 150 °C | $I_{VS(SLEEP)\_150}$ | – | 2 | 100 | µA | $V_S$ = 18 V<br>$V_{OUT}$ = 0 V<br>INx = “low”<br>$T_J$ = 150 °C | P_6.5.32.5 |
| Operating Current in Active Mode (all Channels ON) | $I_{GND(ACTIVE)}$ | – | 5 | 7 | mA | $V_S$ = 18 V<br>$V_{DD}$ = 5 V<br>INx = “high” or<br>**OUT.OUTn** = $1_B$ | P_6.5.32.6 |

**Table 13 Electrical Characteristics: Power Supply BTS71040-4ESP** (continued)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Operating Current in Ready Mode | $I_{GND(READY)}$ | – | 80 | 200 | µA | $V_S$ = 18 V<br>$V_{CSN}$ = $V_{DD}$ = 5 V<br>$f_{SCLK}$ = 0 MHz<br>**DCR.MUX** = $111_B$<br>**OUT.OUTn** = $1_B$ | P_6.5.32.8 |
| Operating Current in Stand-by Mode | $I_{GND(STBY)}$ | – | 1.25 | 2 | mA | $V_S$ = 18 V<br>$V_{DD}$ = 5 V<br>**DCR.MUX** ≠ $111_B$ | P_6.5.32.9 |

1) Test pattern shifted-in on SI: 0101010101010101 and 1010101010101010.
2) Not subject to production test - specified by design.
3) If $V_{DD} < V_{DD(PO)}$, LHI =”low” and any restart counter > 0, $I_{GND(STBY)}$ has to be considered.

# 7 Power Stages

The high-side power stages are built using a N-channel vertical Power MOSFET with charge pump.

## 7.1 Output ON-State Resistance

The ON-state resistance $R_{DS(ON)}$ depends mainly on junction temperature $T_J$. **Figure 18** shows the variation of $R_{DS(ON)}$ across the whole $T_J$ range. The value “2” on the y-axis corresponds to the maximum $R_{DS(ON)}$ measured at $T_J$ = 150 °C.

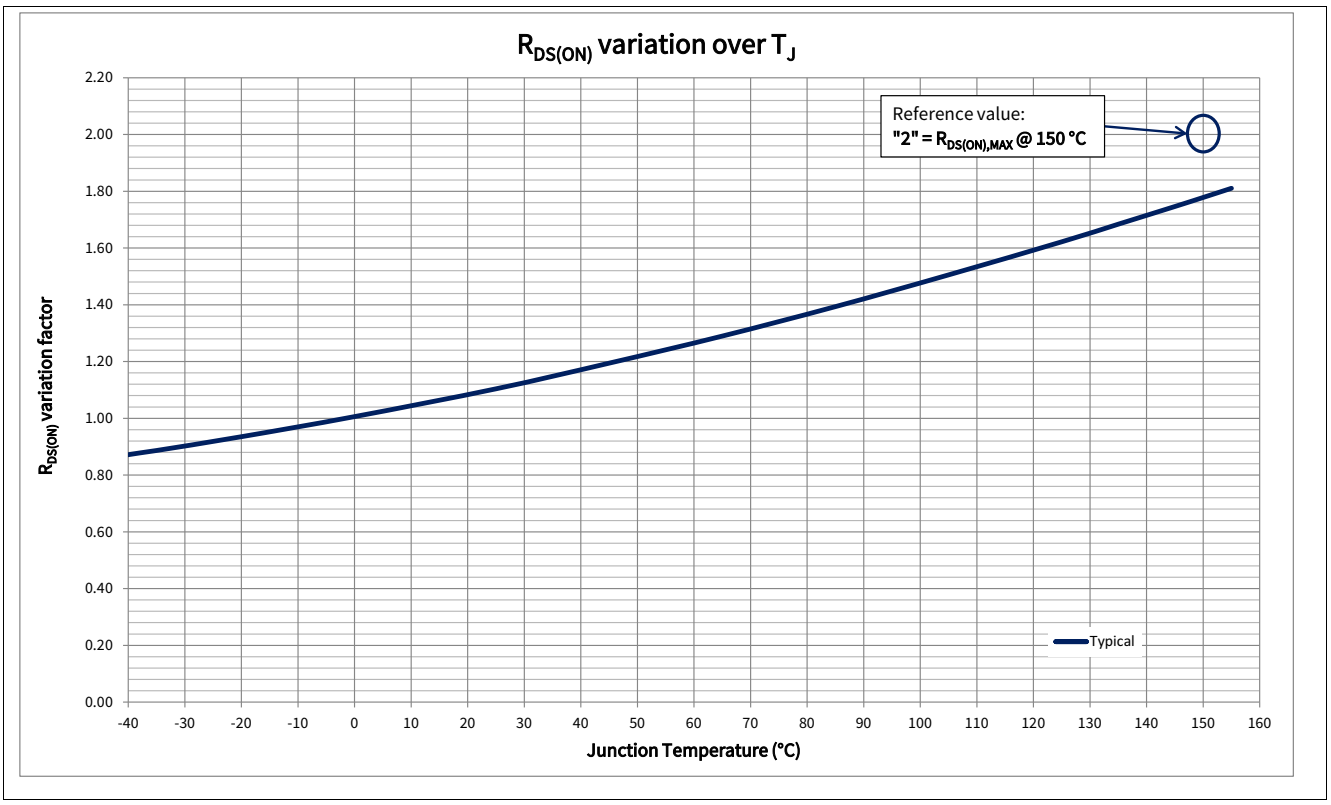



**Figure 18 $R_{DS(ON)}$ variation factor**

The behavior in Reverse Polarity is described in **Chapter 8.4.1**.

## 7.2 Switching loads

### 7.2.1 Switching Resistive Loads

When switching resistive loads, the switching times and slew rates shown in **Figure 19** can be considered. The switch energy values $E_{ON}$ and $E_{OFF}$ are proportional to load resistance and times $t_{ON}$ and $t_{OFF}$.

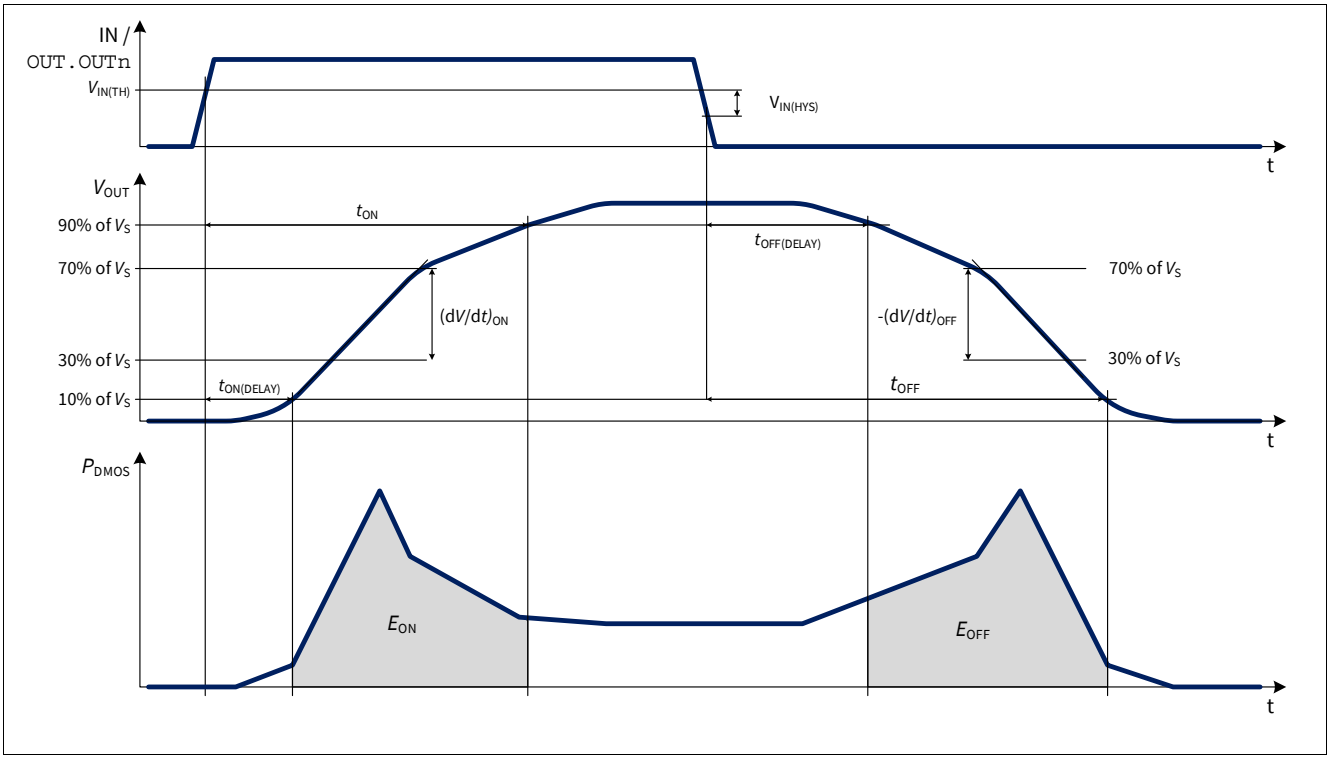



**Figure 19 Switching a Resistive Load**

## 7.2.2 Switching Inductive Loads

When switching OFF inductive loads with high-side switches, the voltage $V_{OUT}$ drops below ground potential, because the inductance intends to continue driving the current. To prevent the destruction of the device due to overvoltage, a voltage clamp mechanism is implemented. The clamping structure limits the negative output voltage so that $V_{DS} = V_{DS(CLAMP)}$. **Figure 20** shows a concept drawing of the implementation. The clamping structure protects the device in all operation modes listed in **Chapter 6.1**.

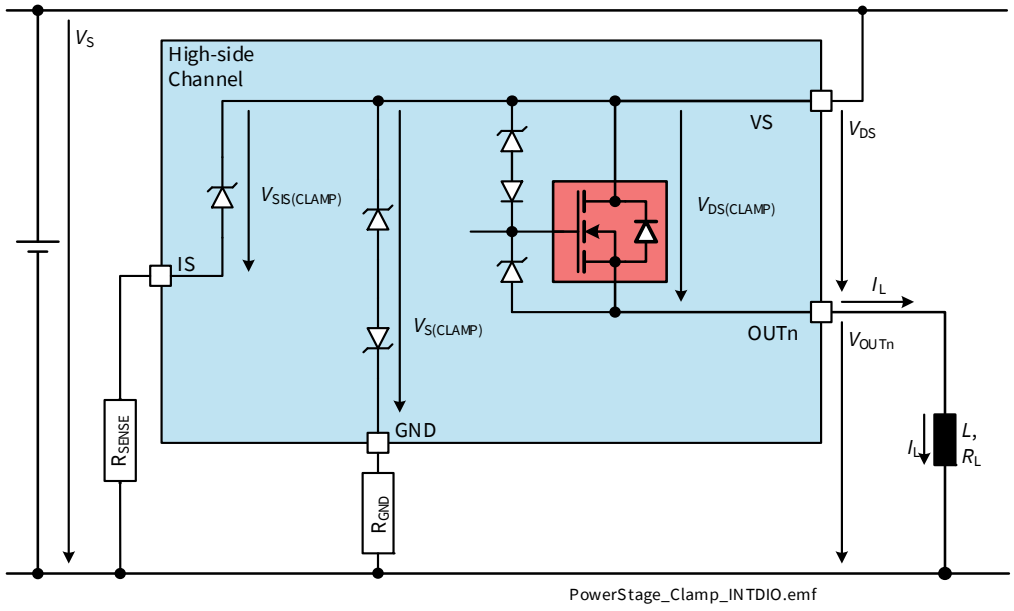



**Figure 20 Output Clamp concept**

During demagnetization of inductive loads, energy has to be dissipated in BTS71040-4ESP. The energy can be calculated with **Equation (7.1)**:

$$E = V_{DS(CLAMP)} \cdot \left[ \frac{V_S - V_{DS(CLAMP)}}{R_L} \cdot \ln\left(1 - \frac{R_L \cdot I_L}{V_S - V_{DS(CLAMP)}}\right) + I_L \right] \cdot \frac{L}{R_L} \quad (7.1)$$

The maximum energy, therefore the maximum inductance for a given current, is limited by the thermal design of the component.

### 7.2.3 Output Voltage Limitation

To increase the current sense accuracy, $V_{DS}$ voltage is monitored. When the output current $I_L$ decreases while the channel is diagnosed (channel selected via **DCR.MUX** - see **Figure 21**) bringing $V_{DS}$ equal or lower than $V_{DS(SLC)}$, the output DMOS gate is partially discharged. This increases the output resistance so that $V_{DS} = V_{DS(SLC)}$ even for very small output currents. The $V_{DS}$ increase allows the current sensing circuitry to work more efficiently, providing better $k_{ILIS}$ accuracy for output current in the low range.

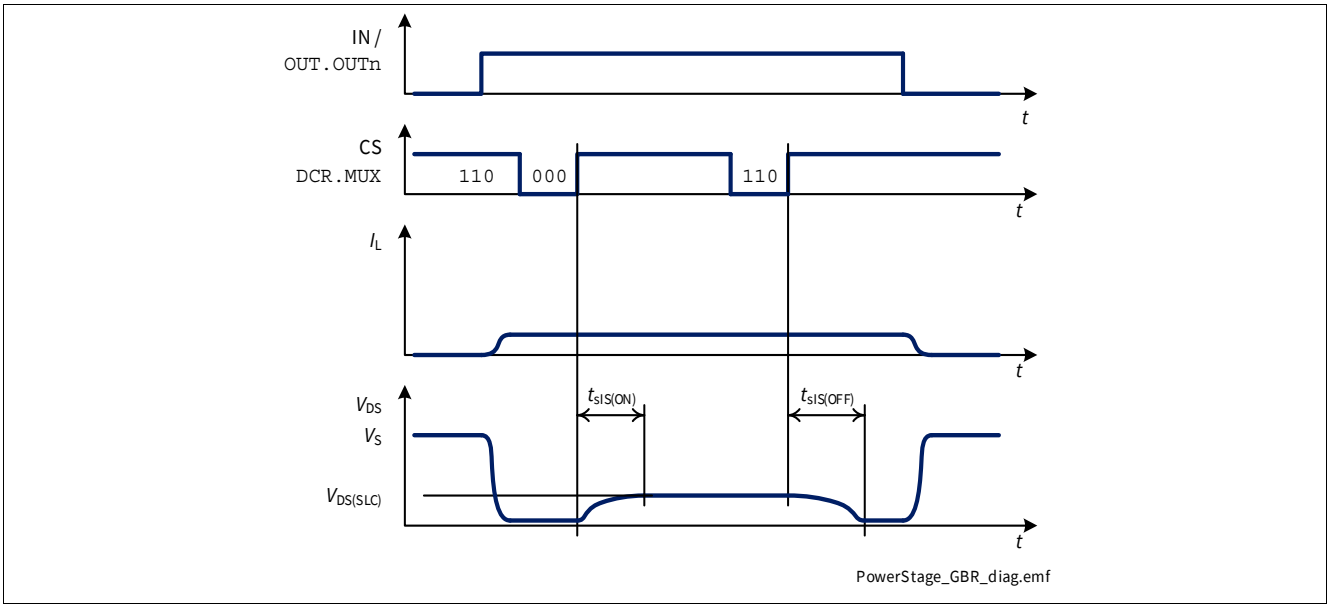



**Figure 21 Output Voltage Limitation activation during diagnosis**

### 7.2.4 Switching Capacitive Loads

When switching ON a capacitive load, the capacitance is causing a high inrush current. The current is depending on the value of the capacitance, the ESR, the impedance of the system and the slew rate of the driver. To improve the load driving capability, BTS71040-4ESP offers a slew rate control feature. When the slew rate bit **SRC.SRCn** is set, the slew rate of the respective channel is reduced to the half (see **Chapter 7.4.1**).

## 7.3 Advanced Switching Characteristics

### 7.3.1 Inverse Current behavior

When $V_{OUT} > V_S$, a current $I_{INV}$ flows into the power output transistor (see **Figure 22**). This condition is known as “Inverse Current”.

If the channel is in OFF state, the current flows through the intrinsic body diode generating high power losses therefore an increase of overall device temperature. This may lead to a switch OFF of unaffected channels due to Overtemperature. If the channel is in ON state, $R_{DS(INV)}$ can be expected and power dissipation in the output stage is comparable to normal operation in $R_{DS(ON)}$.

During Inverse Current condition, the channel remains in ON or OFF state as long as $I_{INV} < I_{L(INV)}$.

With InverseON, it is possible to switch ON the channel during Inverse Current condition as long as $I_{INV} < I_{L(INV)}$ (see **Figure 23**).

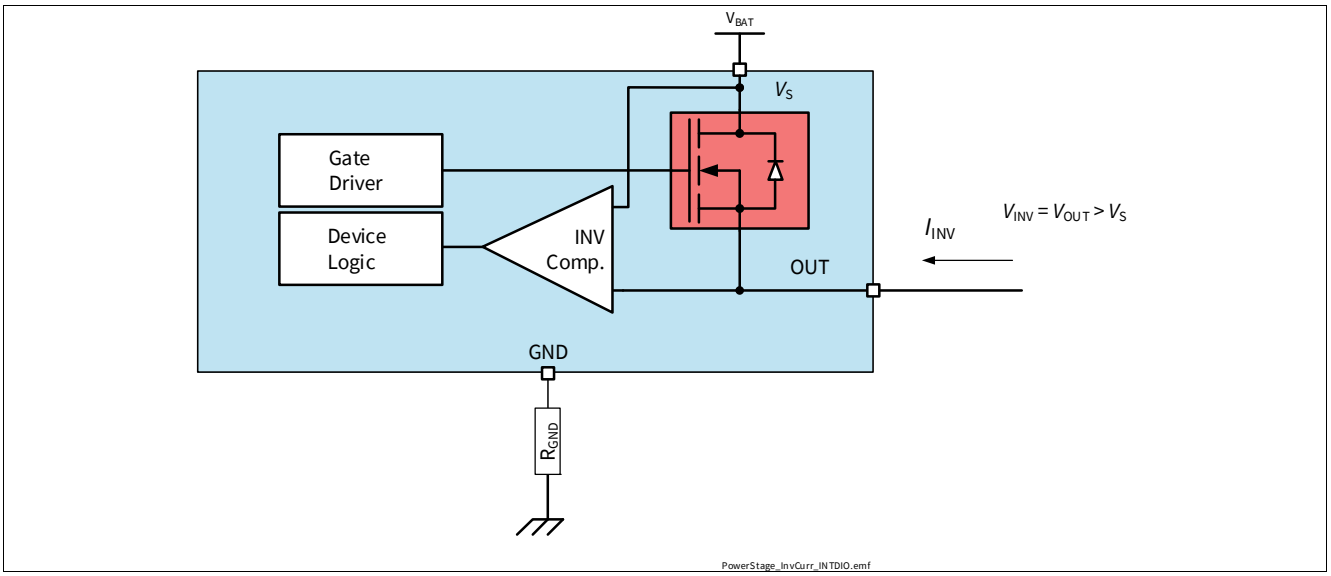



**Figure 22 Inverse Current Circuitry**

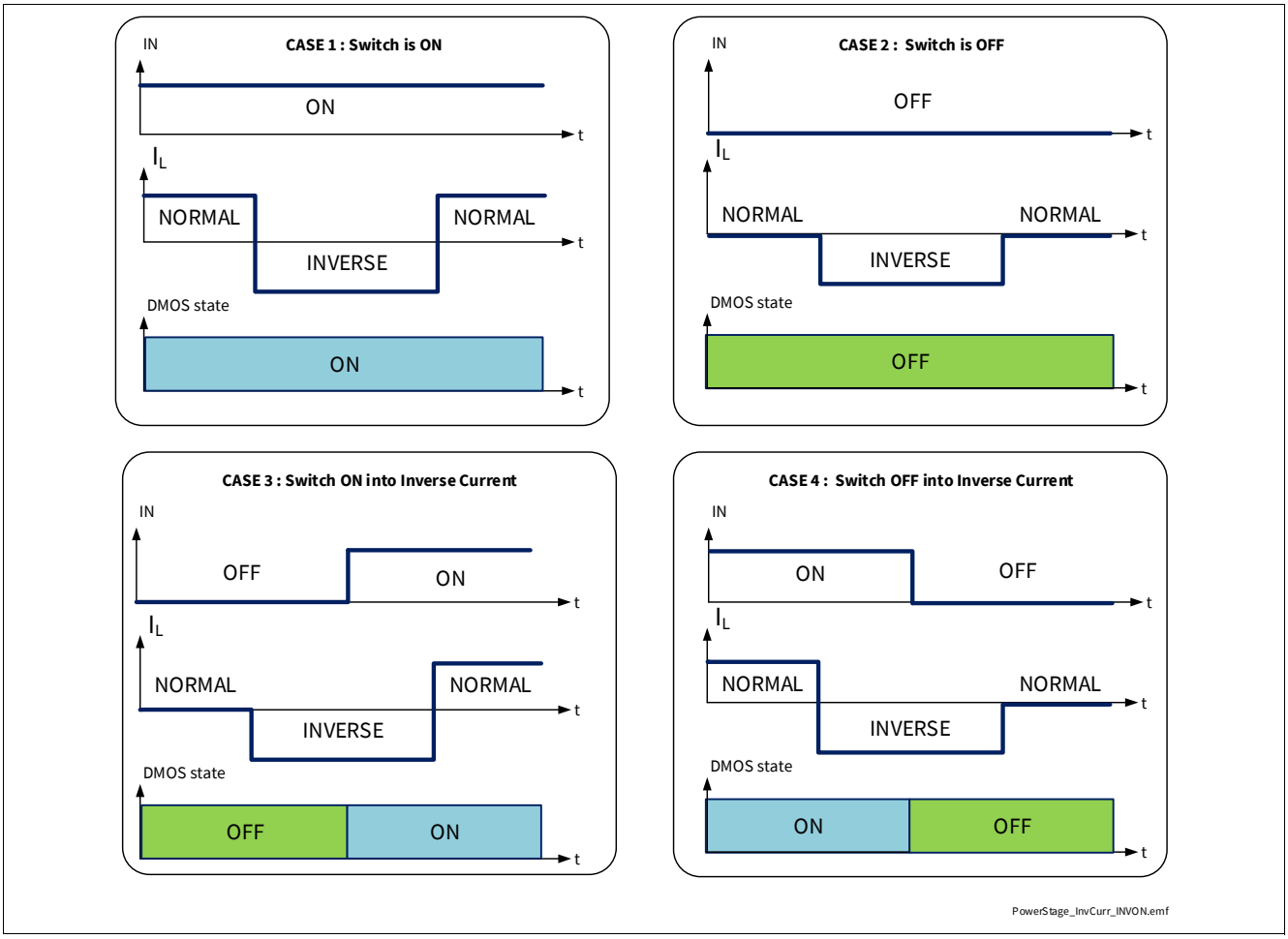



**Figure 23 InverseON - Channel behavior in case of applied Inverse Current**

*Note: No protection mechanism like Overtemperature or Overload protection is active during applied Inverse Currents.*

## 7.3.2 Switching Channels in Parallel

When switching channels in parallel to drive a single load it may happen that the two channels switch OFF asynchronously in case of a fault condition which brings additional stress to the channel that switches OFF last. In order to avoid this condition, it is possible to synchronize the protection of two channels when used in parallel. There are 2 bits in the SPI (**PCS.PCCn**), which allow to synchronize channels 0&3 and 1&2. When the corresponding **PCS.PCCn** bit is set, the switch-OFF and restart of the channels are synchronized and the current trip levels will be reduced to $I_{L(OVL3)}$. In case the current trip level for one channel is set to the low level (**OCR.OCTn** = $1_B$), the current for both channels will be reduced to $I_{L(OVL2)}$. Since the restart counters of the channels in parallel are synchronized, both channels will latch-OFF as soon one counter has reached $n_{RESTART(CR)}$. Due to this reason it is recommended to clear counters before switching channels in parallel. In case the slew rate adjustment for one channels is used, (**SRC.SRCn** = $1_B$), both channels operating in parallel mode will use the adjusted slew rate. When channels are switched in parallel (**PCS.PCCn** = $1_B$), the Output Voltage Drop Limitation at Small Load Currents is disabled. Therefore the current sense ratio specifications at lower currents are not valid. See **Chapter 9.7** for further information. To improve current sense accuracy in parallel channel operation, parallel mode has to be deactivated (**PCS.PCCn** = $0_B$). Since the current sense of the two channels used in parallel is not synchronized, the total current has to be calculated out of the current sense reading of each single channel. Unless otherwise specified parameter deviations are possible when parallel mode is activated.

When two channels are used in parallel, the total current capability $I_{L(NOM)}$ is doubled. It has to be ensured that the outputs used in parallel mode are connected together with a symmetric and low impedance connection either on the PCB or in the wire harness.

### 7.3.3 Cross Current robustness with H-Bridge configuration

When BTS71040-4ESP is used as high-side switch e.g. in a bridge configuration (therefore paired with a low-side switch as shown in **Figure 24**), the maximum slew rate applied to the output by the low-side switch must be lower than | $dV_{OUT}$ / $dt$ |. Otherwise the output stage may turn ON in linear mode (not in $R_{DS(ON)}$) while the low-side switch is commutating. This creates an unprotected overheating for the DMOS due to the cross-conduction current.

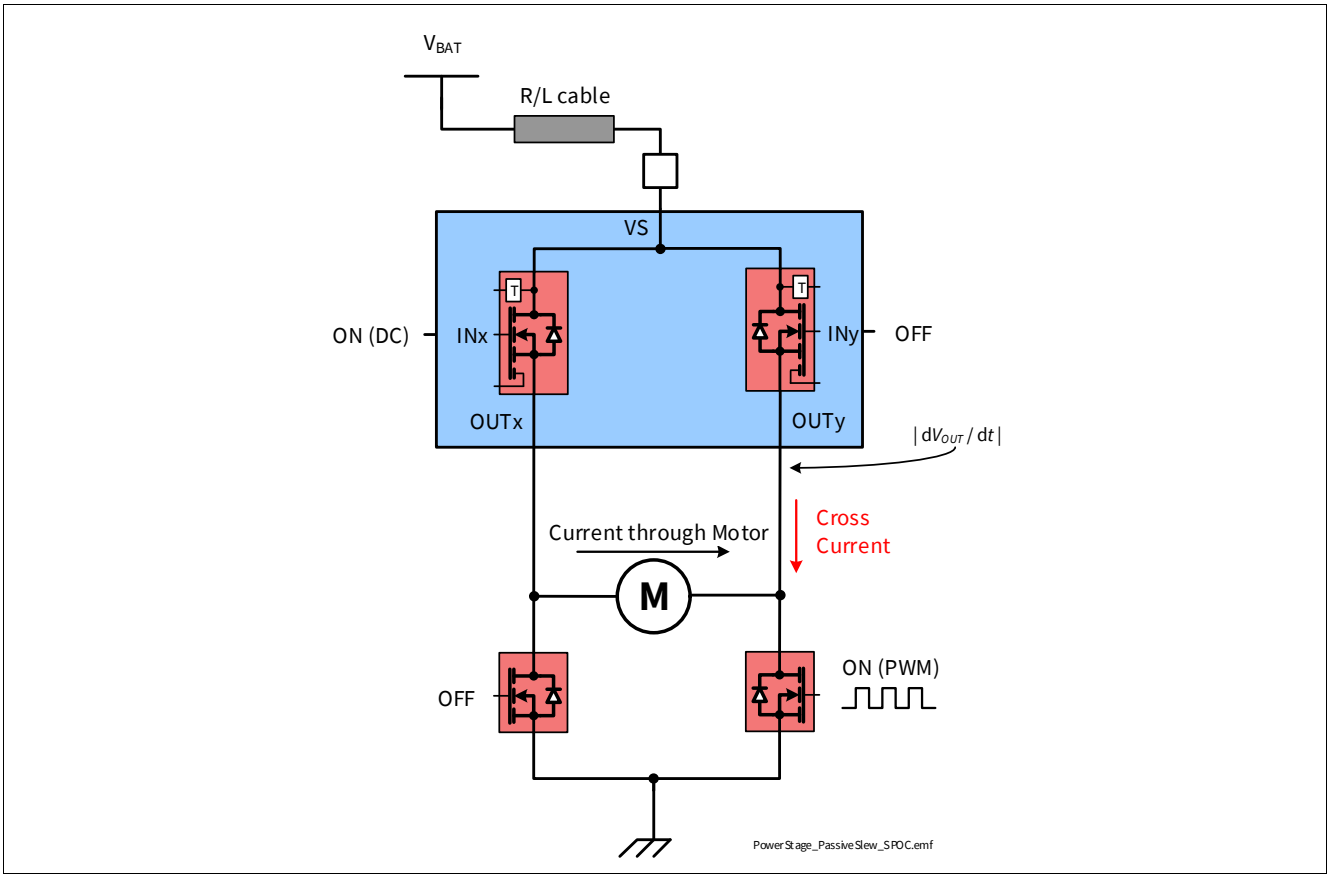



**Figure 24 High-Side switch used in Bridge configuration**

## 7.4 Electrical Characteristics Power Stages

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

22.5 mΩ: $R_L$ = 4.8 Ω

**Table 14 Electrical Characteristics: Power Stages - General**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Voltages** | | | | | | | |
| Drain to Source Clamping Voltage at $T_J$ = -40 °C | $V_{DS(CLAMP)\_-40}$ | 33 | 36.5 | 42 | V | $I_L$ = 5 mA<br>$T_J$ = -40°C<br>See **Figure 20** | P_7.4.0.1 |
| Drain to Source Clamping Voltage at $T_J \geq$ 25 °C | $V_{DS(CLAMP)\_25}$ | 35 | 38 | 44 | V | 1)<br>$I_L$ = 5 mA<br>$T_J \geq$ 25°C<br>See **Figure 20** | P_7.4.0.2 |

1) Tested at $T_J$ = 150°C.

## 7.4.1 Electrical Characteristics Power Stages

**Table 15 Electrical Characteristics: Power Stages**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Timings** | | | | | | | |
| Switch-ON Delay | $t_{ON(DELAY)}$ | 10 | 30 | 60 | µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 10% $V_S$<br>**PCS.PCCn** = $0_B$ | P_7.4.2.1 |
| Switch-ON Delay (parallel mode) | $t_{ON(DELAY)}$ | 10 | 40 | 80 | µs | 2)<br>$V_S$ = 13.5 V<br>$V_{OUT}$ = 10% $V_S$<br>**PCS.PCCn** = $1_B$ | P_7.4.2.16 |
| Switch-OFF Delay | $t_{OFF(DELAY)}$ | 10 | 30 | 60 | µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 90% $V_S$ | P_7.4.2.2 |
| Switch-ON Time | $t_{ON}$ | 20 | 55 | 100 | µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 90% $V_S$<br>**SRC.SRCn** = $0_B$<br>**PCS.PCCn** = $0_B$ | P_7.4.2.3 |
| Switch-ON Time (parallel mode) | $t_{ON}$ | 20 | 70 | 125 | µs | 2)<br>$V_S$ = 13.5 V<br>$V_{OUT}$ = 90% $V_S$<br>**SRC.SRCn** = $0_B$<br>**PCS.PCCn** = $1_B$ | P_7.4.2.20 |

**Table 15 Electrical Characteristics: Power Stages** (continued)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Switch-ON Time | $t_{ON}$ | 30 | 75 | 150 | µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 90% $V_S$<br>SRC.SRCn = $1_B$ | P_7.4.2.4 |
| Switch-OFF Time | $t_{OFF}$ | 20 | 55 | 100 | µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 10% $V_S$<br>SRC.SRCn = $0_B$ | P_7.4.2.6 |
| Switch-OFF Time | $t_{OFF}$ | 30 | 75 | 150 | µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 10% $V_S$<br>SRC.SRCn = $1_B$ | P_7.4.2.7 |
| Switch-ON/OFF Matching $t_{ON}$ - $t_{OFF}$ | $\Delta t_{SW}$ | -50 | 0 | 50 | µs | $V_S$ = 13.5 V<br>PCS.PCCn = $0_B$ | P_7.4.2.9 |
| **Voltage Slope** | | | | | | | |
| Switch-ON Slew Rate | $(dV/dt)_{ON}$ | 0.3 | 0.6 | 0.9 | V/µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 30% to 70% of $V_S$<br>SRC.SRCn = $0_B$ | P_7.4.2.11 |
| Switch-ON Slew Rate | $(dV/dt)_{ON}$ | 0.15 | 0.3 | 0.45 | V/µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 30% to 70% of $V_S$<br>SRC.SRCn = $1_B$ | P_7.4.2.12 |
| Switch-OFF Slew Rate | $-(dV/dt)_{OFF}$ | 0.3 | 0.6 | 0.9 | V/µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 70% to 30% of $V_S$<br>SRC.SRCn = $0_B$ | P_7.4.2.14 |
| Switch-OFF Slew Rate | $-(dV/dt)_{OFF}$ | 0.125 | 0.3 | 0.45 | V/µs | $V_S$ = 13.5 V<br>$V_{OUT}$ = 70% to 30% of $V_S$<br>SRC.SRCn = $1_B$ | P_7.4.2.15 |
| Slew Rate Matching | $\Delta(dV/dt)_{SW}$ | -30 | 0 | 30 | % | 1)<br>$V_S$ = 13.5 V | P_7.4.2.17 |
| **Voltages** | | | | | | | |
| Output Voltage Drop Limitation at Small Load Currents | $V_{DS(SLC)}$ | 2 | 10 | 18 | mV | 2)<br>$I_L = I_{L(OL)}$ = 20 mA | P_7.4.2.18 |

1) $\Delta(dV/dt)_{SW} = ((dV/dt)_{ON} - (dV/dt)_{OFF}) / (((dV/dt)_{ON} + (dV/dt)_{OFF}) / 2)$.

2) Not subject to production test - specified by design.

## 7.5 Electrical Characteristics - Power Output Stages

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

22.5 mΩ: $R_L$ = 4.8 Ω

### 7.5.1 Power Output Stage - 22.5 mΩ

**Table 16 Electrical Characteristics: Power Stages - 22.5 mΩ**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Output characteristics** | | | | | | | |
| ON-State Resistance at $T_J$ = 25 °C | $R_{DS(ON)\_25}$ | – | 22.5 | – | mΩ | 1)<br>$T_J$ = 25 °C | P_7.5.16.1 |
| ON-State Resistance at $T_J$ = 150 °C | $R_{DS(ON)\_150}$ | – | – | 38 | mΩ | $T_J$ = 150 °C | P_7.5.16.2 |
| ON-State Resistance in Cranking | $R_{DS(ON)\_CRANK}$ | – | – | 44 | mΩ | $T_J$ = 150 °C<br>$V_S$ = 3.1 V | P_7.5.16.3 |
| ON-State Resistance in Inverse Current at $T_J$ = 25 °C | $R_{DS(INV)\_25}$ | – | 22.5 | – | mΩ | 1)<br>$T_J$ = 25 °C<br>$I_L$ = -$I_{L(NOM)}$ | P_7.5.16.4 |
| ON-State Resistance in Inverse Current at $T_J$ = 150 °C | $R_{DS(INV)\_150}$ | – | – | 44 | mΩ | 1)<br>$T_J$ = 150 °C<br>$I_L$ = -$I_{L(NOM)}$ | P_7.5.16.5 |
| ON-State Resistance in Reverse Polarity at $T_J$ = 25 °C | $R_{DS(REV)\_25}$ | – | 45 | – | mΩ | 1)<br>$T_J$ = 25 °C<br>$V_S$ = -13.5 V<br>$I_L$ = -$I_{L(NOM)}$<br>$R_{SENSE}$ = 1.2 kΩ | P_7.5.16.6 |
| ON-State Resistance in Reverse Polarity at $T_J$ = 150 °C | $R_{DS(REV)\_150}$ | – | – | 70 | mΩ | 1)<br>$T_J$ = 150 °C<br>$V_S$ = -13.5 V<br>$I_L$ = -$I_{L(NOM)}$<br>$R_{SENSE}$ = 1.2 kΩ | P_7.5.16.7 |
| Nominal Load Current per Channel (all Channels Active) | $I_{L(NOM)}$ | – | 3 | – | A | 1)<br>$T_A$ = 85 °C<br>$T_J$ ≤ 150 °C | P_7.5.16.8 |
| Output Leakage Current at $T_J$ ≤ 85 °C | $I_{L(OFF)\_85}$ | – | 0.03 | 0.15 | µA | 1)<br>$V_{OUT}$ = 0 V<br>$V_{IN}$ = “low” and<br>**OUT.OUTn** = $0_B$<br>$T_A$ ≤ 85 °C | P_7.5.16.9 |

**Table 16 Electrical Characteristics: Power Stages - 22.5 mΩ** (continued)

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Output Leakage Current at $T_J$ = 150 °C | $I_{L(OFF)\_150}$ | – | – | 10 | µA | $V_{OUT}$ = 0 V<br>$V_{IN}$ = “low” and<br>**OUT.OUTn** = $0_B$<br>$T_A$ = 150 °C | P_7.5.16.10 |
| Inverse Current Capability | $I_{L(INV)}$ | – | 3 | – | A | 1)<br>$V_S < V_{OUT}$<br>IN = “high” or<br>**OUT.OUTn** = $1_B$ | P_7.5.16.11 |
| **Voltage Slope** | | | | | | | |
| Passive Slew Rate (e.g. for Half Bridge Configuration) | $\|dV_{OUT} / dt\|$ | – | – | 10 | V/µs | 1)<br>$V_S$ = 13.5 V | P_7.5.16.12 |
| **Voltages** | | | | | | | |
| Drain Source Diode Voltage | $\|V_{DS(DIODE)}\|$ | – | 500 | 600 | mV | 1)<br>$I_L$ = -190 mA<br>$T_J$ = 150 °C | P_7.5.16.13 |
| **Switching Energy** | | | | | | | |
| Switch-ON Energy | $E_{ON}$ | – | 0.30 | – | mJ | 1)<br>$V_S$ = 18 V<br>**SRC.SRCn** = $0_B$<br>**PCS.PCCn** = $0_B$ | P_7.5.16.14 |
| Switch-OFF Energy | $E_{OFF}$ | – | 0.38 | – | mJ | 1)<br>$V_S$ = 18 V<br>**SRC.SRCn** = $0_B$<br>**PCS.PCCn** = $0_B$ | P_7.5.16.15 |

1) Not subject to production test - specified by design.

# 8 Protection

The BTS71040-4ESP is protected against Overtemperature, Overload, Reverse Battery (with ReverseON) and Overvoltage. Overtemperature and Overload protections are working when the device is not in Sleep mode. Overvoltage protection works in all operation modes. Reverse Battery protection works when the GND and VS pins are reverse supplied.

## 8.1 Overtemperature Protection

The device incorporates both an absolute ($T_{J(ABS)}$) and a dynamic ($T_{J(DYN)}$) temperature protection circuitry for each channel. An increase of junction temperature $T_J$ above either one of the two thresholds ($T_{J(ABS)}$ or $T_{J(DYN)}$) switches OFF the overheated channel to prevent destruction. The corresponding **WRNDIAG.WRNn** bits are set and cleared on read. The channel remains switched OFF until junction temperature has reached the “Restart” condition described in **Table 17**. The behavior is shown in **Figure 25** (absolute Overtemperature Protection) and **Figure 26** (dynamic Overtemperature Protection). $T_{J(REF)}$ is the reference temperature used for dynamic temperature protection.

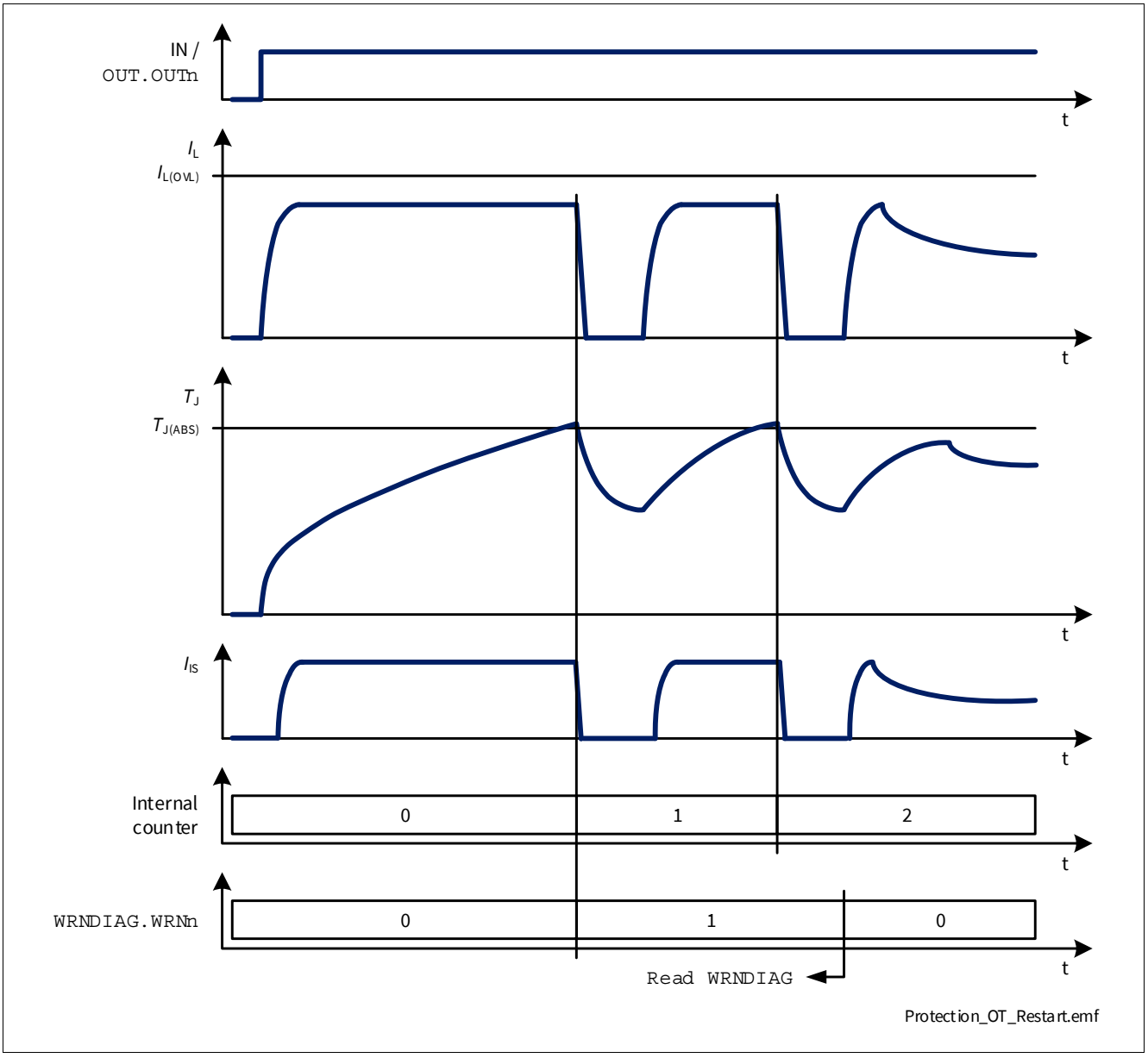



**Figure 25 Overtemperature Protection (Absolute)**

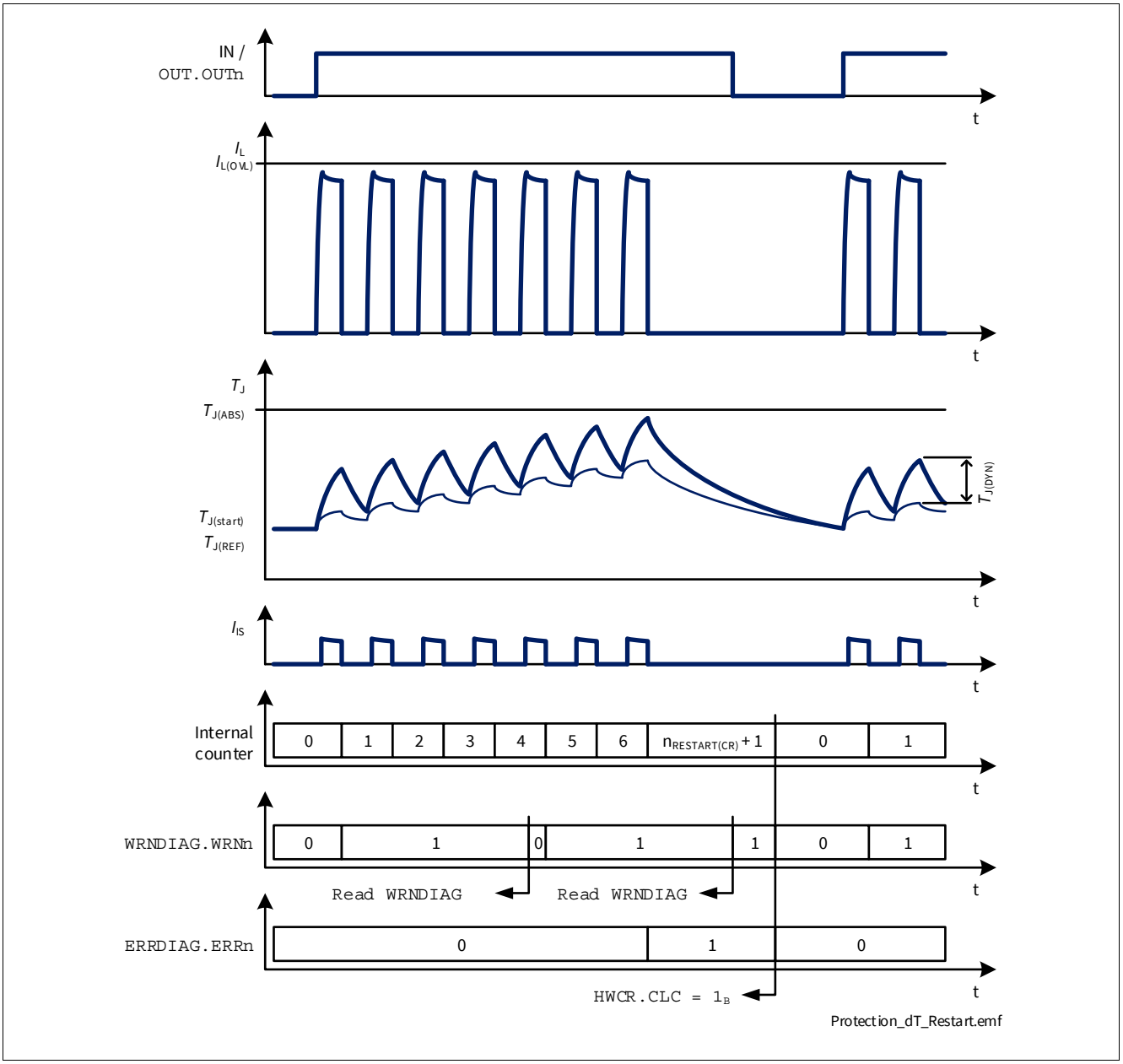



**Figure 26 Overtemperature Protection (Dynamic)**

When the Overtemperature protection circuitry allows the channel to be switched ON again, the restart strategy described in **Chapter 8.3.1** is followed.

## 8.2 Overload Protection

The BTS71040-4ESP is protected in case of Overload or short circuit to ground. Two Overload thresholds are defined (see **Figure 27**) and selected automatically depending on the voltage $V_{DS}$ across the power DMOS:

- $I_{L(OVL0)}$ when $V_{DS}$ < 13 V
- $I_{L(OVL1)}$ when $V_{DS}$ > 22 V

In addition, the Overload threshold can be reduced by setting **OCR.OCTn**.

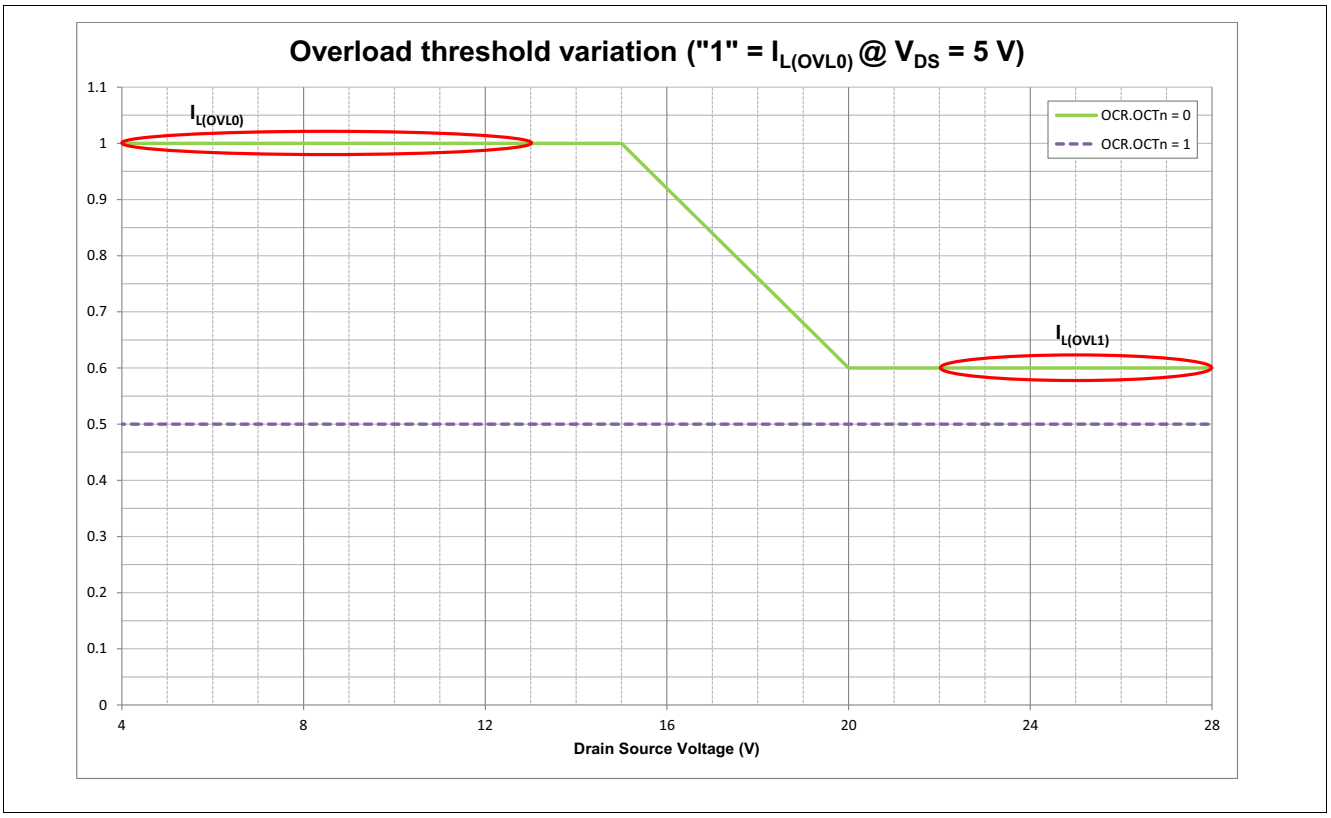



**Figure 27 Overload current thresholds**

When $I_L \geq I_{L(OVL)}$ (either $I_{L(OVL0)}$ or $I_{L(OVL1)}$), the channel is switched OFF. The channel is allowed to restart according to the restart strategy described in **Chapter 8.3.1**.

## 8.3 Protection and Diagnosis in case of Fault

Any event that triggers a protection mechanism (either Overtemperature or Overload) has 3 consequences:

- The affected channel switches OFF and the internal counter is incremented
- The current sense of the affected channel is set to high impedance
- The corresponding **WRNDIAG.WRNn** are set to $1_B$ and latched until readout.

The channel can be switched ON again if all the protection mechanisms fulfill the “restart” conditions described in **Table 17** and the internal restart counter is enabled (**RCD.RCDn** set to $0_B$).

**Table 17 Protection “Restart” Condition**

| Fault condition | Switch OFF event | “Restart” Condition |
|---|---|---|
| Overtemperature | $T_J \geq T_{J(ABS)}$ or $(T_J - T_{J(REF)}) \geq T_{J(DYN)}$ | $T_J < T_{J(ABS)}$ and $(T_J - T_{J(REF)}) < T_{J(DYN)}$ (including hysteresis)<br>$n_{RESTART} < n_{RESTART(CR)}$<br>**RCD.RCDn** = 0 |
| Overload | $I_L \geq I_{L(OVL)}$ | $I_L < 50$ mA<br>$T_J$ within $T_{J(ABS)}$ and $T_{J(DYN)}$ ranges (including hysteresis)<br>$n_{RESTART} < n_{RESTART(CR)}$<br>**RCD.RCDn** = 0 |

### 8.3.1 Restart Strategy

When INx or **OUT.OUTn** is set to “high”, the corresponding channel is switched ON. In case of fault condition the output stage is switched OFF. The channel is allowed to restart only in case the “restart” conditions for the protection mechanisms are fulfilled (see **Table 17**). The **WRNDIAG.WRNn** is set during Overcurrent shutdown. It is reset when the internal fault signal is cleared and the **WRNDIAG** is transmitted, unless latched state is reached by exceeding $n_{RESTART(CR)}$. The next Overcurrent event set the **WRNDIAG.WRNn** again. In case the automatic restarts are not required, they can be deactivated by setting **RCD.RCDn** to $1_B$. When **RCD.RCDn** is set to $1_B$, the restart counter will be reset. When a channel reaches latched state, the corresponding **ERRDIAG.ERRn** bit is set. The restart latch and counter are cleared by setting the SPI bit **HWCR.CLC** to $1_B$. If the input pin is “high” or **OUT.OUTn** is still set to $1_B$, the channel is switched ON immediately after the command that set **HWCR.CLC** bit to $1_B$. To ensure an adequate cool down after latch-OFF condition, application software needs to wait for $t > t_{RETRY}$ before restarting the channel.

The restart strategy is shown in **Figure 28**.

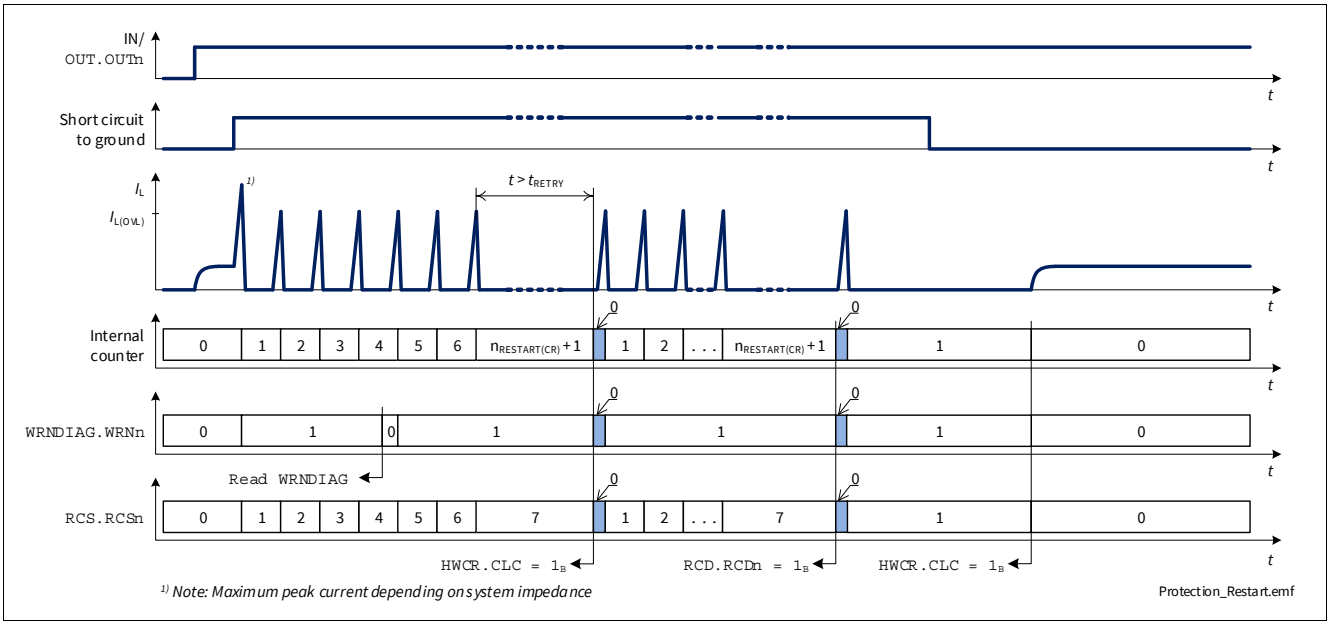



**Figure 28 Restart Strategy timing diagram**

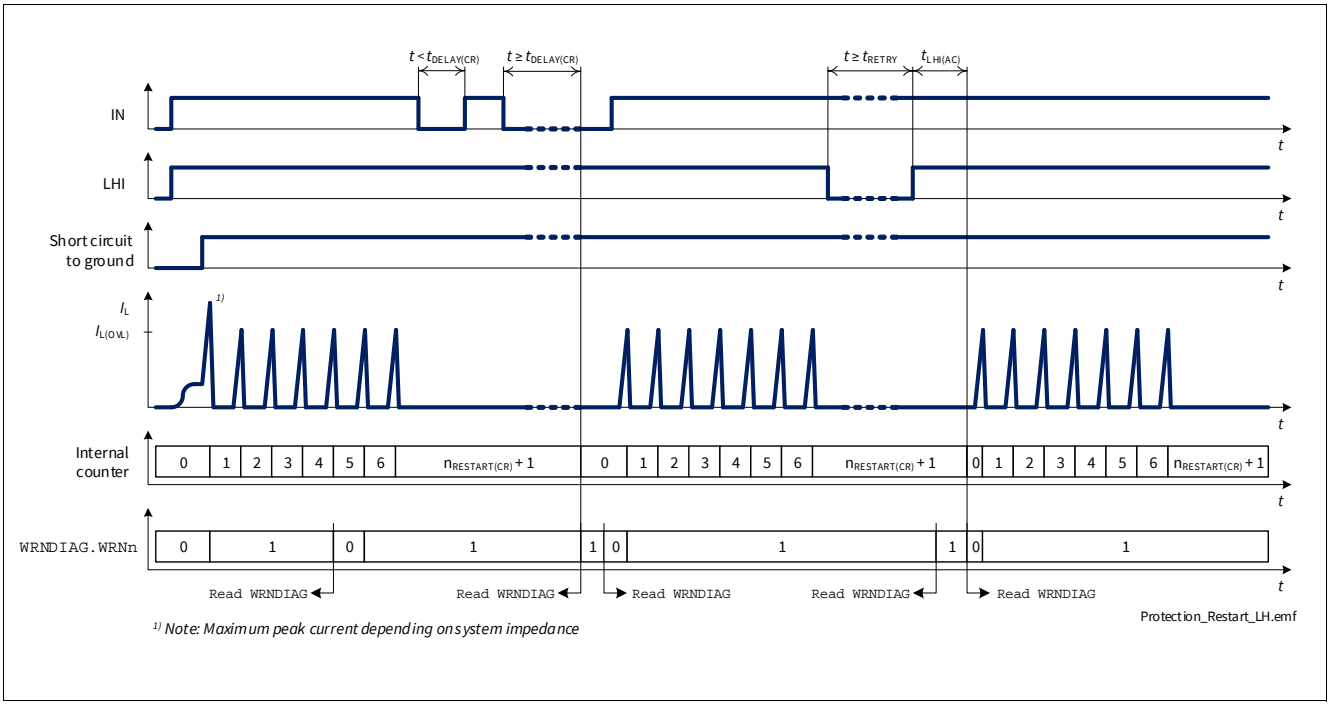



**Figure 29 Restart Strategy timing diagram in Limp Home**

## 8.4 Additional protections

### 8.4.1 Reverse Polarity Protection

In Reverse Polarity condition (also known as Reverse Battery), the output stages are switched ON (see parameter $R_{DS(REV)}$) because of ReverseON feature which limits the power dissipation in the output stages. Each ESD diode of the logic contributes to total power dissipation. The reverse current through the output stages must be limited by the connected loads. The current through digital power supply $V_{DD}$ and Digital Input pins has to be limited as well by an external resistor (please refer to the Absolute Maximum Ratings listed in **Chapter 4.1** and to Application Information in **Chapter 11**).

**Figure 30** shows a typical application including a device with ReverseON. A current flowing into GND pin ($-I_{GND}$) during Reverse Polarity condition is necessary to activate ReverseON, therefore a resistive path between module ground and device GND pin must be present.

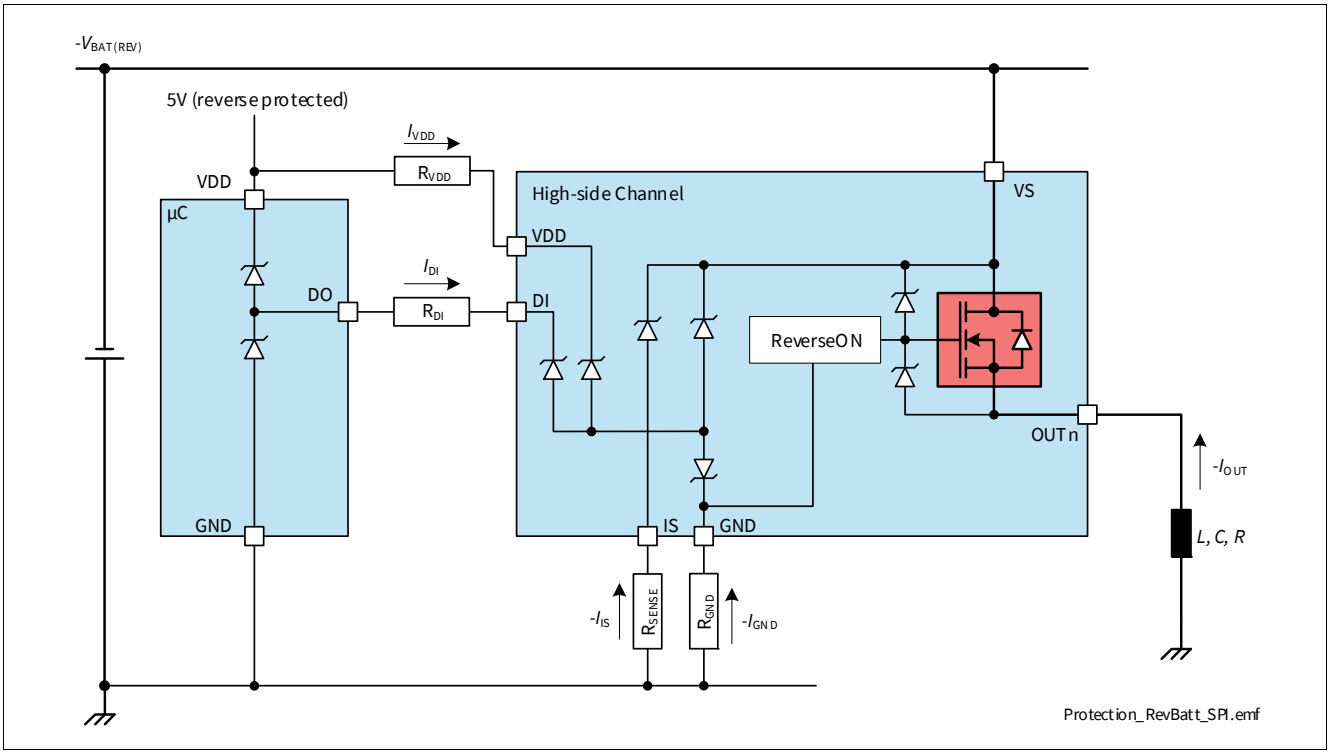



**Figure 30 Reverse Battery Protection (application example)**

## 8.4.2 Overvoltage Protection

In the case of supply voltages between $V_{S(EXT,UP)}$ and $V_{BAT(LD)}$, the output transistors are still operational and follow the input pins or the **OUT** register. In addition to the output clamp for inductive loads as described in **Chapter 7.2.2**, there is a clamp mechanism available for Overvoltage protection for the logic and the output channels, monitoring the voltage between VS and GND pins ($V_{S(CLAMP)}$).

## 8.5 Protection against loss of connection

### 8.5.1 Loss of Battery and Loss of Load

The loss of connection to battery or to the load has no influence on device robustness when load and wire harness are purely resistive. In case of driving an inductive load, the energy stored in the inductance must be handled. BTS71040-4ESP can handle the inductivity of the wire harness up to 10 µH with $I_{L(NOM)}$. In case of applications where currents and/or the aforementioned inductivity are exceeded, an external suppressor diode (like diode $D_{Z2}$ shown in **Chapter 11**) is recommended to handle the energy and to provide a well-defined path to the load current.

*Note: In case of a lost battery connection the VS monitoring function protects the SPI registers as soon the device is out of Sleep mode. This means that any command sent to the device will be ignored and the device will just send back the **STDDIAG**. Furthermore, the status of the LHI pin is blanked, which means that it is not possible to enter Limp Home mode.*

### 8.5.2 Loss of Ground

In case of loss of device ground, it is recommended to have a resistor connected between any Digital Input pin and the microcontroller to ensure a channel switch OFF (as described in **Chapter 11**).

*Note: In case any Digital Input pin is pulled to ground (either by a resistor or active) a parasitic ground path is available, which could keep the device operational during loss of device ground. The same behavior applies for the SPI functionality.*

## 8.6 Electrical Characteristics Protection

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

22.5 mΩ: $R_L$ = 4.8 Ω

**Table 18 Electrical Characteristics: Protection - General**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Thermal Shutdown Temperature (Absolute) | $T_{J(ABS)}$ | 150 | 175 | 200 | °C | 1)2) See **Figure 25** | P_8.6.0.1 |
| Thermal Shutdown Hysteresis (Absolute) | $T_{HYS(ABS)}$ | – | 30 | – | K | 3) See **Figure 25** | P_8.6.0.2 |
| Thermal Shutdown Temperature (Dynamic) | $T_{J(DYN)}$ | – | 80 | – | K | 3) See **Figure 26** | P_8.6.0.3 |
| Power Supply Clamping Voltage at $T_J$ = -40 °C | $V_{S(CLAMP)\_-40}$ | 33 | 36.5 | 42 | V | $I_{VS}$ = 5 mA $T_J$ = -40 °C See **Figure 20** | P_8.6.0.6 |
| Power Supply Clamping Voltage at $T_J \geq$ 25 °C | $V_{S(CLAMP)\_25}$ | 35 | 38 | 44 | V | 2) $I_{VS}$ = 5 mA $T_J \geq$ 25 °C See **Figure 20** | P_8.6.0.7 |
| Power Supply Voltage Threshold for Overcurrent Threshold Reduction in case of Short Circuit | $V_{S(JS)}$ | 20.5 | 22.5 | 24.5 | V | 3) Setup acc. to AEC-Q100-012 | P_8.6.0.8 |

1) Functional test only.
2) Tested at $T_J$ = 150°C only.
3) Not subject to production test - specified by design.

### 8.6.1 Electrical Characteristics Protection

**Table 19 Electrical Characteristics: Protection**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Counter Reset Delay Time after Fault Condition in Limp Home | $t_{DELAY(CR)}$ | 40 | 70 | 100 | ms | 1) LHI = “high” INx = “low” | P_8.6.2.1 |
| Automatic Restarts in Case of Fault after a Counter Reset | $n_{RESTART(CR)}$ | – | 6 | – | – | 1) | P_8.6.2.2 |

1) Not subject to production test - specified by design.

## 8.7 Electrical Characteristics Protection - Power Output Stages

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

22.5 mΩ: $R_L$ = 4.8 Ω

### 8.7.1 Protection Power Output Stage - 22.5 mΩ

**Table 20 Electrical Characteristics: Protection - 22.5 mΩ**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Overload Detection Current High Level | $I_{L(OVL0)}$ | 44 | 48 | 53 | A | 1)<br>OCR.OCTn= $0_B$<br>$T_J$ = -40 °C to 50 °C<br>d$I$/d$t$ = 0.2 A/µs | P_8.7.16.3 |
| Overload Detection Current High Level | $I_{L(OVL0)}$ | 35 | 39 | 44 | A | 2)<br>OCR.OCTn= $0_B$<br>$T_J$ = 150 °C<br>d$I$/d$t$ = 0.2 A/µs | P_8.7.16.4 |
| Overload Detection Current Low Level | $I_{L(OVL2)}$ | 19 | 24 | 29 | A | 2)<br>OCR.OCTn= $1_B$<br>d$I$/d$t$ = 0.2 A/µs | P_8.7.16.2 |
| Overload Detection Current High Level (parallel mode) | $I_{L(OVL3)}$ | 22 | 31 | 36 | A | 2)3)<br>OCR.OCTn= $0_B$<br>PCS.PCCn= $1_B$<br>d$I$/d$t$ = 0.2 A/µs | P_8.7.16.6 |
| Overload Detection Current at High $V_{DS}$ | $I_{L(OVL1)}$ | – | 29 | – | A | 2)<br>d$I$/d$t$ = 0.2 A/µs | P_8.7.16.5 |
| Overload Detection Current Jump Start Condition | $I_{L(OVL\_JS)}$ | – | 29 | – | A | 2)<br>OCR.OCTn= $0_B$<br>$V_S > V_{S(JS)}$<br>d$I$/d$t$ = 0.2 A/µs | P_8.7.16.7 |

1) Tested at $T_J$ = -40 °C.
2) Not subject to production test - specified by design.
3) $I_{L(OVL3)}$ applies for one channel. Total current for two channels in parallel $I_{L(OVL)} \leq 2 \times I_{L(OVL3)}$.

# 9 Diagnosis

For diagnosis purpose, the BTS71040-4ESP provides a current sense at pin IS as well as a diagnosis feedback via SPI. In case of disabled diagnostic, IS pin becomes high impedance. The integrated current sense multiplexer is controlled via SPI.

A sense resistor $R_{SENSE}$ must be connected between IS pin and module ground if the current sense diagnosis is used. $R_{SENSE}$ value has to be higher than 820 Ω (or 400 Ω when a central Reverse Battery protection is present on the battery feed) to limit the power losses in the sense circuitry. A typical value is $R_{SENSE}$ = 1.2 kΩ.

Due to the internal connection between IS pin and $V_S$ supply voltage, it is not recommended to connect the IS pin to the sense current output of other devices, if they are supplied by a different battery feed or using a different sense concept.

See **Figure 31** for details as an overview. For diagnosis feedback at different operation modes, please see **Chapter 9.2**.

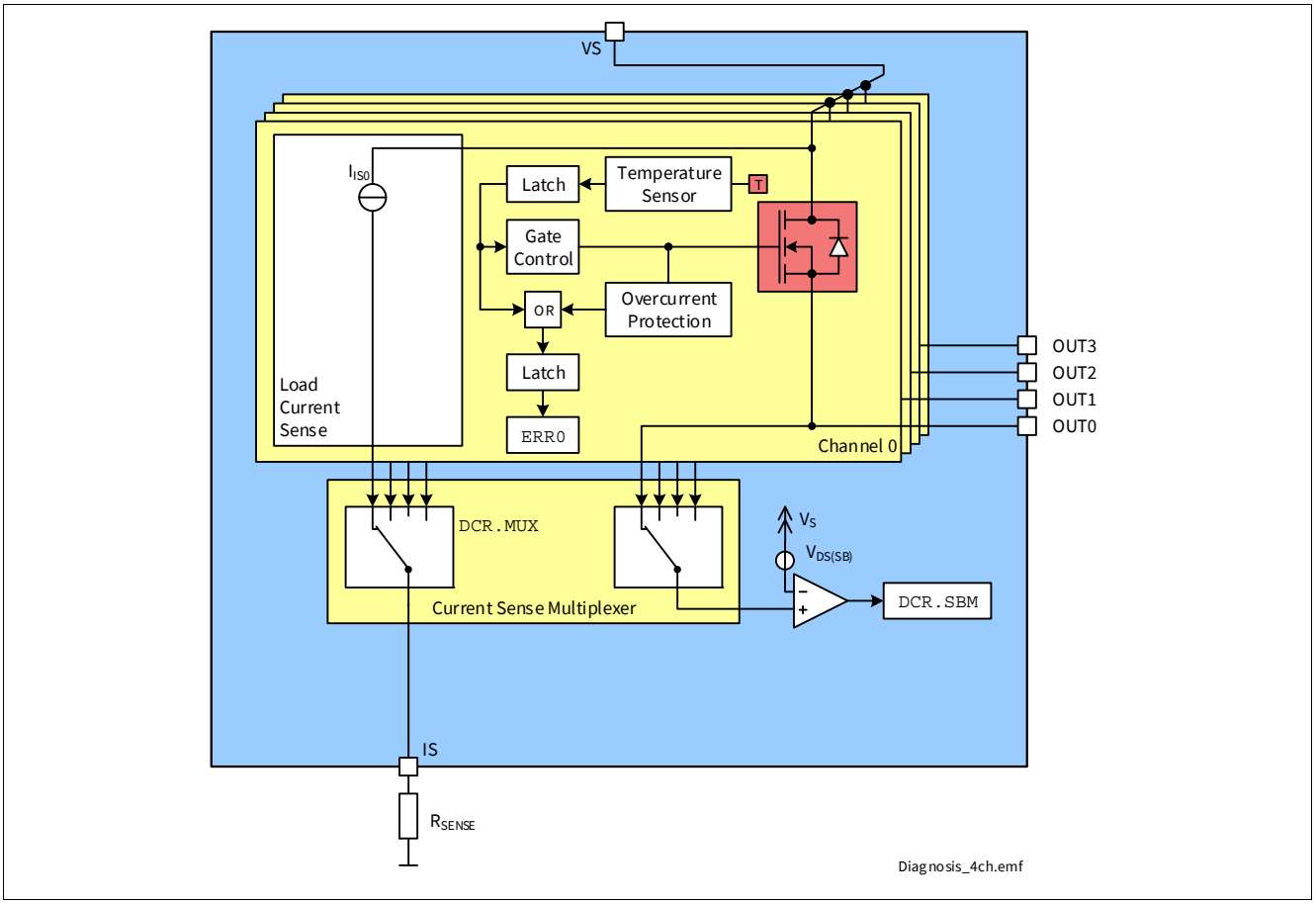



**Figure 31 Diagnosis block diagram**

## 9.1 Overview

**Table 21** gives a quick reference to the state of the IS pin during BTS71040-4ESP operation.

**Table 21 Diagnosis feedback, Function of Operation Mode**

| Operation Mode | Input level `OUT.OUTn` | $V_{OUT}$ | Current sense $I_{IS}$ | `WRNDIAG.WRNn` | `STDDIAG.SBM` |
|---|---|---|---|---|---|
| Normal operation | Low / $0_B$ OFF | ~ GND | Z | 0 | 1 |
| Short circuit to GND | | ~ GND | Z | 0 | 1 |
| Overtemperature | | Z | Z | 1 | x |
| Short circuit to $V_S$ | | $V_S$ | Z | 0 | 0 |
| Open Load | | $< V_S - V_{DS(SB)}$<br>$> V_S - V_{DS(SB)}$ [1] | Z<br>Z | 0<br>0 | 1<br>0 |
| Sense verification [2] | | x | $I_{IS(VER)}$ | x | 0 |
| Normal operation | High / $1_B$ ON | ~ $V_S$ | $I_{IS} = I_{L(NOM)} / k_{ILIS}$ | 0 | 0 |
| Overload | | $< V_S$ | $I_{IS} = I_L / k_{ILIS}$ | 0 | x |
| Short circuit to GND | | ~ GND | Z | 1 | 1 |
| Overtemperature | | Z | Z | 1 | x |
| Short circuit to $V_S$ | | $V_S$ | $I_{IS} < I_L / k_{ILIS}$ | 0 | 0 |
| Open Load | | ~ $V_S$ [3] | $I_{IS} = I_{IS(EN)}$ | 0 | 0 |
| Sense verification [2] | | x | $I_{IS(VER)}$ | x | 0 |
| Under load (e.g. Output Voltage Limitation condition) | | ~ $V_S$ [4] | $I_{IS(EN)} < I_{IS} < I_{L(NOM)} / k_{ILIS}$ | 0 | 0 |

1) With additional pull-up resistor.
2) `DCR.MUX` = $101_B$.
3) The output current has to be smaller than $I_{L(OL)}$.
4) The output current has to be higher than $I_{L(OL)}$.

## 9.2 Diagnosis Word at SPI

Diagnostic information about the status of each channel is provided through SPI. The fault flags, an OR combination of the overtemperature flags and the Overload monitoring signals are provided in the **WRNDIAG** register.

The Overload monitoring signals are latched in the **WRNDIAG.WRNn** bits and cleared each time the **WRNDIAG** is transmitted via SPI unless the maximum number of restarts is reached and the channel protects itself. The protection latches are cleared by SPI command **HWCR.CLC**.

## 9.3 Diagnosis in ON state

A current proportional to the load current (ratio $k_{ILIS} = I_L / I_{IS}$) is provided at pin IS when the following conditions are fulfilled:

- A power output stage is switched ON with $V_{DS} < V_{DS(SB)}$
- The diagnosis is enabled for that channel
- No fault (as described in **Chapter 8.3**) is present

If a “hard” failure mode is present or occurs for the channel selected using the **DCR.MUX** bits, the IS pin remains in or changes to “high impedance” state.

### 9.3.1 Current Sense ($k_{ILIS}$)

The accuracy of the sense current depends on temperature and load current. $I_{IS}$ increases linearly with $I_L$ output current until it reaches the saturation current $I_{IS(SAT)}$. In case of Open Load at the output stage ($I_L$ close to 0 A), the maximum sense current $I_{IS(EN)}$ (no load, diagnosis enabled) is specified. This condition is shown in **Figure 33**. The blue line represents the ideal $k_{ILIS}$ line, while the red lines show the behavior of a typical product.

An external RC filter between IS pin and microcontroller ADC input pin is recommended to reduce signal ripple and oscillations (a minimum time constant of 1 µs for the RC filter is recommended).

The $k_{ILIS}$ factor is specified with limits that take into account effects due to temperature, supply voltage and manufacturing process. Tighter limits are possible (within a defined current window) with calibration:

- A well-defined and precise current ($I_{L(CAL)}$) is applied at the output during End of Line test at customer side
- The corresponding current at IS pin is measured and the $k_{ILIS}$ is calculated ($k_{ILIS}$ @ $I_{L(CAL)}$)
- Within the current range going from $I_{L(CAL)\_L}$ to $I_{L(CAL)\_H}$ the $k_{ILIS}$ is equal to $k_{ILIS}$ @ $I_{L(CAL)}$ with limits defined by $\Delta k_{ILIS}$

The derating of $k_{ILIS}$ after calibration is calculated using the formulas in **Figure 32** and it is specified by $\Delta k_{ILIS}$

$$\Delta k_{ILIS,MAX} = 100 \cdot MAX\left(\frac{k_{ILIS}@I_{L(CAL)\_L}}{k_{ILIS}@I_{L(CAL)}} - 1, \frac{k_{ILIS}@I_{L(CAL)\_H}}{k_{ILIS}@I_{L(CAL)}} - 1\right)$$

$$\Delta k_{ILIS,MIN} = 100 \cdot MIN\left(\frac{k_{ILIS}@I_{L(CAL)\_L}}{k_{ILIS}@I_{L(CAL)}} - 1, \frac{k_{ILIS}@I_{L(CAL)\_H}}{k_{ILIS}@I_{L(CAL)}} - 1\right)$$

**Figure 32 $\Delta k_{ILIS}$ calculation formulas**

The calibration is intended to be performed at $T_{A(CAL)}$ = 25°C. The parameter $\Delta k_{ILIS}$ includes the drift overtemperature as well as the drift over the current range from $I_{L(CAL)\_L}$ to $I_{L(CAL)\_H}$.

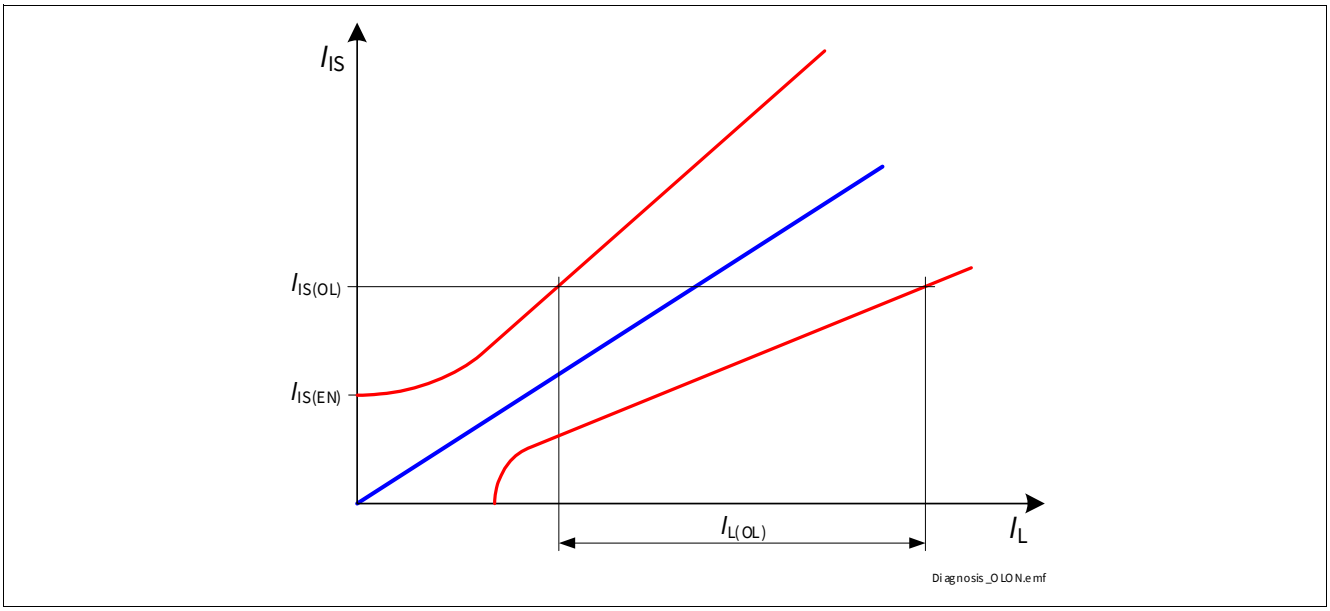



**Figure 33 Current Sense Ratio in Open Load at ON condition**

### 9.3.2 Current Sense Multiplexer

There is a current sense multiplexer implemented in the BTS71040-4ESP that routes the sense current of the selected channel to the diagnosis pin IS. The channel is selected via SPI register **DCR.MUX**. The sense current can also be disabled by SPI register **DCR.MUX**. For details on timing of the current sense multiplexer, refer to **Figure 34**. In addition **DCR.MUX** is used in combination with other SPI bits to address further functions of the device. To verify the function of the current sensing path in ON and OFF state, the device offers a sense verification mode. In this mode a predefined current $I_{IS(VER)}$ is provided on the current sense pin independent on the load condition of any channel. This enables the microcontroller to verify the sense path at any time. The sense verification mode is enabled when **DCR.MUX** = $101_B$.

All commands and functions involving the **DCR.MUX** bits are listed below:

- The main function of **DCR.MUX** is to switch the current sense multiplexer
- Executing **PCS.CLCS** = $1_B$ clears the counter and latches OFF the channel selected by **DCR.MUX**
- Executing **PCS.SRCS** = $1_B$ the slew rate of the channel selected by **DCR.MUX** will be changed. See **Chapter 7.4.1** for further information
- When reading **RCS.RCSn** bits, the status of the internal counter of the channel selected by **DCR.MUX** is responded
- When setting **DCR.MUX** = $101_B$ the sense verification mode is enabled

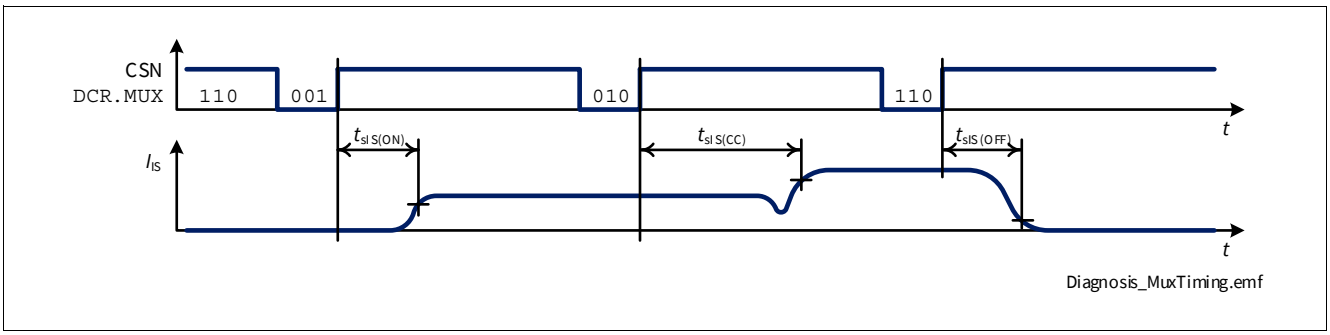



**Figure 34 Current Sense Multiplexer Timings**

## 9.4 Diagnosis in OFF state

When a power output stage is in OFF state, the BTS71040-4ESP can measure the output voltage and compare it with a threshold voltage. In this way, using some additional external components (a pull-down resistor and a switchable pull-up current source), it is possible to detect if the load is missing or if there is a short circuit to battery.

### 9.4.1 Switch Bypass Monitor

To detect short circuit to $V_S$, there is a switch bypass monitor implemented. In case of short circuit between the output pin OUT and VS in ON state, the current flows through the power transistor as well as through the short circuit (bypass) with undefined share between the two. As a result, the current sense signal shows lower values than expected by the load current. In OFF state, the output voltage remains close to $V_S$ potential which leads to a small $V_{DS}$. The switch bypass monitor compares the threshold $V_{DS(SB)}$ with the voltage $V_{DS}$ across the power transistor of that channel which is selected by the current sense multiplexer (**DCR.MUX**). The result of the comparison can be read in the standard diagnosis **STDDIAG.SBM**. In addition the switch bypass monitor can be used to detect an Open Load in OFF state. In this case a switchable pull-up resistor has to be placed to pull the OUT to VS potential.

## 9.5 SENSE Timings

**Figure 35** shows the timing during settling $t_{sIS(ON)}$ and disabling $t_{sIS(OFF)}$ of the SENSE (including the case of load change). As a proper signal cannot be established before the load current is stable (therefore before $t_{ON}$), $t_{sIS(DIAG)} = t_{sIS(ON)} + t_{ON}$.

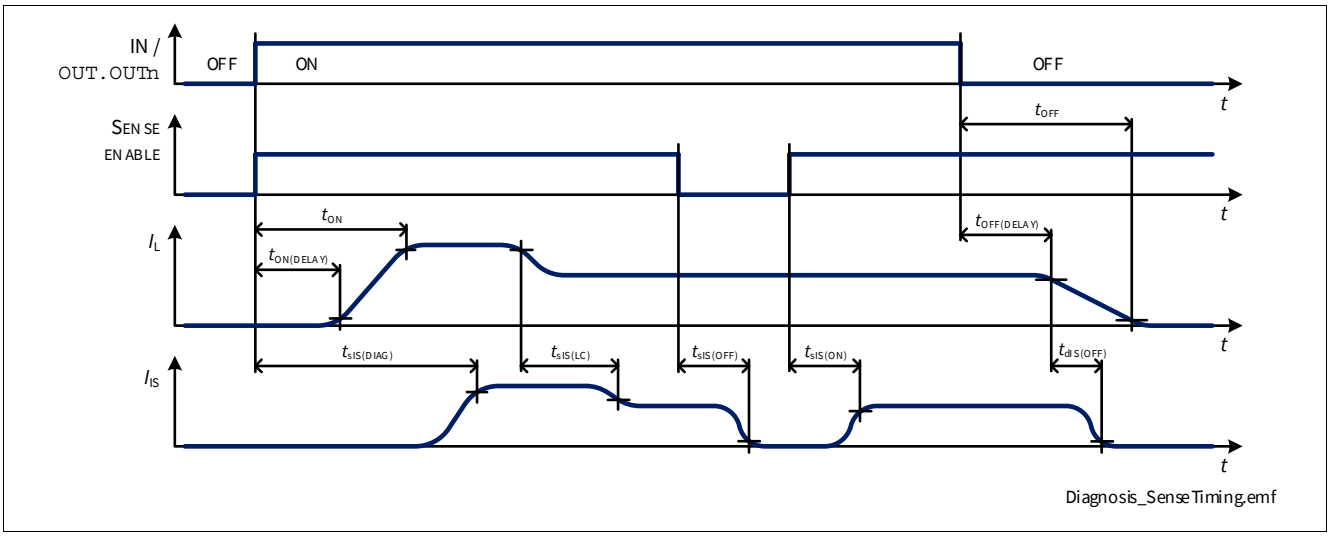



**Figure 35 SENSE Settling / Disabling Timing**

## 9.6 Electrical Characteristics Diagnosis

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

22.5 mΩ: $R_L$ = 4.8 Ω

**Table 22 Electrical Characteristics: Diagnosis - General**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| SENSE Saturation Current | $I_{IS(SAT)}$ | 4.2 | – | 15 | mA | 1)<br>$R_{SENSE}$ = 1.2 kΩ | P_9.6.0.12 |
| SENSE Saturation Current | $I_{IS(SAT)}$ | 5 | – | 15 | mA | 1)<br>$R_{SENSE}$ = 1.2 kΩ<br>$V_S$ = 8 V to 18 V | P_9.6.0.17 |
| SENSE Leakage Current when Disabled | $I_{IS(OFF)}$ | – | 0.01 | 0.5 | µA | $I_L \geq I_{L(NOM)}$<br>$V_{IS}$ = 0 V<br>DCR.MUX = $110_B$ | P_9.6.0.2 |
| SENSE Leakage Current when Enabled at $T_J \leq$ 85 °C | $I_{IS(EN)\_85}$ | – | 0.2 | 1 | µA | 1)<br>$T_J \leq$ 85 °C<br>DCR.MUX ≠ <$110_B$,$111_B$><br>See **Figure 33** | P_9.6.0.3 |
| SENSE Leakage Current when Enabled at $T_J$ = 150 °C | $I_{IS(EN)\_150}$ | – | 1 | 2 | µA | $T_J$ = 150 °C<br>DCR.MUX ≠ <$110_B$,$111_B$><br>See **Figure 33** | P_9.6.0.11 |
| Saturation Voltage in $k_{ILIS}$ Operation ($V_S$ - $V_{IS}$) | $V_{SIS\_k}$ | – | 0.5 | 1 | V | 1)<br>$V_S$ = 6 V<br><br>INx = “high” or OUT.OUTn = $1_B$<br>$I_L \leq 2 * I_{L(NOM)}$ | P_9.6.0.6 |
| Power Supply to IS Pin Clamping Voltage at $T_J$ = -40 °C | $V_{SIS(CLAMP)\_-40}$ | 33 | 36.5 | 42 | V | $I_{IS}$ = 1 mA<br>$T_J$ = -40 °C<br>See **Figure 20** | P_9.6.0.9 |
| Power Supply to IS Pin Clamping Voltage at $T_J \geq$ 25 °C | $V_{SIS(CLAMP)\_25}$ | 35 | 38 | 44 | V | 2)<br>$I_{IS}$ = 1 mA<br>$T_J \geq$ 25 °C<br>See **Figure 20** | P_9.6.0.10 |

1) Not subject to production test - specified by design.

2) Tested at $T_J$ = 150°C.

### 9.6.1 Electrical Characteristics Diagnosis

**Table 23 Electrical Characteristics: Diagnosis - Thresholds, Timings**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Switch Bypass Monitor Threshold | $V_{DS(SB)}$ | 1.3 | 1.9 | 2.5 | V | OFF state | P_9.6.2.1 |
| SENSE Settling Time with Nominal Load Current Stable | $t_{sIS(ON)}$ | – | 8 | 20 | µs | $V_S$ = 13.5 V<br>$I_L = I_{L(NOM)}$<br>**DCR.MUX**: $110_B \rightarrow 001_B$ | P_9.6.2.2 |
| SENSE Settling Time with Small Load Current Stable | $t_{sIS(ON)\_SLC}$ | – | – | 60 | µs | 2)<br>$V_S$ = 13.5 V<br>$I_L = I_{L(CAL)\_OL}$<br>**DCR.MUX**: $110_B \rightarrow 001_B$ | P_9.6.2.10 |
| SENSE Settling Time after Channel Change | $t_{sIS(CC)}$ | – | – | 20 | µs | 1)<br>$V_S$ = 13.5 V<br>$I_L = I_{L(NOM)}$<br>**DCR.MUX**: $001_B \rightarrow 010_B$ | P_9.6.2.4 |
| SENSE Settling Time after Channel Change with Small Load Current | $t_{sIS(CC)\_SLC}$ | – | – | 60 | µs | 2)<br>$V_S$ = 13.5 V<br>Start channel:<br>$I_L = I_{L(CAL)}$<br>End channel:<br>$I_L = I_{L(CAL)\_OL}$<br>**DCR.MUX**: $001_B \rightarrow 010_B$ | P_9.6.2.11 |
| SENSE Disable Time | $t_{sIS(OFF)}$ | – | – | 20 | µs | 1)<br>$V_S$ = 13.5 V<br>$I_L = I_{L(NOM)}$<br>**DCR.MUX**: $010_B \rightarrow 110_B$ | P_9.6.2.5 |
| SENSE Settling Time after Load Change | $t_{sIS(LC)}$ | – | – | 20 | µs | 2) | P_9.6.2.6 |
| SENSE Settling Time after Load Change with Small Load Current | $t_{sIS(LC)\_SLC}$ | – | 250 | 400 | µs | 2)<br>$V_S$ = 13.5 V<br>from $I_L = I_{L(CAL)}$ to $I_L = I_{L(CAL)\_OL}$ | P_9.6.2.12 |
| SENSE Disable Time after Channel Deactivation | $t_{dIS(OFF)}$ | – | – | 20 | µs | 2) | P_9.6.2.7 |
| SENSE Current in Sense Verification Mode | $I_{IS(VER)}$ | 400 | 500 | 600 | µA | **DCR.MUX** = $101_B$ | P_9.6.2.8 |

1) Production test for functionality within parameter limits.

2) Not subject to production test - specified by design.

## 9.7 Electrical Characteristics Diagnosis - Power Output Stages

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

Typical resistive loads connected to the outputs for testing (unless otherwise specified):

22.5 mΩ: $R_L$ = 4.8 Ω

### 9.7.1 Diagnosis Power Output Stage - 22.5 mΩ

**Table 24 Electrical Characteristics: Diagnosis - 22.5 mΩ - high range[1)]**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Open Load Output Current at $I_{IS}$ = 4 µA | $I_{L(OL)\_4u}$ | 2 | 7 | 15 | mA | [2)] $I_{IS} = I_{IS(OL)}$ = 4 µA | P_9.7.16.1 |
| Current Sense Ratio at $I_L = I_{L01}$ | $k_{ILIS01}$ | -65% | 2000 | +65% | | [2)] $I_{L01}$ = 10 mA | P_9.7.16.3 |
| Current Sense Ratio at $I_L = I_{L03}$ | $k_{ILIS03}$ | -60% | 2000 | +60% | | [2)] $I_{L03}$ = 30 mA | P_9.7.16.5 |
| Current Sense Ratio at $I_L = I_{L05}$ | $k_{ILIS05}$ | -55% | 2000 | +55% | | [2)] $I_{L05}$ = 100 mA | P_9.7.16.7 |
| Current Sense Ratio at $I_L = I_{L07}$ | $k_{ILIS07}$ | -45% | 2000 | +45% | | [2)] $I_{L07}$ = 250 mA | P_9.7.16.9 |
| Current Sense Ratio at $I_L = I_{L10}$ | $k_{ILIS10}$ | -24% | 2000 | +24% | | $I_{L10}$ = 1 A | P_9.7.16.12 |
| Current Sense Ratio at $I_L = I_{L12}$ | $k_{ILIS12}$ | -8% | 2000 | +8% | | $I_{L12}$ = 2 A | P_9.7.16.14 |
| Current Sense Ratio at $I_L = I_{L15}$ | $k_{ILIS15}$ | -8% | 2000 | +8% | | $I_{L15}$ = 5.5 A | P_9.7.16.17 |
| SENSE Current Derating with Low Current Calibration | $\Delta k_{ILIS(OL)}$ | -30 | 0 | +30 | % | [2)3)] $I_{L(CAL)\_OL} = I_{L03}$ $I_{L(CAL)\_OL\_H} = I_{L05}$ $I_{L(CAL)\_OL\_L} = I_{L01}$ $T_{A(CAL)}$ = 25 °C | P_9.7.16.37 |
| SENSE Current Derating with Nominal Current Calibration | $\Delta k_{ILIS(NOM)}$ | -9 | 0 | +9 | % | [3)] $I_{L(CAL)} = I_{L12}$ $I_{L(CAL)\_H} = I_{L15}$ $I_{L(CAL)\_L} = I_{L10}$ $T_{A(CAL)}$ = 25 °C | P_9.7.16.38 |

1) Parameter valid only if **KRC.KRCn** = $0_B$.
2) Parameter valid only if **PCS.PCCn** = $0_B$.
3) Not subject to production test - specified by design.

**Table 25 Electrical Characteristics: Diagnosis - 22.5 mΩ - low range[1)]**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| Open Load Output Current at $I_{IS}$ = 4 µA | $I_{L(OL)\_4u}$ | 0.5 | 3.2 | 6 | mA | 2)3) $I_{IS} = I_{IS(OL)}$ = 4 µA | P_9.7.16.18 |
| Current Sense Ratio at $I_L = I_{L00}$ | $k_{ILIS00}$ | -65% | 660 | +65% | | 2)3) $I_{L00}$ = 5 mA | P_9.7.16.19 |
| Current Sense Ratio at $I_L = I_{L01}$ | $k_{ILIS01}$ | -60% | 660 | +60% | | 2)3) $I_{L01}$ = 10 mA | P_9.7.16.20 |
| Current Sense Ratio at $I_L = I_{L03}$ | $k_{ILIS03}$ | -55% | 660 | +55% | | 2)3) $I_{L03}$ = 30 mA | P_9.7.16.23 |
| Current Sense Ratio at $I_L = I_{L05}$ | $k_{ILIS05}$ | -45% | 660 | +45% | | 2)3) $I_{L05}$ = 100 mA | P_9.7.16.26 |
| Current Sense Ratio at $I_L = I_{L07}$ | $k_{ILIS07}$ | -30% | 660 | +30% | | 2)3) $I_{L07}$ = 250 mA | P_9.7.16.29 |
| Current Sense Ratio at $I_L = I_{L08}$ | $k_{ILIS08}$ | -20% | 660 | +20% | | 3) $I_{L08}$ = 450 mA | P_9.7.16.31 |
| Current Sense Ratio at $I_L = I_{L10}$ | $k_{ILIS10}$ | -8% | 660 | +8% | | 3) $I_{L10}$ = 1 A | P_9.7.16.33 |
| Current Sense Ratio at $I_L = I_{L12}$ | $k_{ILIS12}$ | -8% | 660 | +8% | | 3) $I_{L12}$ = 2 A | P_9.7.16.35 |
| SENSE Current Derating with Low Current Calibration | $\Delta k_{ILIS(OL)}$ | -30 | 0 | +30 | % | 2)4) $I_{L(CAL)\_OL} = I_{L01}$ $I_{L(CAL)\_OL\_H} = I_{L03}$ $I_{L(CAL)\_OL\_L} = I_{L00}$ $T_{A(CAL)}$ = 25 °C | P_9.7.16.39 |
| SENSE Current Derating with Nominal Current Calibration | $\Delta k_{ILIS(NOM)}$ | -9 | 0 | +9 | % | 2)4) $I_{L(CAL)} = I_{L10}$ $I_{L(CAL)\_H} = I_{L12}$ $I_{L(CAL)\_L} = I_{L08}$ $T_{A(CAL)}$ = 25 °C | P_9.7.16.40 |

1) Parameter valid only if **KRC.KRCn** = $1_B$.
2) Parameter valid only if **PCS.PCCn** = $0_B$.
3) $k_{ILIS}$ accuracy valid if 1 µs RC filter is placed at ADC input.
4) Not subject to production test - specified by design.

# 10 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) is a full duplex synchronous serial slave interface, which uses four lines: SO, SI, SCLK and CSN. Data is transferred by the lines SI and SO at the rate given by SCLK. The falling edge of CSN indicates the beginning of an access. Data is sampled-in on line SI at the falling edge of SCLK and shifted out on line SO at the rising edge of SCLK. Each access must be terminated by a rising edge of CSN. A modulo 8 counter ensures that data is taken only when a multiple of 8 bit has been transferred. The interface provides daisy chain capability with modulo 8 bit SPI devices.

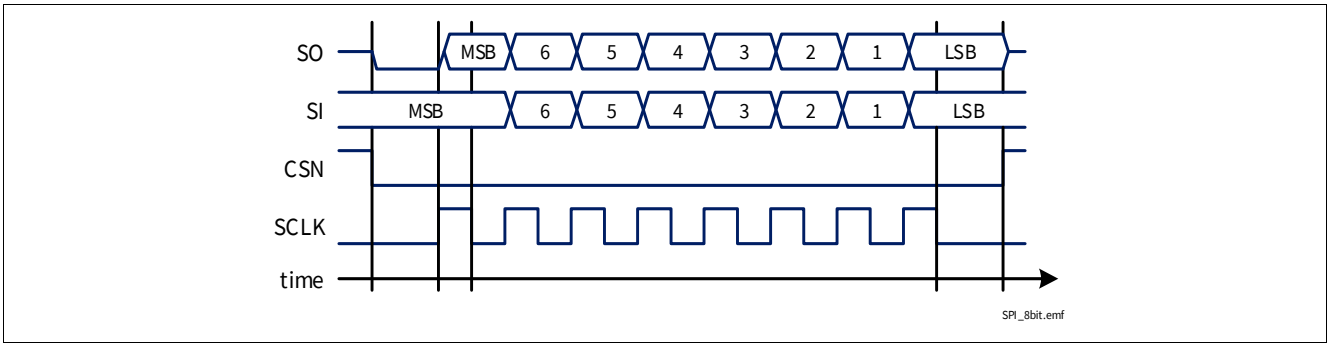



**Figure 36 Serial Peripheral Interface**

## 10.1 SPI Signal Description

### CSN - Chip Select Negated

The system microcontroller selects the BTS71040-4ESP by means of the CSN pin. Whenever the pin is in “low” state, data transfer can take place. When CSN is in “high” state, any signals at the SCLK and SI pins are ignored and SO is forced into a “high impedance” state.

### CSN “high” to “low” Transition

- The requested information is transferred into the shift register.
- SO changes from “high impedance” state to “low” state.

### CSN “low” to “high” Transition

- Command decoding is only done, when after the falling edge of CSN exactly a multiple (1, 2, 3, …) of eight SCLK signals have been detected. In case of an incorrect SCLK count, the transmission error flag (**STDDIAG.TER**) is set and the command is ignored.
- Data from shift register is transferred into the addressed register.

### SCLK - Serial Clock

This input pin clocks the internal shift register. The serial input (SI) transfers data into the shift register on the falling edge of SCLK while the serial output (SO) shifts diagnostic information out on the rising edge of the serial clock. It is essential that the SCLK pin is in “low” state whenever chip select CSN makes any transition, otherwise the command may not be accepted.

### SI - Serial Input

Serial input data bits are shifted in at this pin, the most significant bit first. SI information is read on the falling edge of SCLK. The input data consists of two parts, control bits followed by data bits. Please refer to **Chapter 10.5** for further information.

### SO Serial Output

Data is shifted out serially at this pin, the most significant bit first. SO is in “high impedance” state until the CSN pin goes to “low” state. New data will appear at the SO pin following the rising edge of SCLK.

Please refer to **Chapter 10.5** for further information.

## 10.2 Daisy Chain Capability

The SPI of BTS71040-4ESP provides daisy chain capability for modulo 8 bit SPI devices. In this configuration several devices are activated by the same CSN signal MCSN. The SI line of one device is connected with the SO line of another device (see **Figure 37**), in order to build a chain. The end of the chain is connected to the output and input of the master device, MO and MI respectively. The master device provides the master clock MCLK which is connected to the SCLK line of each device in the chain.

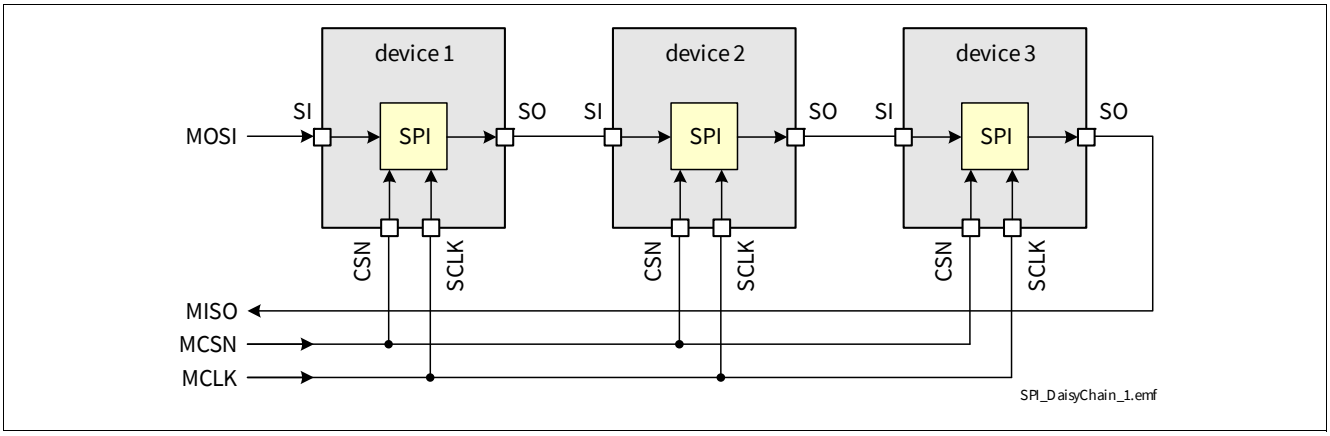



**Figure 37 Daisy Chain Configuration**

In the SPI block of each device, there is one shift register where each bit from SI line is shifted in each SCLK. The bit is shifted out on SO pin. After eight SCLK cycles, the data transfer for one device is finished. In single chip configuration, the CSN line must turn “high” to make the device acknowledge the transferred data. In daisy chain configuration, the data shifted out at device 1 has been shifted into device 2. When using three devices in daisy chain, three times 8 bits have to be shifted through the devices. After that, the MCSN line must turn “high” (see **Figure 38**).

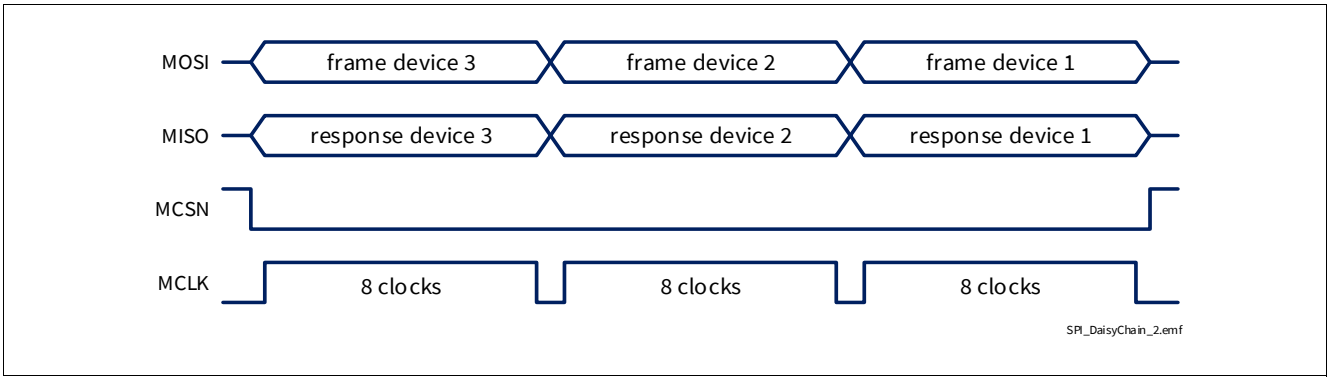



**Figure 38 Data Transfer in Daisy Chain Configuration**

## 10.3 Timing Diagrams

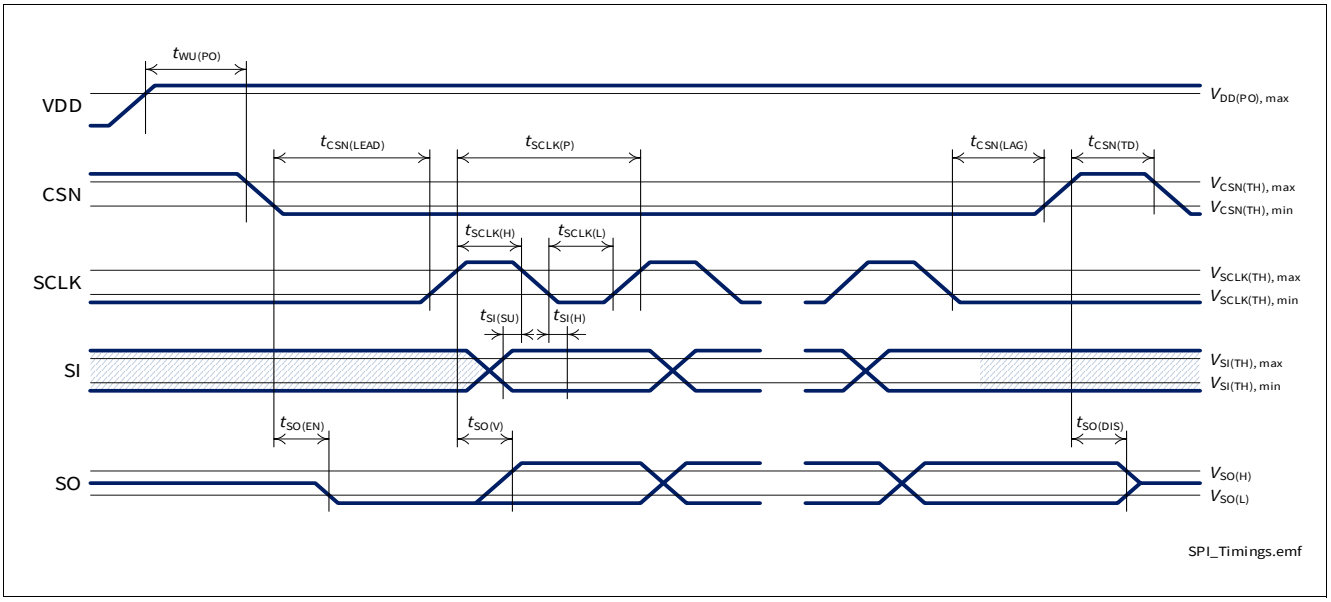



**Figure 39 Timing Diagram SPI Access**

## 10.4 Electrical Characteristics

$V_{DD}$ = 3.0 V to 5.5 V, $V_S$ = 6 V to 18 V, $T_J$ = -40 °C to +150 °C
Typical values: $V_{DD}$ = 5.0 V, $V_S$ = 13.5 V, $T_J$ = 25 °C

**Table 26 Electrical Characteristics Serial Peripheral Interface (SPI)**

| Parameter | Symbol | Values | | | Unit | Note or Test Condition | Number |
|---|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | | |
| **Timings** | | | | | | | |
| Enable Lead Time (falling CSN to rising SCLK) | $t_{CSN(LEAD)}$ | 200 | – | – | ns | 1) | P_10.4.0.1 |
| Enable Lag Time (falling SCLK to rising CSN) | $t_{CSN(LAG)}$ | 200 | – | – | ns | 1) | P_10.4.0.2 |
| Transfer Delay Time (rising CSN to falling CSN) | $t_{CSN(TD)}$ | 500 | – | – | ns | 1) | P_10.4.0.3 |
| Output Enable Time (falling CSN to SO valid) | $t_{SO(EN)}$ | – | 30 | 100 | ns | 1) $C_{L(SO)}$ = 50 pF | P_10.4.0.4 |
| Output Disable Time (rising CSN to SO tristate) | $t_{SO(DIS)}$ | – | 30 | 100 | ns | 1) $C_{L(SO)}$ = 50 pF | P_10.4.0.5 |
| Serial Clock Frequency | $f_{SCLK}$ | 0 | – | 5 | MHz | 1) | P_10.4.0.6 |
| Serial Clock Period | $t_{SCLK(P)}$ | 200 | – | – | ns | 1) | P_10.4.0.7 |
| Serial Clock “High” Time | $t_{SCLK(H)}$ | 90 | – | – | ns | 1) | P_10.4.0.8 |
| Serial Clock “Low” Time | $t_{SCLK(L)}$ | 90 | – | – | ns | 1) | P_10.4.0.9 |
| Data Setup Time (required Time SI to falling SCLK) | $t_{SI(SU)}$ | 20 | – | – | ns | 1) | P_10.4.0.10 |
| Data Hold Time (falling SCLK to SI) | $t_{SI(H)}$ | 20 | – | – | ns | 1) | P_10.4.0.11 |
| Output Data Valid Time with Capacitive Load | $t_{SO(V)}$ | – | – | 60 | ns | 1) $C_{L(SO)}$ = 50 pF | P_10.4.0.12 |

1) Not subject to production test - specified by design.

## 10.5 SPI Protocol

The relationship between SI and SO content during SPI communication is shown in **Figure 40**. SI line represents the frame sent from the µC and SO line is the answer provided by BTS71040-4ESP. The “previous response” means that the frame sent back depends on the command frame sent from the µC before.

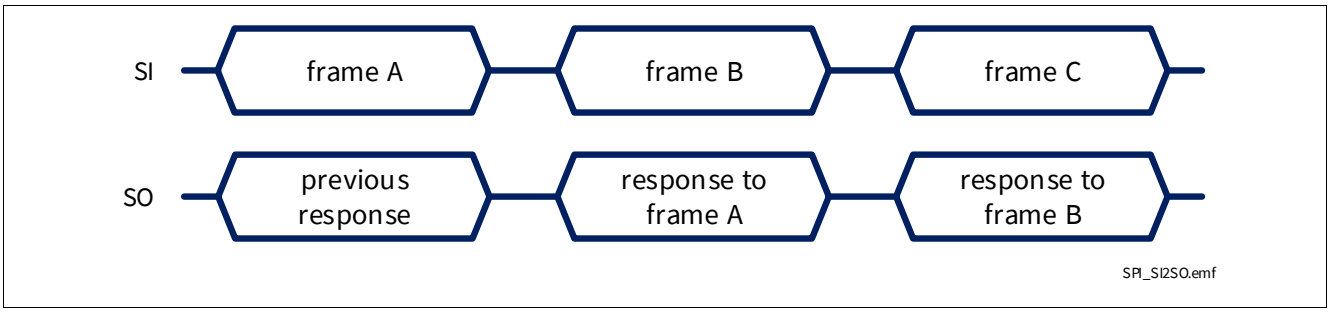



**Figure 40 Relationship between SI and SO during SPI communication**

The SPI protocol provides the answer to a command frame only with the next transmission triggered by the µC. The responses of write commands are deterministic and can be decoded as STDDIAG or WRNDIAG frame. For responses of read commands previous transmission has to be considered for decoding.

More in detail, the sequence of commands to “read” and “write” the content of a register will look as follows:

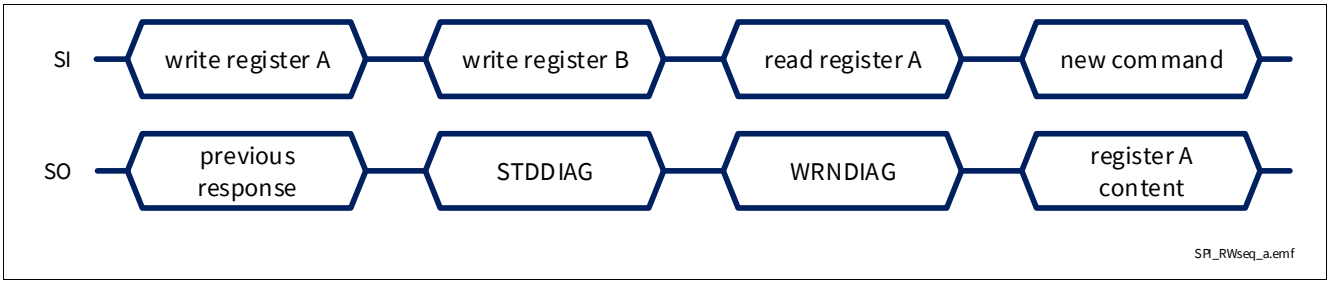



**Figure 41 Register content sent back to µC (a)**

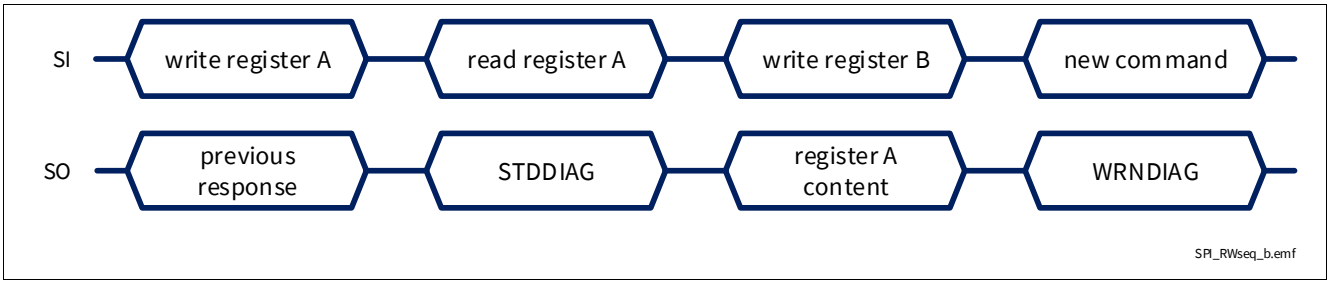



**Figure 42 Register content sent back to µC (b)**

There are 3 special situations where the frame sent back to the µC doesn't depend on the previous received frame:

- In case an error in transmission happened during the previous frame (for instance, the clock pulses were not multiple of 8), shown in **Figure 43**
- When BTS71040-4ESP digital supply comes out of Power-On reset condition, as shown in **Figure 44**
- When $V_S < V_{S(TP)}$ and **DCR.MUX** $\neq 111_B$, as shown in **Figure 45**

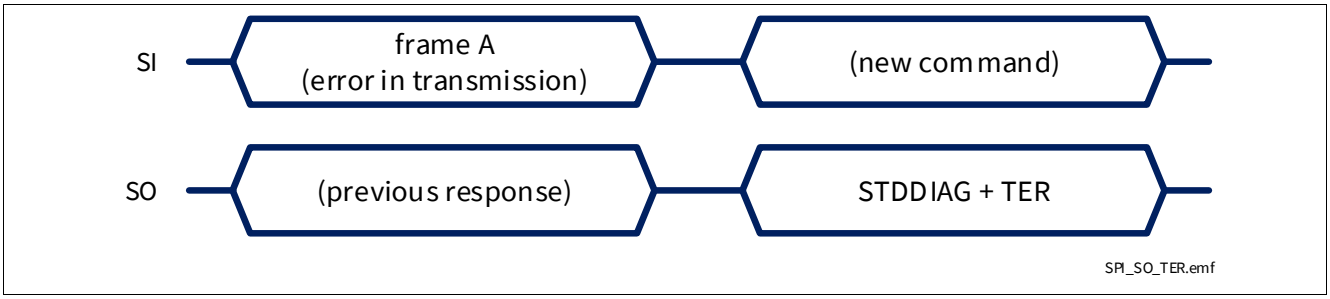



**Figure 43 SPI response after an error in transmission**

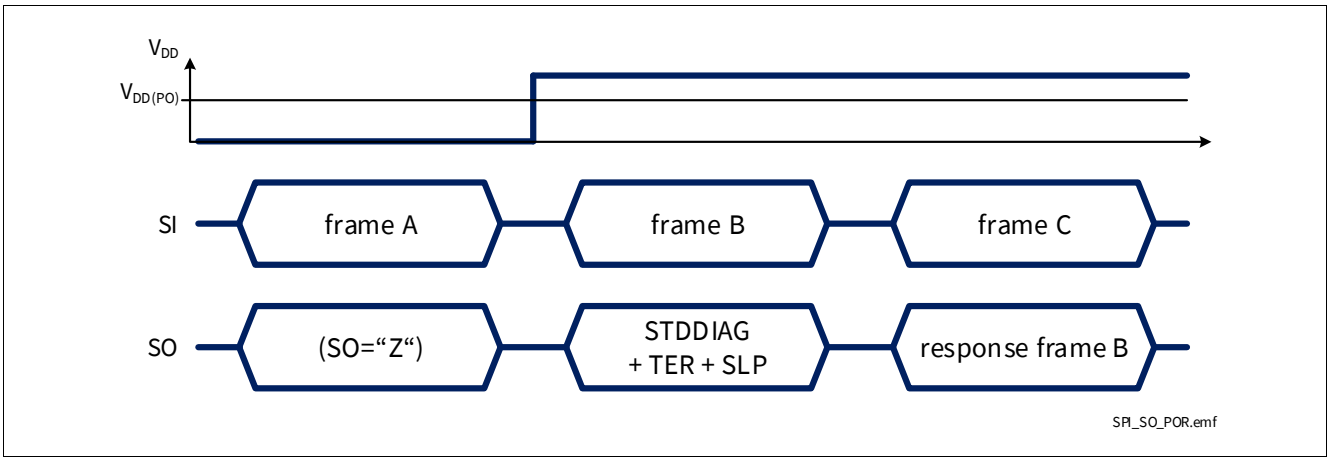



**Figure 44 SPI response after coming out of Power-On reset at $V_{DD}$**

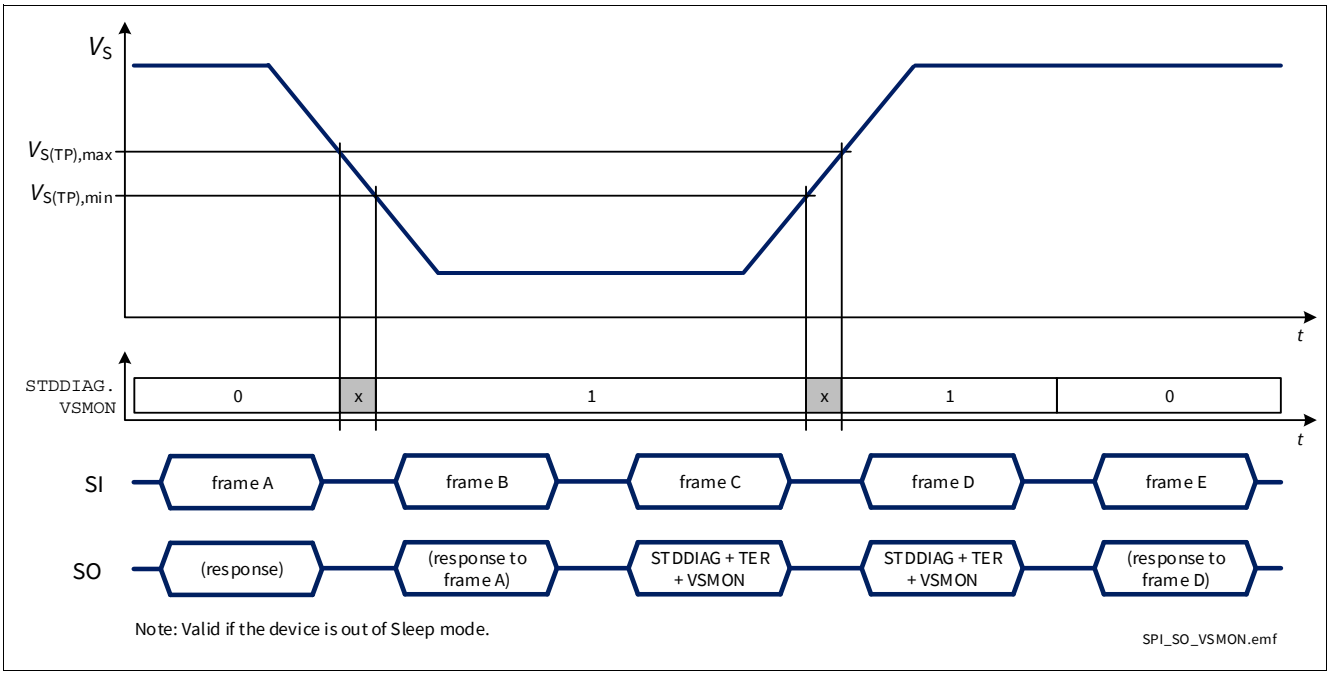



**Figure 45 SPI response in case of voltage drop on battery**

A summary of all possible SPI commands is presented in **Table 27**, including the answer that BTS71040-4ESP will send back at the next transmission.

**Table 27 SPI Command Summary**

| Requested Operation | Frame sent to device (SI pin) | Frame received from device (SO pin) with the next command |
|---|---|---|
| Write **OUT** register **DCR.SWR** = $x_B$ | $100xdddd_B$<br>where:<br>"$xdddd_B$" = new **OUT** register content<br>("$x_B$" = don't care) | $00dddddd_B$ - STDDIAG or<br>$01dddddd_B$ - WRNDIAG<br>(Standard Diagnosis or Warning Diagnosis will be sent alternating) |
| Read **OUT** register | $0xxxaaaa_B$<br>where:<br>"$aaaa_B$" = ADDR1 [1]<br>("$x_B$" = don't care) | $1000dddd_B$<br>("$dddd_B$" = **OUT** register content) |
| Read **RCS** register | $0xxxaaaa_B$<br>where:<br>"$aaaa_B$" = ADDR1 [1]<br>("$x_B$" = don't care) | $10000ddd_B$<br>("$ddd_B$" = **RCS** register content) |
| Write Configuration registers | $11aadddd_B$<br>where:<br>"$aa_B$" = ADDR0 [1]<br>"$dddd_B$" = new register content | $00dddddd_B$ - STDDIAG<br>$01dddddd_B$ - WRNDIAG<br>(Standard Diagnosis or Warning Diagnosis will be sent alternating) |
| Read Configuration registers | $0xxxaaaa_B$<br>where:<br>"$aaaa_B$" = ADDR1 [1]<br>("$x_B$" = don't care) | $11aadddd_B$<br>where:<br>"$aa_B$" = ADDR0 [1]<br>"$dddd_B$" = register content |
| Read Warning Diagnosis | $0xxxx001_B$<br>("$x_B$" = don't care) | $0100dddd_B$ - WRNDIAG<br>(Warning Diagnosis) |
| Read Standard Diagnosis | $0xxxx010_B$<br>("$x_B$" = don't care) | $00dddddd_B$ - STDDIAG<br>(Standard Diagnosis) |
| Read Error Diagnosis | $0xxxx011_B$<br>("$x_B$" = don't care) | $0100dddd_B$ - ERRDIAG<br>(Error Diagnosis) |

1) **ADDR0** and **ADDR1** are defined according to **Table 28**.

## 10.6 SPI Diagnosis Registers

### 10.6.1 Diagnosis Registers - Read Commands

| Name | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|---|---|---|---|---|---|---|---|---|
| **WRNDIAG** | 0 | x | x | x | 0 | 0 | 0 | 1 |
| **STDDIAG** | 0 | x | x | x | 0 | 0 | 1 | 0 |
| **ERRDIAG** | 0 | x | x | x | 0 | 0 | 1 | 1 |

### 10.6.2 Diagnosis Registers - Responses

| Name | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 | Default |
|---|---|---|---|---|---|---|---|---|---|
| **WRNDIAG** | 0 | 1 | 0 | 0 | **WRNDIAG.WRNn** | | | | $40_H$ |
| **STDDIAG** | 0 | 0 | **STDDIAG.TER** | **STDDIAG.CSV** | **STDDIAG.LHI** | **STDDIAG.SLP** | **STDDIAG.SBM** | **STDDIAG.VSMON** | $24_H$ |
| **ERRDIAG** | 0 | 1 | 0 | 0 | **ERRDIAG.ERRn** | | | | $40_H$ |

| Field | Bits | Type | Description |
|---|---|---|---|
| STDDIAG.TER | 5 | r | **Transmission Error**<br>$0_B$ Previous transmission was successful (modulo 8 clocks received)<br>$1_B$ (default) Previous transmission failed or first transmission after Power-On reset or $V_S < V_{S(TP)}$ if **STDDIAG.VSMON** = $1_B$ |
| STDDIAG.CSV | 4 | r | **Checksum Verification**[1)]<br>$0_B$ (default) Checksum verification was pass or no checksum calculated<br>$1_B$ Previous checksum verification was fail |
| STDDIAG.LHI | 3 | r | **Limp Home monitor**<br>$0_B$ (default) “Low” level at pin LHI<br>$1_B$ “High” level at pin LHI |
| STDDIAG.SLP | 2 | r | **Sleep mode monitor**<br>$0_B$ Device out of Sleep mode<br>$1_B$ (default) Device is in Sleep mode |
| STDDIAG.SBM | 1 | r | **Switch Bypass Monitor**[2)]<br>$0_B$ $V_{DS} < V_{DS(SB)}$<br>$1_B$ $V_{DS} > V_{DS(SB)}$ |
| STDDIAG.VSMON | 0 | r | **$V_S$ monitor**<br>$0_B$ (default) $V_S$ always > $V_{S(UV)}$ since last Standard Diagnosis readout<br>$1_B$ $V_S < V_{S(UV)}$ at least once or $V_S < V_{S(TP)}$ if **STDDIAG.TER** = $1_B$ |

| Field | Bits | Type | Description |
|---|---|---|---|
| WRNDIAG.WRNn<br>n = 3 to 0 | 3:0 | r | **Warning Diagnosis of Channel n**<br>$0_B$ (default) No failure<br>$1_B$ Overcurrent, Overtemperature or delta T detected |
| ERRDIAG.ERRn<br>n = 3 to 0 | 3:0 | r | **Error Diagnosis of Channel n**<br>$0_B$ (default) No failure<br>$1_B$ Channel latched OFF |

1) See **Chapter 10.8** for details on checksum calculation.
2) The switch bypass monitor compares the threshold $V_{DS(SB)}$ with the voltage $V_{DS}$ across the power transistor of that channel which is selected by the current sense multiplexer (**DCR.MUX**).

## 10.7 SPI Configuration Registers

The following table provides an overview on the registers available and the available address space.

**Table 28 Register Overview**

| Name | SWR [1] | RB | ADDR0 | ADDR1 | Content |
|---|---|---|---|---|---|
| OUT | x/0 [2] | 0 | (na) | 0000 | Output configuration |
| RCS | 1 | 0 | (na) | 1000 | Restart counter status (read-only) |
| SRC | 1 | 0 | (na) | 1001 | Slew Rate Control register (read-only) |
| OCR | 0 | 1 | 00 | 0100 | Overcurrent threshold configuration |
| RCD | 1 | 1 | 00 | 1100 | Restart counter disable |
| KRC | 0 | 1 | 01 | 0101 | KILIS range control |
| PCS | 1 | 1 | 01 | 1101 | Parallel channel and Slew Rate control |
| HWCR | 0 | 1 | 10 | 0110 | Hardware configuration |
| ICS | 1 | 1 | 10 | 1110 | Input status & checksum input |
| DCR | x | 1 | 11 | x111 | Diagnostic configuration and Swap bit |

1) **DCR.SWR** bit is only changed for write commands. For read commands it is used as part of the read address.
2) For writing to **OUT** register **DCR.SWR** = x, for read address **DCR.SWR** = $0_B$.

**Table 29 Configuration Registers - Write Commands RB-0**

| Bit | | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|---|---|---|---|---|---|---|---|---|---|
| **Name** | **SWR** | **7** | **RB** | **5** | **4** | **3** | **2** | **1** | **0** |
| **OUT** | x | 1 | 0 | 0 | x | **OUT.OUTn** | | | |

**Table 30 Configuration Registers - Write Commands RB-1**

| Bit | | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|---|---|---|---|---|---|---|---|---|---|
| **Name** | **SWR** | **7** | **RB** | **ADDR0** | | **3** | **2** | **1** | **0** |
| **OCR** | 0 | 1 | 1 | 0 | 0 | **OCR.OCTn** | | | |
| **RCD** | 1 | 1 | 1 | 0 | 0 | **RCD.RCDn** | | | |
| **KRC** | 0 | 1 | 1 | 0 | 1 | **KRC.KRCn** | | | |
| **PCS** | 1 | 1 | 1 | 0 | 1 | **PCS.PCCn** | | **PCS.CLCS** | **PCS.SRCS** |

**Table 30 Configuration Registers - Write Commands RB-1**

| Bit | | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|---|---|---|---|---|---|---|---|---|---|
| **Name** | **SWR** | **7** | **RB** | **ADDR0** | | **3** | **2** | **1** | **0** |
| HWCR | 0 | 1 | 1 | 1 | 0 | 0 | HWCR.COL | HWCR.RST | HWCR.CLC |
| ICS | 1 | 1 | 1 | 1 | 0 | ICS.CSRn [1] | | | |
| DCR | x | 1 | 1 | 1 | 1 | DCR.SWR | DCR.MUX | | |

1) See **Chapter 10.8** for details on checksum calculation.

**Table 31 Configuration Registers - Read Commands**

| Bit | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|---|---|---|---|---|---|---|---|---|
| **Name** | **7** | **6** | **5** | **4** | **ADDR1** | | | |
| OUT | 0 | x | x | x | 0 | 0 | 0 | 0 |
| RCS | 0 | x | x | x | 1 | 0 | 0 | 0 |
| SRC | 0 | x | x | x | 1 | 0 | 0 | 1 |
| OCR | 0 | x | x | x | 0 | 1 | 0 | 0 |
| RCD | 0 | x | x | x | 1 | 1 | 0 | 0 |
| KRC | 0 | x | x | x | 0 | 1 | 0 | 1 |
| PCS | 0 | x | x | x | 1 | 1 | 0 | 1 |
| HWCR | 0 | x | x | x | 0 | 1 | 1 | 0 |
| ICS | 0 | x | x | x | 1 | 1 | 1 | 0 |
| DCR | 0 | x | x | x | x | 1 | 1 | 1 |

**Table 32 Configuration Registers - Responses**

| Bit | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 | |
|---|---|---|---|---|---|---|---|---|---|
| **Name** | **7** | **6** | **5** | **4** | **3** | **2** | **1** | **0** | **Default** |
| OUT | 1 | 0 | 0 | x | OUT.OUTn | | | | $80_H$ |
| RCS | 1 | 0 | 0 | 0 | 0 | RCS.RCSn | | | $80_H$ |
| SRC | 1 | 0 | 0 | 1 | SRC.SRCn | | | | $90_H$ |
| OCR | 1 | 1 | 0 | 0 | OCR.OCTn | | | | $C0_H$ |
| RCD | 1 | 1 | 0 | 0 | RCD.RCDn | | | | $C0_H$ |
| KRC | 1 | 1 | 0 | 1 | KRC.KRCn | | | | $D0_H$ |
| PCS | 1 | 1 | 0 | 1 | PCS.PCCn | | 0 | 0 | $D0_H$ |
| HWCR | 1 | 1 | 1 | 0 | 0 | HWCR.COL | HWCR.SLP | 0 | $E2_H$ |
| ICS | 1 | 1 | 1 | 0 | ICS.INSTn | | | | $E0_H$ |
| DCR | 1 | 1 | 1 | 1 | DCR.SWR | DCR.MUX | | | $F7_H$ |

| Field | Bits | Type | Description |
|---|---|---|---|
| RB | 6 | rw | **Register Bank**<br>$0_B$ (default) Read/write to OUT/RCS register<br>$1_B$ Read/write to other registers |
| OUT.OUTn<br>n = 3 to 0 | 3:0 | rw | **Output Control Register of Channel n**<br>$0_B$ (default) channel is OFF<br>$1_B$ Channel is ON |
| RCS.RCSn<br>n = 2 to 0 | 2:0 | r | **Restart Counter Status of Channel selected via MUX**<br>$000_B$ (default) Restart counter value = 0<br>$001_B$ Restart counter value = 1<br>$010_B$ Restart counter value = 2<br>$011_B$ Restart counter value = 3<br>$100_B$ Restart counter value = 4<br>$101_B$ Restart counter value = 5<br>$110_B$ Restart counter value = 6<br>$111_B$ Restart counter value = 7 |
| SRC.SRCn<br>n = 3 to 0 | 3:0 | r | **Set Slew Rate control for Channel n (read only)**<br>$0_B$ (default) Normal Slew Rate<br>$1_B$ Adjusted Slew Rate |
| OCR.OCTn<br>n = 3 to 0 | 3:0 | rw | **Set Overcurrent Level for Channel n**<br>$0_B$ (default) High level of overcurrent threshold $I_{L(OVL0)}$<br>$1_B$ Low level of overcurrent threshold $I_{L(OVL2)}$ |
| RCD.RCDn<br>n = 3 to 0 | 3:0 | rw | **Set Restart Strategy for Channel n**<br>$0_B$ (default) Automatic restart mode<br>$1_B$ Latch mode |
| KRC.KRCn<br>n = 3 to 0 | 3:0 | rw | **Set Current Sense Ratio Range for Channel n**<br>$0_B$ (default) High range of current sense ratio<br>$1_B$ Low range of current sense ratio |

| Field | Bits | Type | Description |
|---|---|---|---|
| PCS.SRCS | 0 | w | **Set Slew Rate control for Channel selected by DCR.MUX**<br>$0_B$ (default) Normal Slew Rate<br>$1_B$ Adjusted Slew Rate |
| PCS.CLCS | 1 | w | **Clear Restart Counters and Latches for Channel selected by DCR.MUX**<br>$0_B$ (default) Restart counters and latches are untouched<br>$1_B$ Restart counters and latches are reset |
| PCS.PCCn<br>n = 1 to 0 | 3:2 | rw | **Parallel Channel Configuration**<br>$00_B$ (default) Channels are operating independent<br>$01_B$ OUT0 + OUT3 are in parallel configuration<br>$10_B$ OUT1 + OUT2 are in parallel configuration<br>$11_B$ OUT0 + OUT3 and OUT1 + OUT2 are in parallel configuration |
| HWCR.CLC | 0 | w | **Clear Restart Counters and Latches**<br>$0_B$ (default) Restart counters and latches are untouched<br>$1_B$ Restart counters and latches are reset for all channels |
| HWCR.RST | 1 | w | **Reset Command**<br>$0_B$ (default) Normal operation<br>$1_B$ Execute reset command |
| HWCR.SLP | 1 | r | **Sleep Mode**<br>$0_B$ Device is awake<br>$1_B$ (default) DCR.MUX = $111_B$ |
| HWCR.COL | 2 | rw | **Input Combinatorial Logic Configuration**<br>$0_B$ (default) Input signal OR-combined with according OUT register bit[1)]<br>$1_B$ Input signal AND-combined with according OUT register bit |
| ICS.CSRn<br>n = 3 to 0 | 3:0 | w | **Checksum Input Register**<br>4 bit Checksum is written to this register |
| ICS.INSTn<br>n = 3 to 0 | 3:0 | r | **Input Status Monitor Channel n**<br>$0_B$ (default) Input signal is “low”<br>$1_B$ Input signal is “high” |

| Field | Bits | Type | Description |
|---|---|---|---|
| DCR.MUX | 2:0 | rw | **Set Current Sense Multiplexer Configuration in OFF state**<br>$000_B$ IS pin is “high impedance”<br>$001_B$ IS pin is “high impedance”<br>$010_B$ IS pin is “high impedance”<br>$011_B$ IS pin is “high impedance”<br>$100_B$ IS pin is “high impedance”<br>$101_B$ Current sense verification mode<br>$110_B$ IS pin is “high impedance”<br>$111_B$ Sleep mode (IS pin is “high impedance”)<br>**Set Multiplexer Configuration in ON state**<br>$000_B$ Current sense of channel 0 is routed to IS pin<br>$001_B$ Current sense of channel 1 is routed to IS pin<br>$010_B$ Current sense of channel 2 is routed to IS pin<br>$011_B$ Current sense of channel 3 is routed to IS pin<br>$100_B$ IS pin is “high impedance”<br>$101_B$ Current sense verification mode<br>$110_B$ IS pin is “high impedance”<br>$111_B$ Sleep mode (IS pin is “high impedance”) |
| DCR.SWR | 3 | rw | **Switch Register**<br>$0_B$ (default) Registers **OUT**, **OCR**, **KRC**, **HWCR** and **DCR** can be written<br>$1_B$ Registers **OUT**, **RCD**, **PCS**, **ICS** and **DCR** can be written |

1) In Limp Home mode (LHI pin set to “high”) the combinatorial logic is switched to OR-mode.

## 10.8 SPI Checksum Verification

BTS71040-4ESP offers a simple parity check to identify unexpected content or unintended changes of configuration registers. For the checksum calculation a subset of the configuration bits is used, which is expected not to be changed periodically. The checksum calculation is an easy column parity calculation. The configuration bits which are used for the calculation are shown in **Table 34**. The SPI master writes the result to **ICS.CSRn**. After the 4bit checksum is written to **ICS** register, the device is doing once the comparison and the result can be read within the next **STDDIAG** frame in the bit **STDDIAG.CSV**. The **STDDIAG.CSV** bit is cleared with the next **STDDIAG** readout. In case the **ICS** register is not written, the checksum comparison is disabled and the bit **STDDIAG.CSV** = $0_B$. If Limp Home mode is entered after **ICS.CSRn** is written but before **STDDIAG.CSV** is read, the checksum verification is not valid. Same applies in case **STDDIAG.TER** and **STDDIAG.VSMON** are set to $1_B$. In these cases checksum verification result shall be discarded.

**Table 33 Conventions for parity calculation**

| Number of '1' in a column | Result with EVEN-parity | Result with ODD-parity |
|---|---|---|
| EVEN | 0 | 1 |
| ODD | 1 | 0 |

**Table 34 Checksum calculation bit matrix**

| Name | 3 | 2 | 1 | 0 |
|---|---|---|---|---|
| **OCR** | OCT3 | OCT2 | OCT1 | OCT0 |
| **RCD** | RCD3 | RCD2 | RCD1 | RCD0 |
| **KRC** | KRC3 | KRC2 | KRC1 | KRC0 |
| **SRC** | SRC3 | SRC2 | SRC1 | SRC0 |
| **HWCR**/**PCS** | 0 | COL | PCC | PCC0 |
| Parity | even | odd | even | odd |
| **ICS** | CSR3 | CSR2 | CSR1 | CSR0 |

**Table 35 Checksum calculation bit matrix example**

| Name | 3 | 2 | 1 | 0 |
|---|---|---|---|---|
| **OCR** | 0 | 1 | 0 | 0 |
| **RCD** | 1 | 0 | 0 | 0 |
| **KRC** | 0 | 1 | 1 | 0 |
| **SRC** | 0 | 0 | 1 | 0 |
| **HWCR**/**PCS** | 0 | 0 | 0 | 0 |
| Parity | even | odd | even | odd |
| **ICS** | 1 | 1 | 0 | 1 |

## 10.9 SPI command quick list

A summary of the most used SPI commands (read and write operations) is shown in Table 154.

**Table 36 SPI command quick list**

| Name | "read" command [1] | "write" command [2] | SWR [3] |
|---|---|---|---|
| OUT | $0xxx0000_B$ | $10dddddd_B$ | x |
| RCS | $0xxx1000_B$ | | |
| SRC | $0xxx1001_B$ | | |
| OCR | $0xxx0100_B$ | $1100dddd_B$ | 0 |
| RCD | $0xxx1100_B$ | $1100dddd_B$ | 1 |
| KRC | $0xxx0101_B$ | $1101dddd_B$ | 0 |
| PCS | $0xxx1101_B$ | $1101dddd_B$ | 1 |
| HWCR | $0xxx0110_B$ | $1110dddd_B$ | 0 |
| ICS | $0xxx1110_B$ | $1110dddd_B$ | 1 |
| DCR | $0xxxx111_B$ | $1111dddd_B$ | x |
| | | | |
| WRNDIAG | $0xxx0001_B$ | | |
| STDDIAG | $0xxx0010_B$ | | |
| ERRDIAG | $0xxx0011_B$ | | |

1) x = don't care bits.
2) d = data bits.
3) DCR.SWR bit needs to be set for writing a register. For reading a register the DCR.SWR bit is part of the read address.

# 11 Application Information

*Note: The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device.*

## 11.1 Application setup

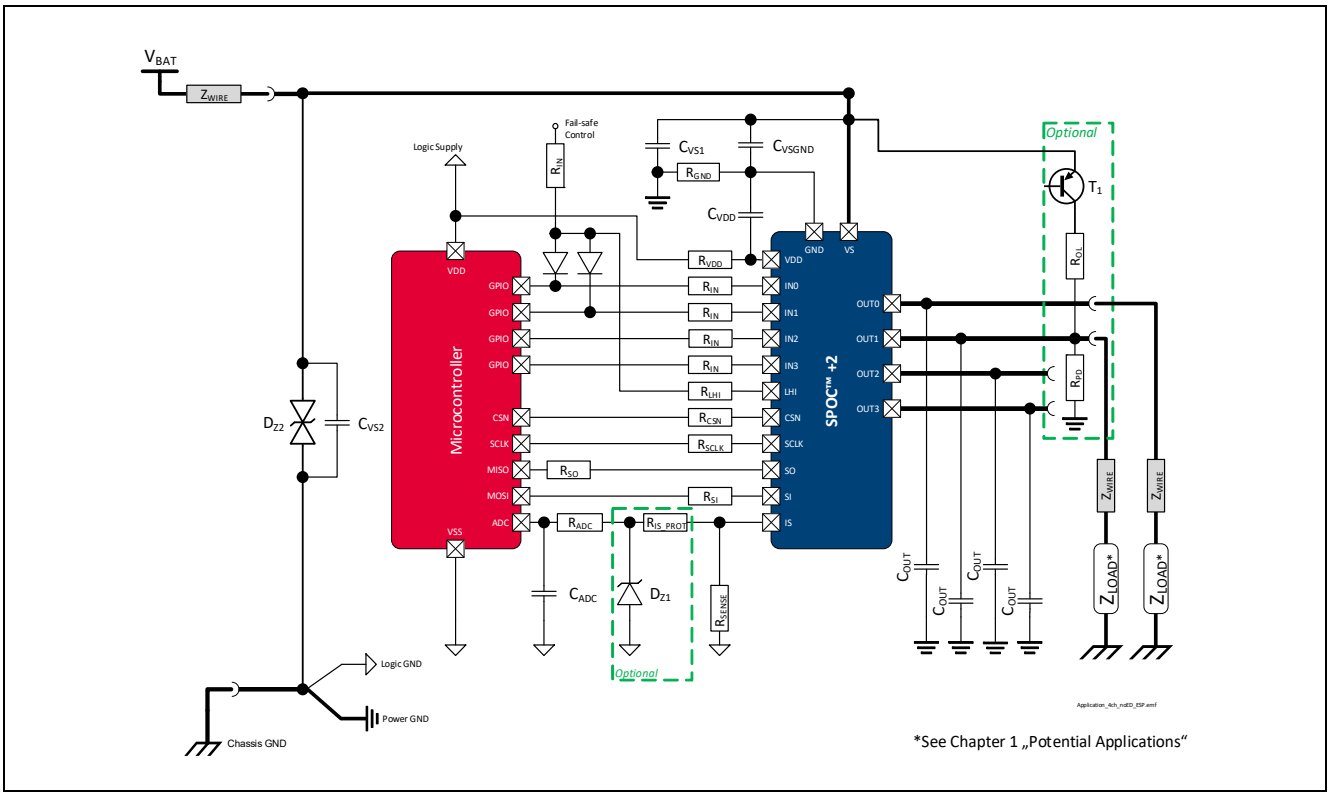



**Figure 46 Application Diagram**

*Note: This is a very simplified example of an application circuit. The function must be verified in the real application.*

## 11.2 External Components

**Table 37 Suggested Component values**

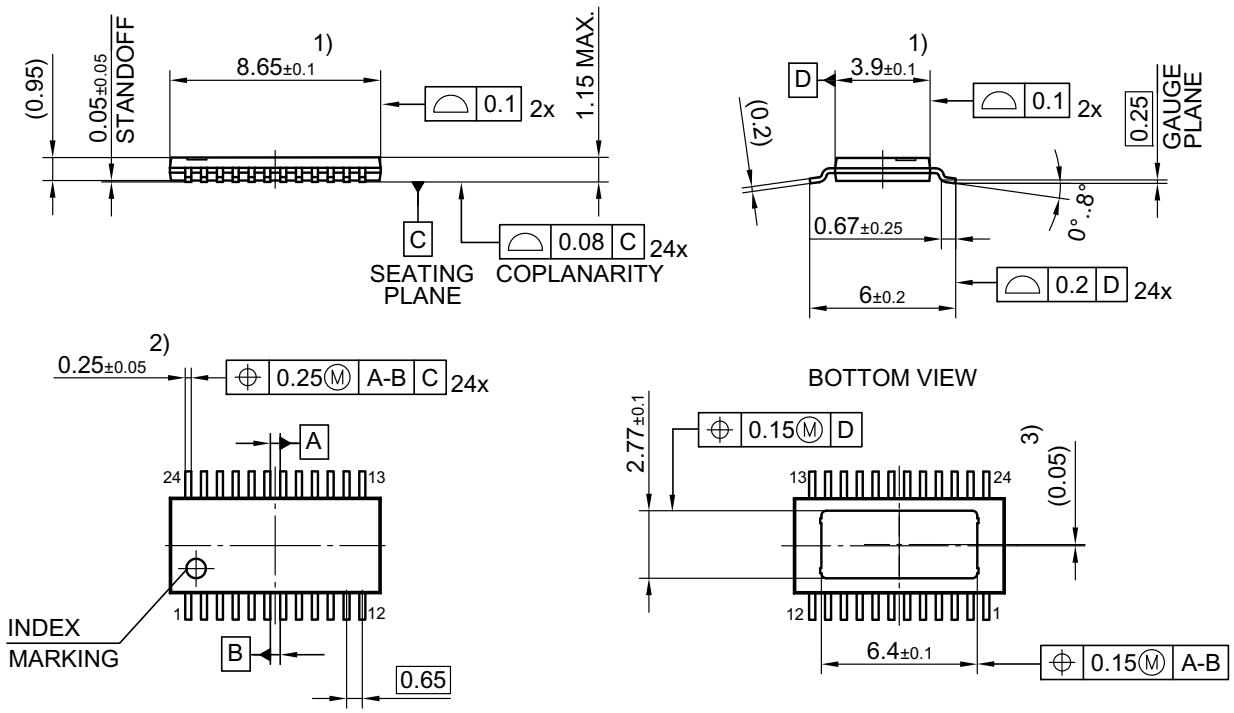
| Reference | Value | Purpose |
|---|---|---|
| $R_{VDD}$ | 470 Ω | Device logic protection |
| $R_{IN}$ | 4.7 kΩ | Protection of the microcontroller during overvoltage, reverse polarity<br>Guarantee BTS71040-4ESP output OFF during Loss of Ground |
| $R_{IS\_PROT}$ | 4.7 kΩ | Protection resistor for overvoltage, reverse polarity and Loss of Ground<br>Value to be tuned with µC specification |
| $R_{SENSE}$ | 1.2 kΩ | Sense resistor |
| $R_{ADC}$ | 4.7 kΩ | µC-ADC voltage spikes filtering |
| $R_{CSN}$ | 1.2 kΩ | Protection of the µC during overvoltage and reverse polarity |
| $R_{SCLK}$ | 1.2 kΩ | Protection of the µC during overvoltage and reverse polarity |
| $R_{SO}$ | 1.2 kΩ | Protection of the µC during overvoltage and reverse polarity |
| $R_{SI}$ | 1.2 kΩ | Protection of the µC during overvoltage and reverse polarity |
| $R_{LHI}$ | 4.7 kΩ | Protection of the µC during overvoltage and reverse polarity |
| $C_{ADC}$ | 220 pF | µC-ADC voltage spikes filtering<br>A time constant ($R_{ADC}$ * $C_{ADC}$) longer than 1 µs is recommended |
| $C_{VDD}$ | 470 nF | Digital supply voltage spikes filtering and for improved robustness against battery voltage transients |
| $C_{VS1}$ | 100 nF | Battery voltage spikes filtering |
| $C_{VS2}$ | - | Filtering / buffer capacitor located at VBAT connector |
| $C_{VSGND}$ | 22 nF | Battery voltage spikes filtering |
| $C_{OUT}$ | 10 nF | For improved electromagnetic compatibility (EMC) |
| $R_{GND}$ | 47 Ω | Ground voltage spikes filtering for improved robustness against battery voltage transients |
| $T_1$ | BC 807 | Switch the battery voltage for Open Load in OFF diagnosis |
| $R_{PD}$ | 47 kΩ | Output polarization (pull-down)<br>Ensure polarization of BTS71040-4ESP output to distinguish between Open Load and Short to $V_S$ in OFF diagnosis |
| $R_{OL}$ | 1.5 kΩ | Output polarization (pull-up)<br>Ensure polarization of BTS71040-4ESP output during Open Load in OFF diagnosis |

*Note: The suggested component values above are determined for typical applications with 5 V microcontrollers. Based on the application circuit and the used components connected to BTS71040-4ESP, it could be necessary to adjust the recommended values to stay below the maximum ratings for all components under all operating conditions (e.g. reverse battery, transients on battery, etc.).*

## 11.3 Further Application Information

- Please contact us for information regarding the Pin FMEA
- For further information you may contact **http://www.infineon.com/**

# 12 Package Outlines




1) DOES NOT INCLUDE PLASTIC OR METAL PROTRUSION OF 0.15 MAX. PER SIDE
2) DAMBAR PROTUSION SHALL BE MAXIMUM 0.1MM TOTAL IN EXCESS OF LEAD WIDTH
3) DISTANCE FROM CENERLINE EXPOSED PAD TO PACKAGE CENTERLINE
ALL DIMENSIONS ARE IN UNITS MM
THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 [ ]

**Figure 47 PG-TSDSO-24** (Thin (Slim) Dual Small Outline 24 pins) **Package drawing**

## Package Outlines

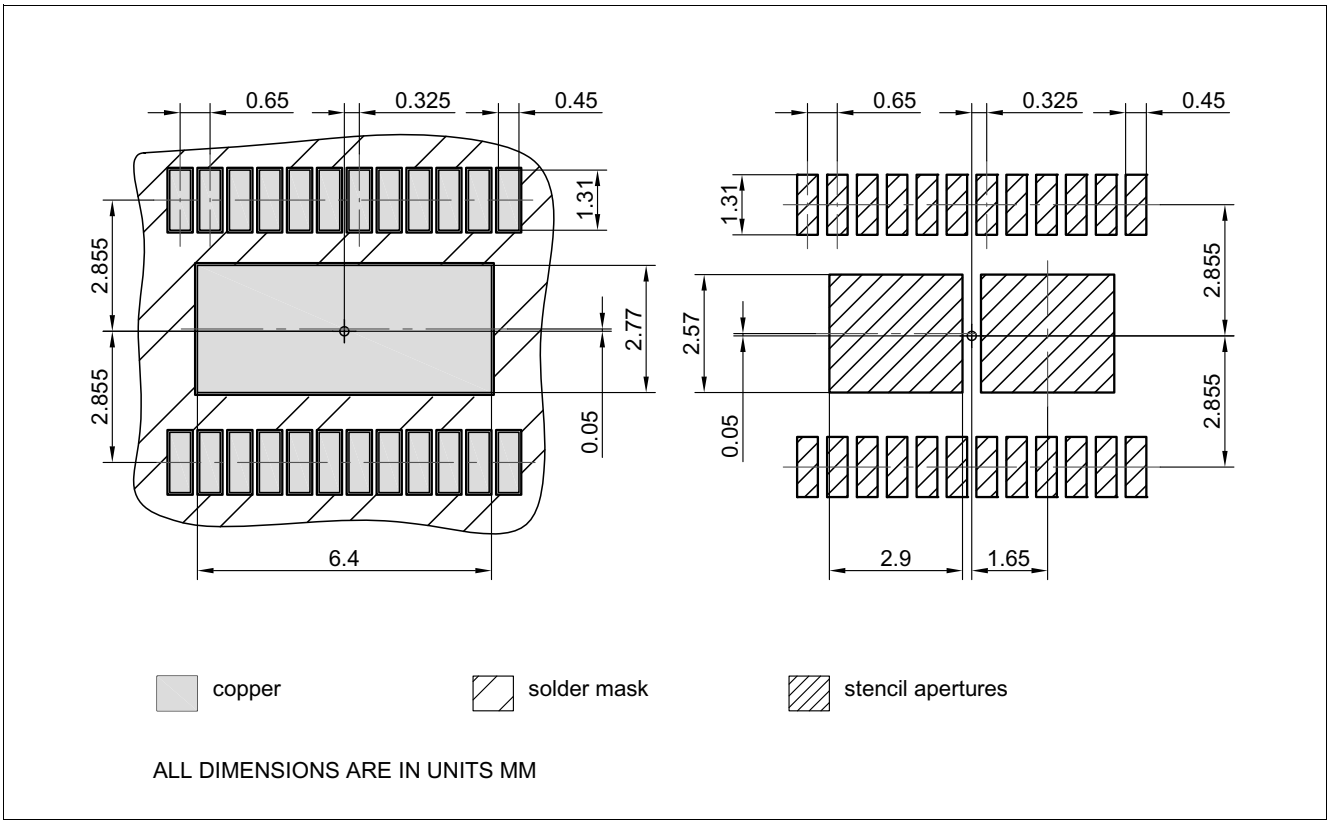



**Figure 48 PG-TSDSO-24** (Thin (Slim) Dual Small Outline 24 pins) **Package pads and stencil**

### Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

### Further information on packages

**https://www.infineon.com/packages**

# 13 Revision History

**Table 38 BTS71040-4ESP - List of changes**

| Revision | Changes |
|---|---|
| **1.00**, 2022-04-05 | Data Sheet available |

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